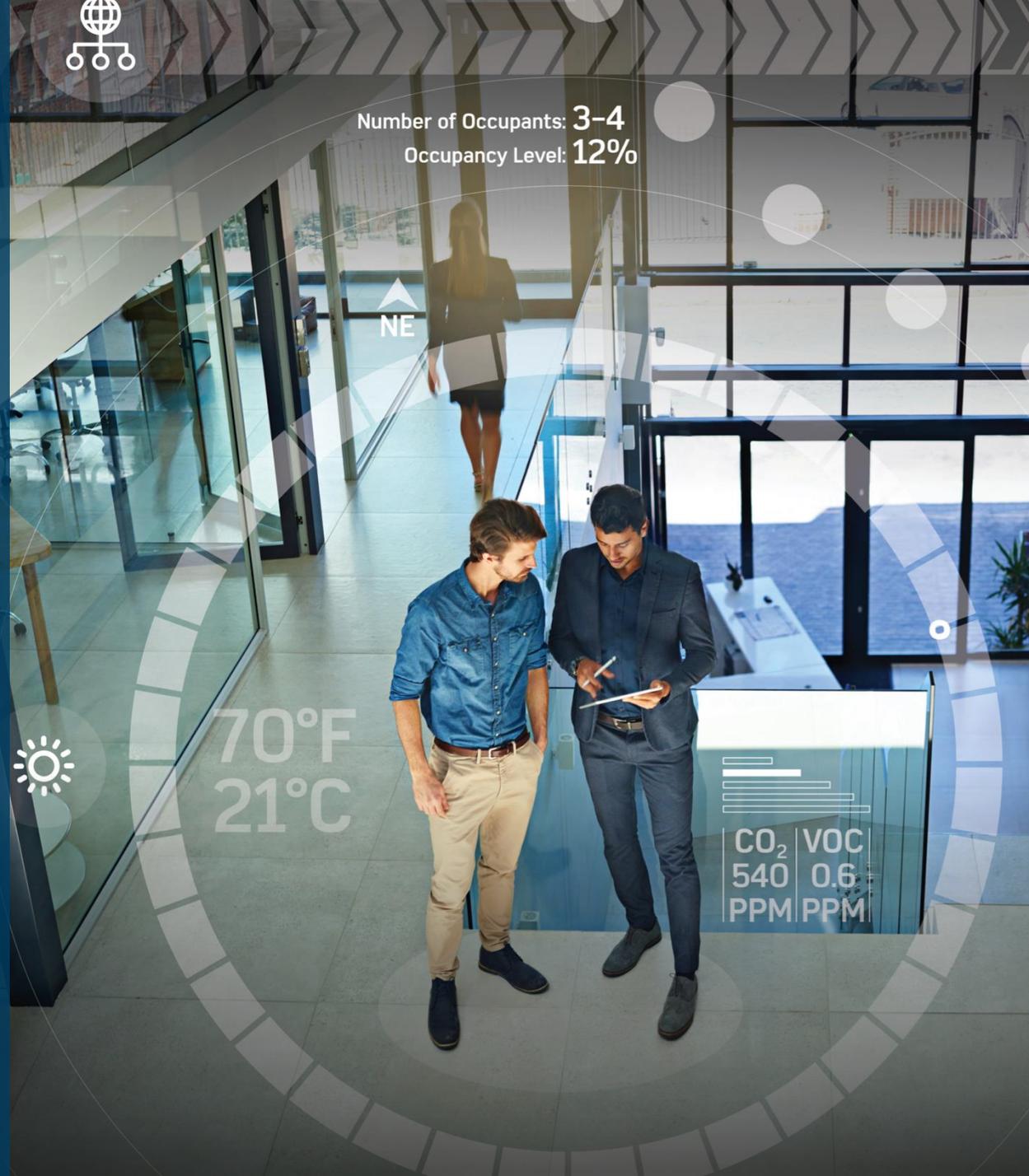




AHEAD OF WHAT'S POSSIBLE™

Mixed-signal technologies for ultra-wide band signal processing systems

GABRIELE MANGANARO

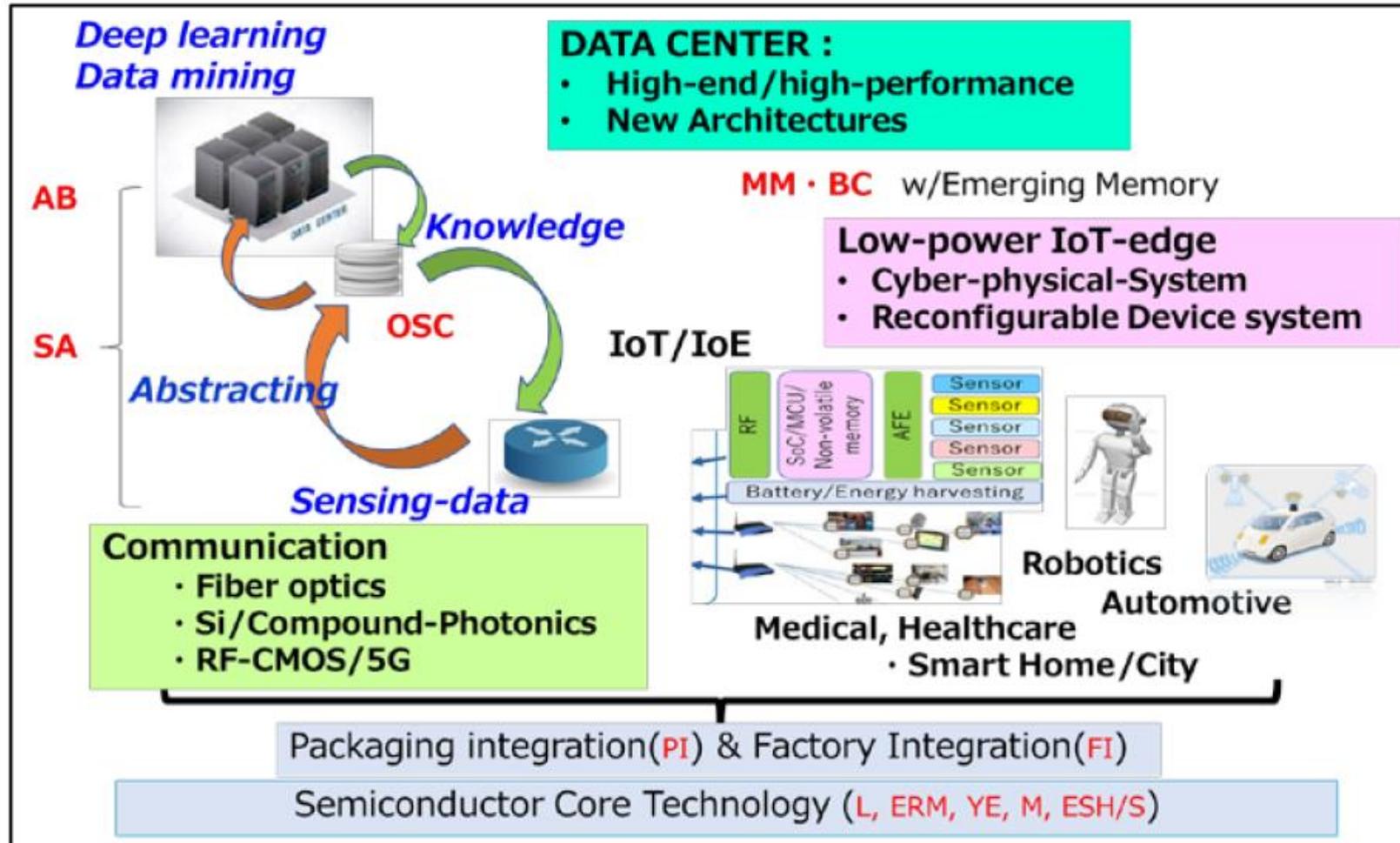


Agenda

- ▶ Motivation / Applications
- ▶ Process Technology
- ▶ ADC architectures
- ▶ Integration
- ▶ Signal Chain Linearization
- ▶ Conclusion

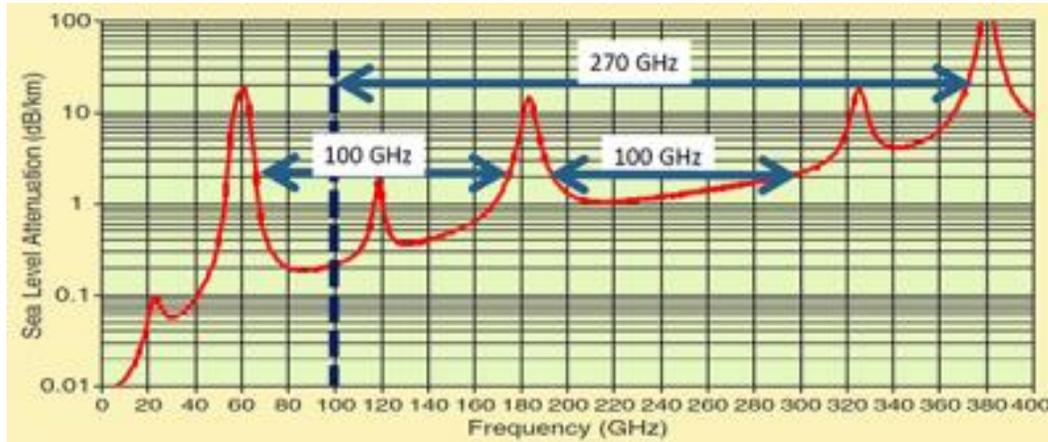
Motivation / Applications

Application pull / Technology Push



- AB: Applications Benchmark
- SA: Systems & Architecture
- OSC: Outside System Connectivity
- MM: Moore Moore
- BC: Beyond CMOS
- PI: Packaging Integration
- FI: Factory Integration
- L: Lithography
- M: Metrology
- ERM: Emerging Research Materials
- YE: Yield Enhancement
- ESH/S: Environment, Safety & Health and Sustainability

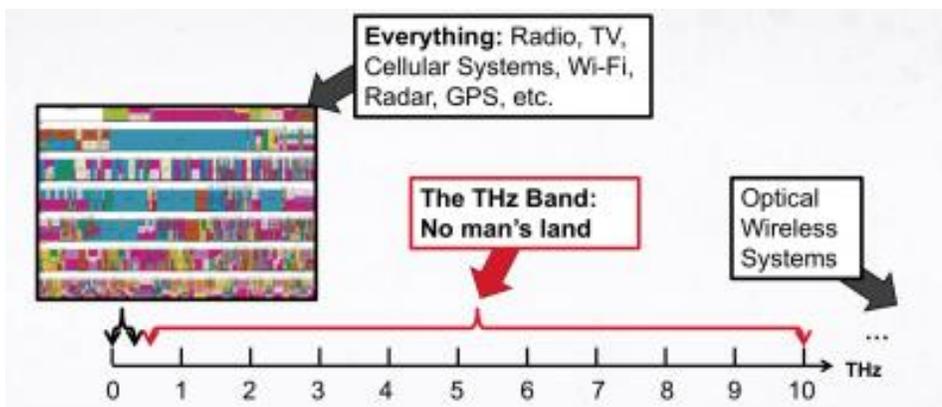
Higher frequency in search for more BANDWIDTH



T. Rappaport et al., “Wireless Communications and Applications Above 100 GHz: Opportunities and Challenges for 6G and Beyond”, IEEE Access, June 2019

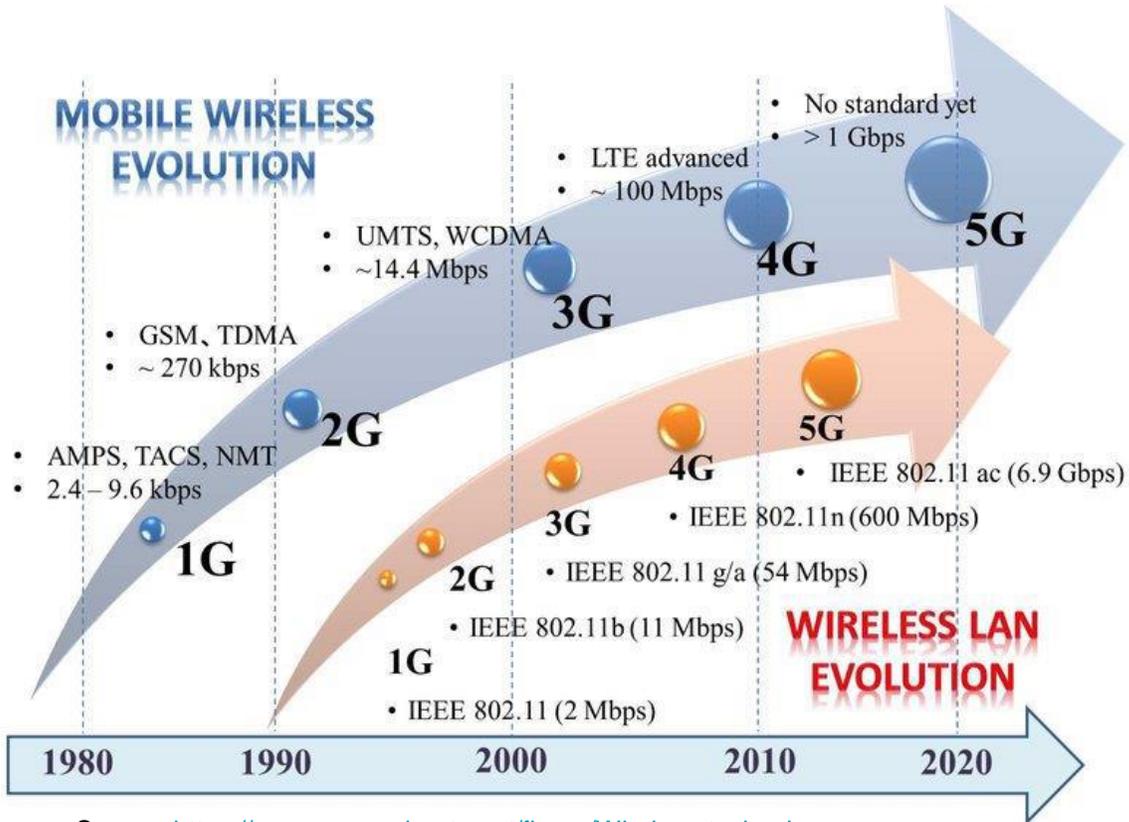
Some application drivers:

- ▶ 6G wireless / “Future Networks”
- ▶ Data centers / Comm Backhaul
- ▶ Immersive virtual reality / remote medicine
- ▶ Broadband sensing for cyber-physical systems
- ▶ Beamformers / wideband radars



J. M. Jornet, “Terahertz Communications: The Quest for Spectrum”, IEEE ComSoc News, 22 Nov 2019

Mobile phone's generations



Source: https://www.researchgate.net/figure/Wireless-technology-evolution_fig1_322584266

	<1GHz	3GHz	4GHz	5GHz	24-30GHz	37-50GHz	64-71GHz	>95GHz
USA	600MHz (2x35MHz)	2.5/2.6GHz (B41/n41)	3.45-3.55GHz, 3.7-4.2GHz	5.9-7.1GHz	24.25-24.45GHz, 24.75-25.25GHz, 27.5-28.35GHz	37-37.6GHz, 37.6-40GHz, 47.2-48.2GHz	64-71GHz	>95GHz
Canada	600MHz (2x35MHz)		3.475-3.65 GHz		26.5-27.5GHz, 27.5-28.35GHz	37-37.6GHz, 37.6-40GHz	64-71GHz	
EU	700MHz (2x30 MHz)		3.4-3.8GHz	5.9-6.4GHz	24.5-27.5GHz			
UK	700MHz (2x30 MHz)		3.4-3.8GHz		26GHz			
Germany	700MHz (2x30 MHz)		3.4-3.8GHz		26GHz			
France	700MHz (2x30 MHz)		3.46-3.8GHz		26GHz			
Italy	700MHz (2x30 MHz)		3.6-3.8GHz		26.5-27.5GHz			
China	700MHz	2.5/2.6GHz (B41/n41)	3.3-3.6GHz	4.8-5GHz	24.75-27.5GHz	40-43.5GHz		
Korea	700/800MHz	2.3-2.39GHz	3.4-3.42GHz, 3.7GHz, 4.0GHz	5.9-7.1GHz	25.7-26.5GHz, 26.5-28.9GHz, 28.9-29.5GHz	37.5-38.7GHz		
Japan			3.6-4.1GHz	4.5-4.9GHz	26.6-27GHz, 27-29.5GHz	39-43.5GHz		
India	700MHz		3.3-3.6GHz		24.25-27.5GHz, 27.5-29.5GHz	37-43.5GHz		
Australia			3.4-3.7GHz		24.25-27.5GHz	39GHz		

Global snapshot of allocated/targeted 5G spectrum

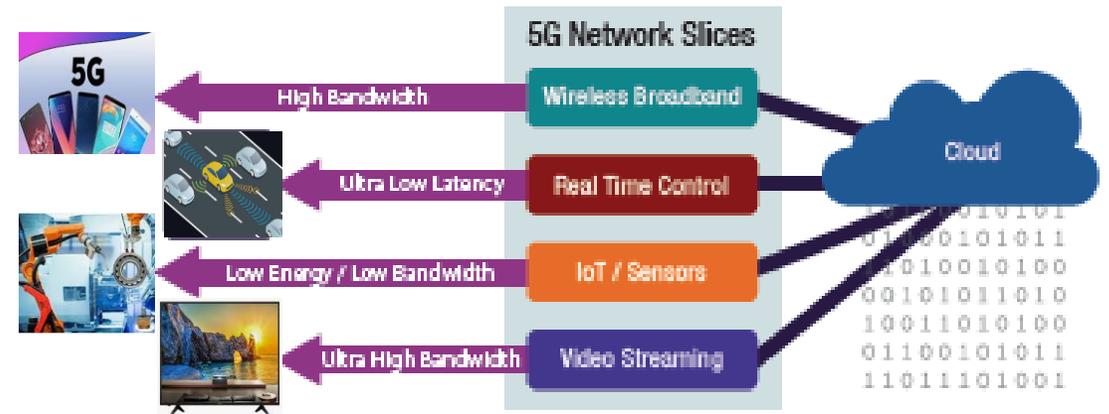
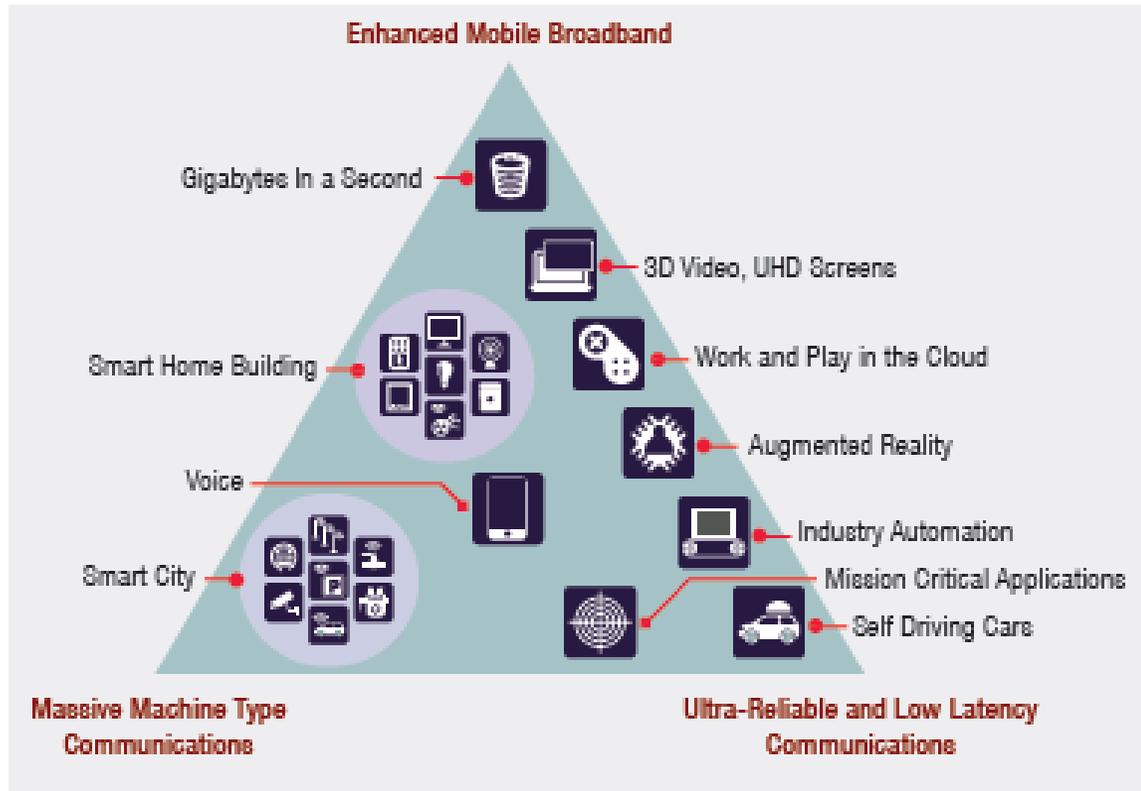
5G is being designed for diverse spectrum types/bands

New 5G band

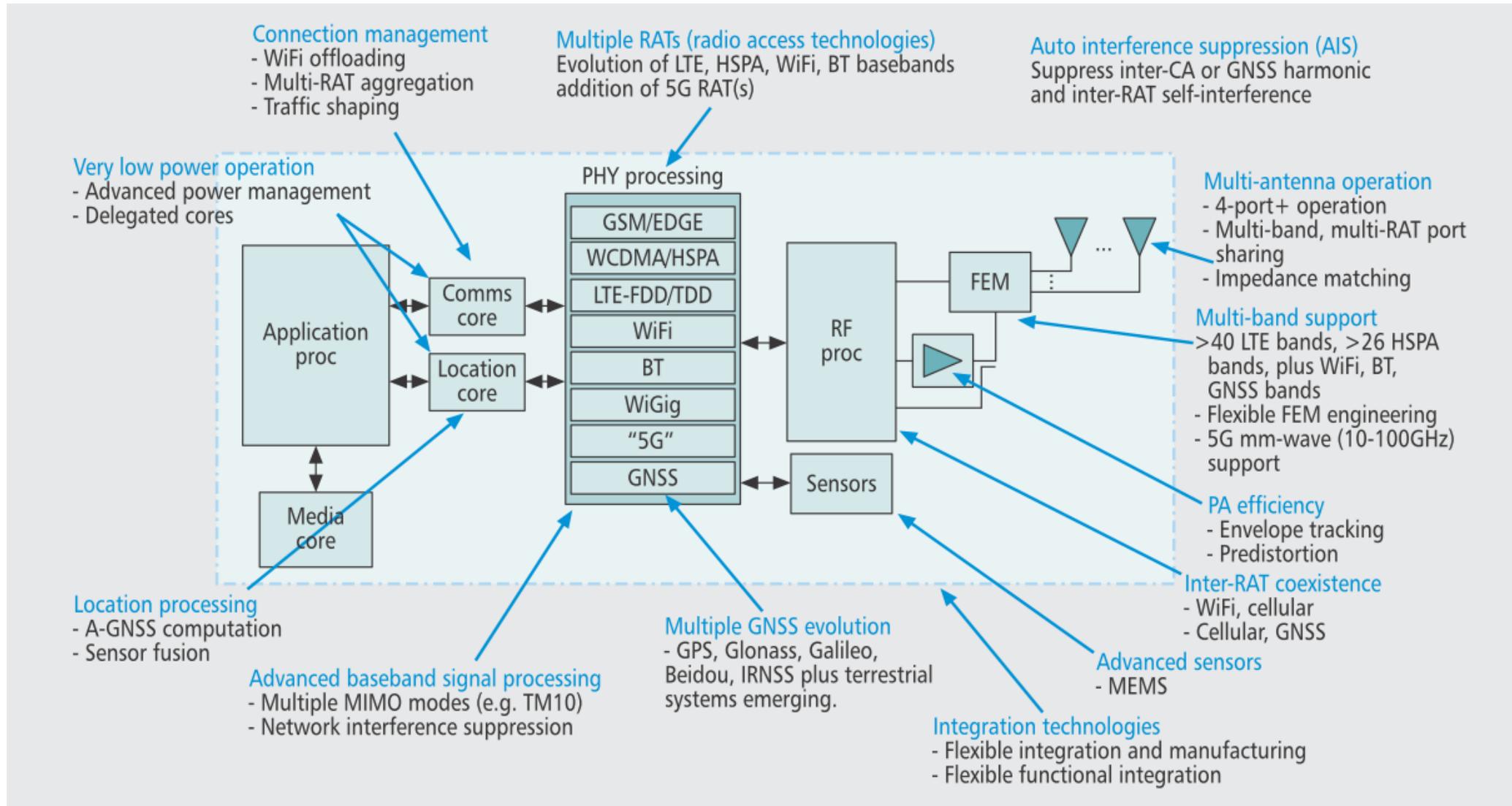
- Licensed
- Unlicensed/shared
- Existing band

Qualcomm – Global update on spectrum for 4G & 5G, April 2020

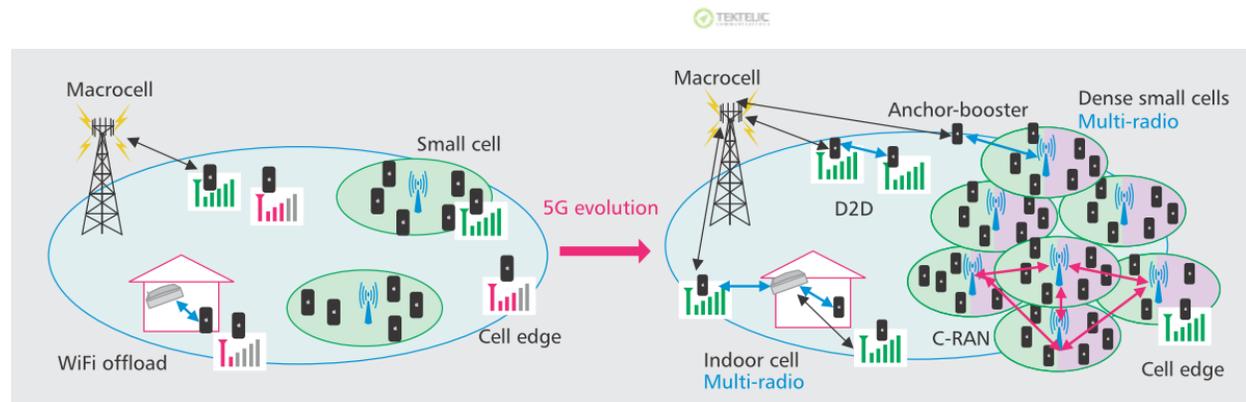
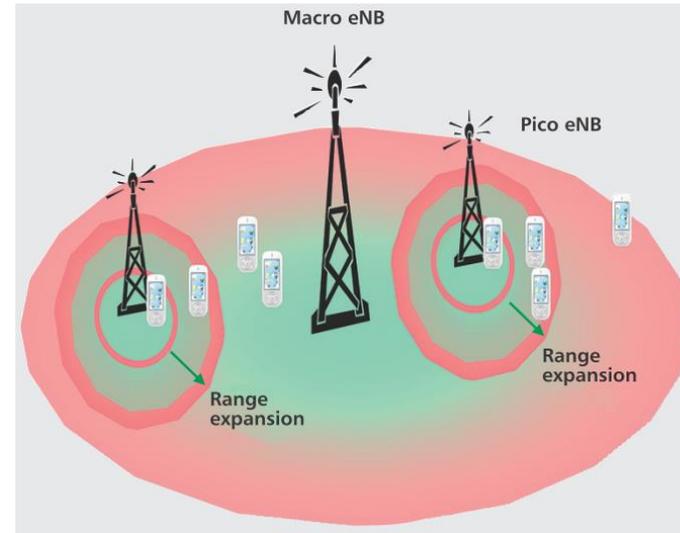
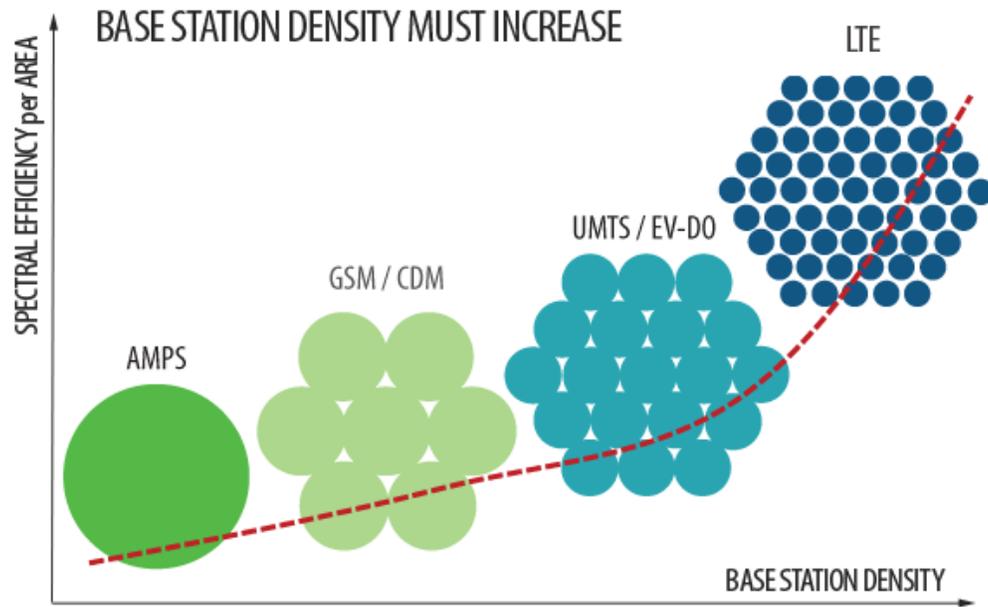
Wireless communication: 5G



Wireless communication: 5G

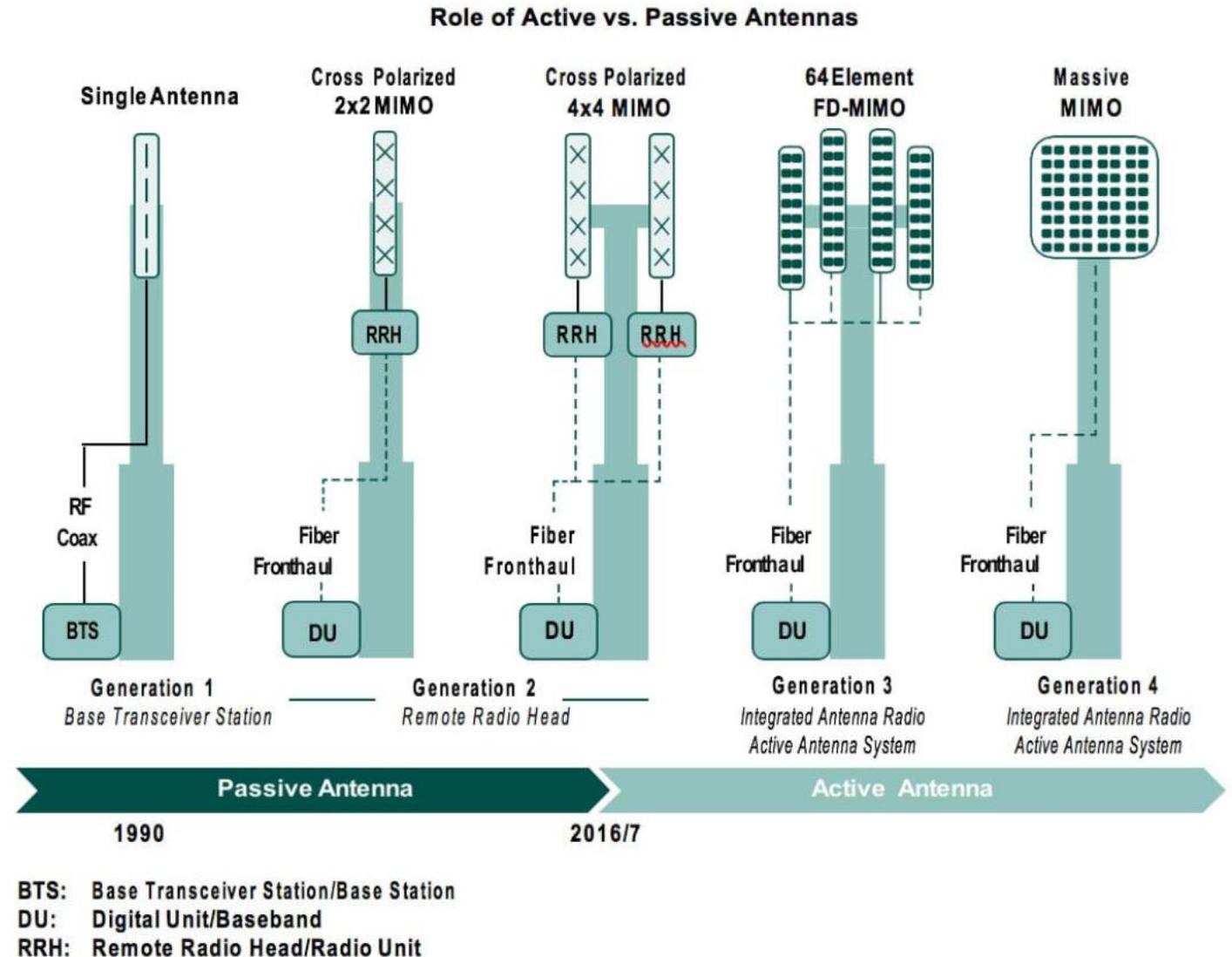


Densification/Range Extension



Cellular Base Stations (BTs)

- Three complementary initiatives:
 - Proactive cell shaping
 - Vector sectorization
 - MIMO Antennas
- An active antenna is one that has active electronic components (i.e., transistors).
- Examples of active antennas:
 - Smart antennas
 - Remote radio head antennas
 - Beamforming antennas.



Antenna arrays

$$G = \frac{4\pi A_{phys}\eta}{\lambda^2}$$

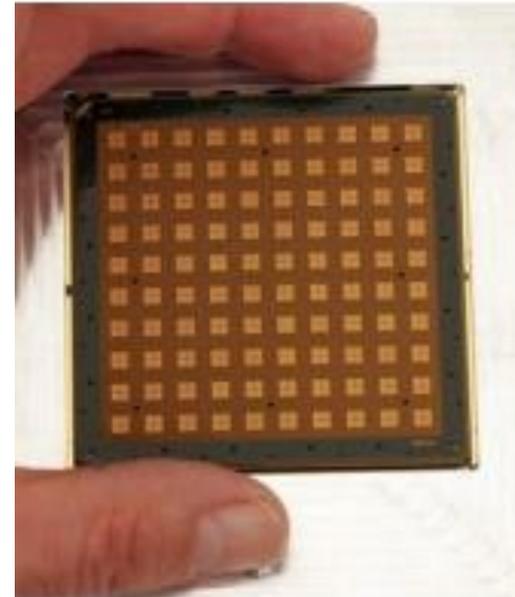
A_{phys} : Physical aperture area
 η : Aperture efficiency
 λ : Wavelength

UHF Phased Array Radar



Source: <https://www.bcpowersys.com/military-programs/uhf-phased-array-radar/>

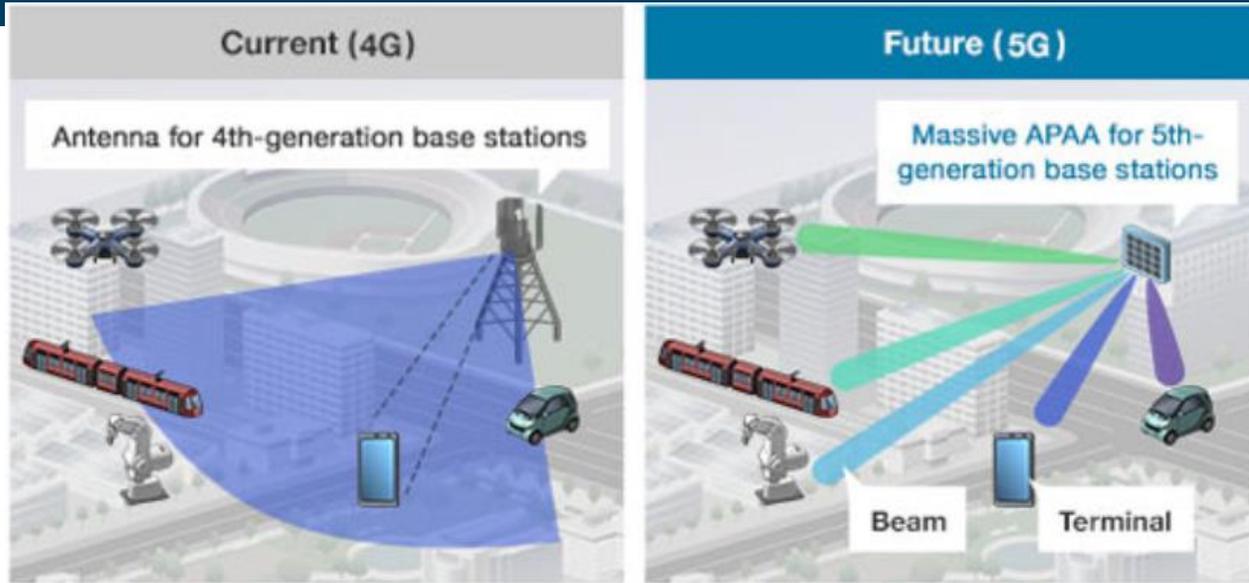
mmW Phased Array Antenna



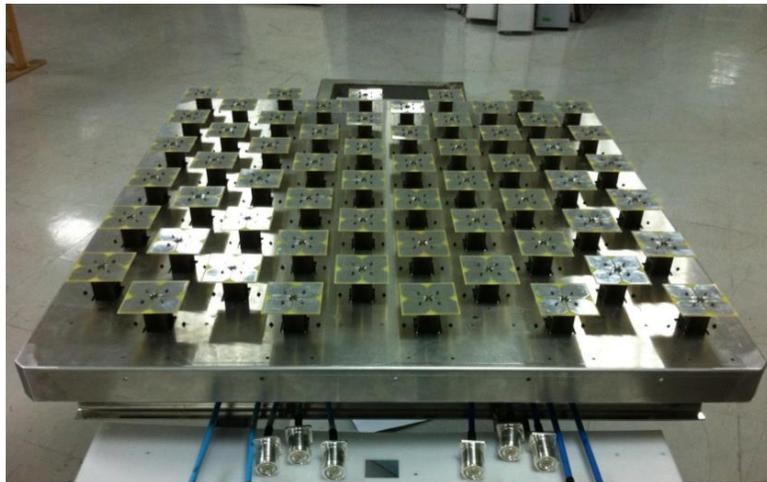
Source:

<https://www.sciencedirect.com/topics/engineering/antenna-arrays>

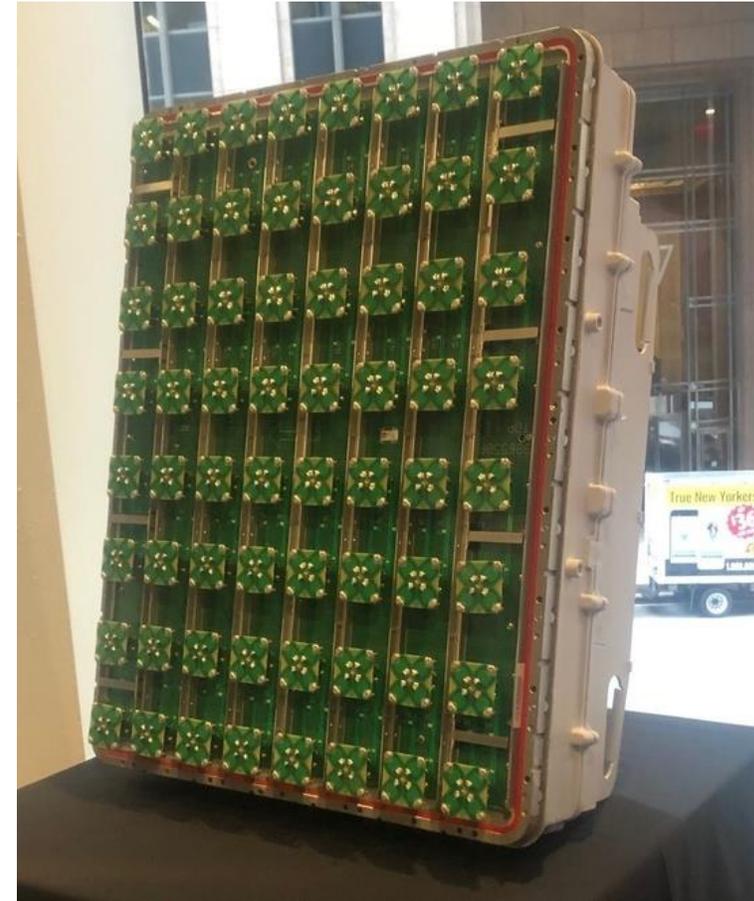
5G Antenna Arrays



Source: <https://www.mitsubishielectric.com/en/about/rd/research/highlights/communications/5g.page>



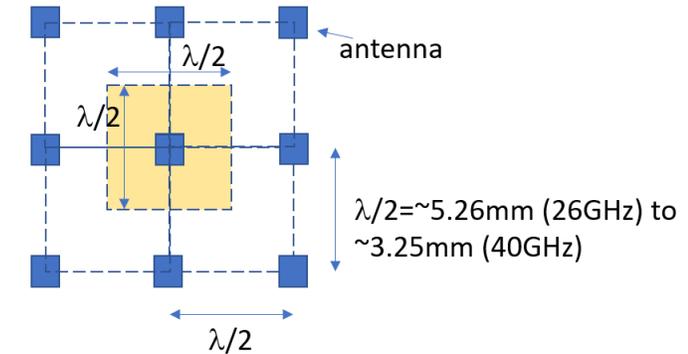
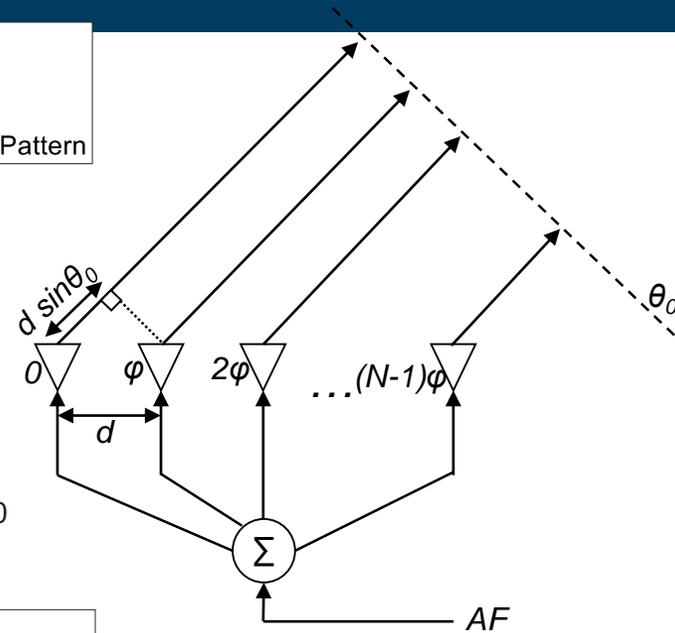
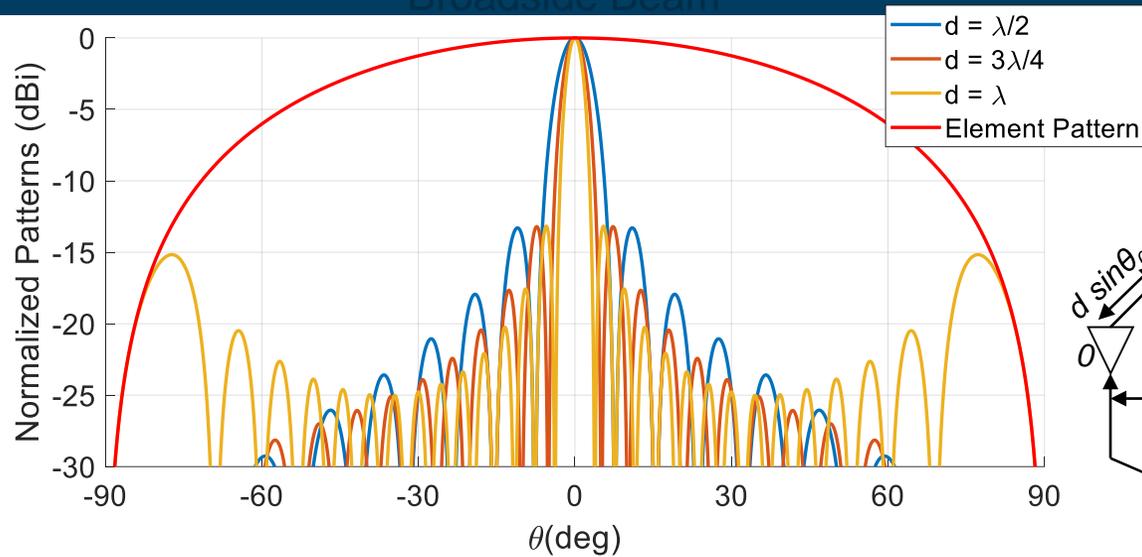
Source: https://www.engineersaustralia.org.au/sites/default/files/resource-files/2017-01/Div_Syd_techPres_advanced_cellular_base_station_antennas.pdf



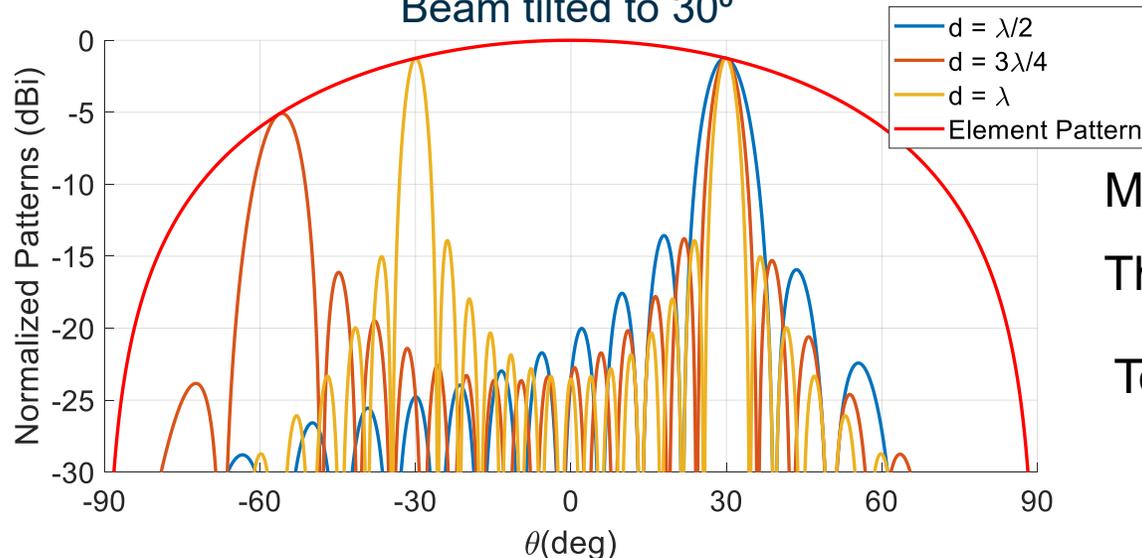
Source: *Sprint's massive-MIMO/Bevin Fletcher, FierceWireless*
<https://www.fiercewireless.com/5g/sba-says-sprint-only-carrier-it-sees-deploying-massive-mimo>

What determines the spacing between the antenna elements?

Broadside Beam



Beam tilted to 30°



$$AF = 1 + e^{j\varphi} + e^{j2\varphi} + \dots + e^{jN\varphi}, \quad \varphi = kd \sin \theta_0$$

Maximum beams occur at $\varphi = \pm n\pi \rightarrow \sin \theta_0 = \pm n\pi / kd$

These beams are in real space when $-1 < \sin \theta_0 < 1$

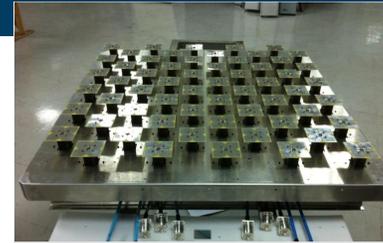
To avoid grating lobes:

$$d < \frac{\lambda}{1 + |\sin(\theta_0)|}$$

θ_0 is the beam angle

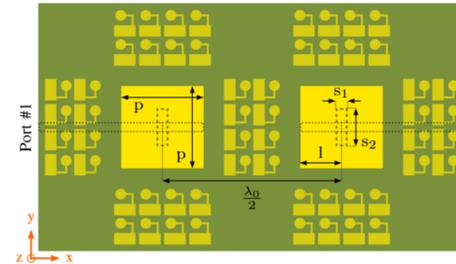
Phased arrays / Beamforming

- Ultra-wideband base station antennas
- High dense antenna arrays
- Phased array calibration
- Beamforming and beam management

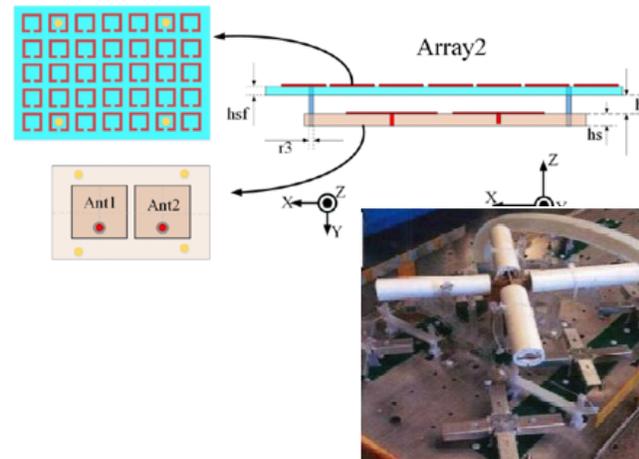


Source:

https://www.engineersaustralia.org.au/sites/default/files/resource-files/2017-01/Div_Syd_techPres_advanced_cellular_base_station_antennas.pdf



A. Stark, "Buried EBG Structures for Antenna Array Applications," Proceedings of the 40th European Microwave Conference, 2010

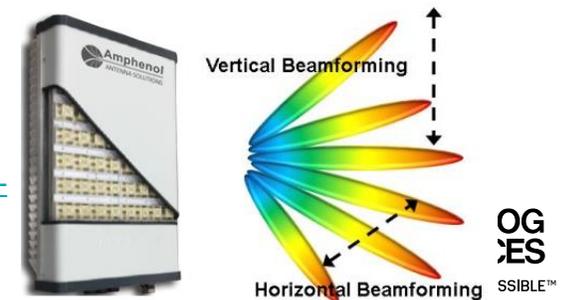


Z. Wang et al, "A meta-surface antenna array decoupling (MAAD) method for mutual coupling reduction in a MIMO antenna system," Scientific Report, Feb. 2018

Roy Butler et al, "Broadband multiband phased array antennas for cellular communications," ISAP, 2016

Source:

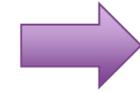
<https://amphenol-antennas.com/news-2/10020-2-4/>



Phased array system evolution

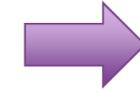
Classical

- ▶ All Analog Beamforming
- ▶ Centralized Receivers & Exciters
 - ▶ Low electronics content:



Hybrid Solution

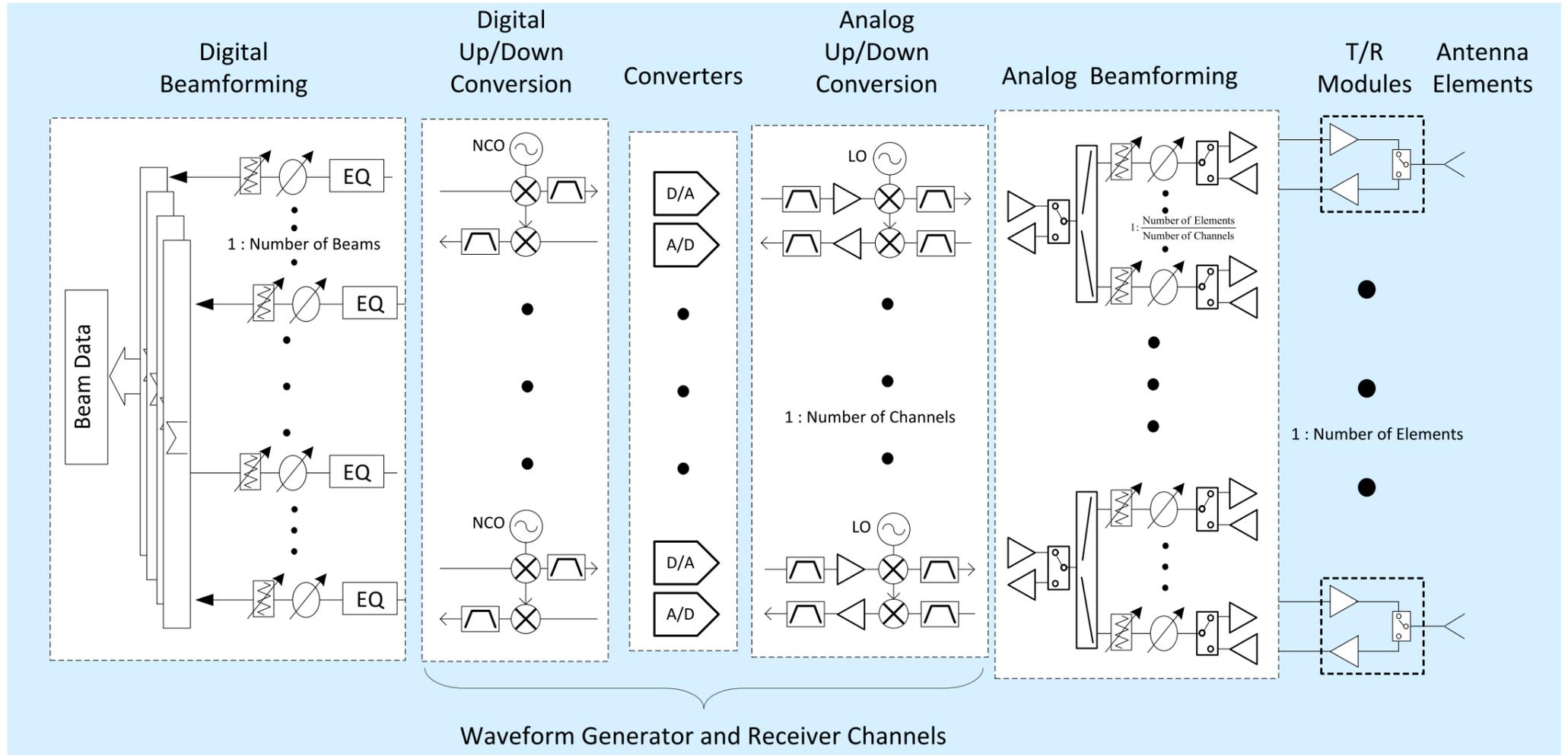
- ▶ Sub-array Architecture
 - ▶ Analog/Digital Beamforming
- ▶ Distributed Receivers & Exciters
 - ▶ At Subarray Level



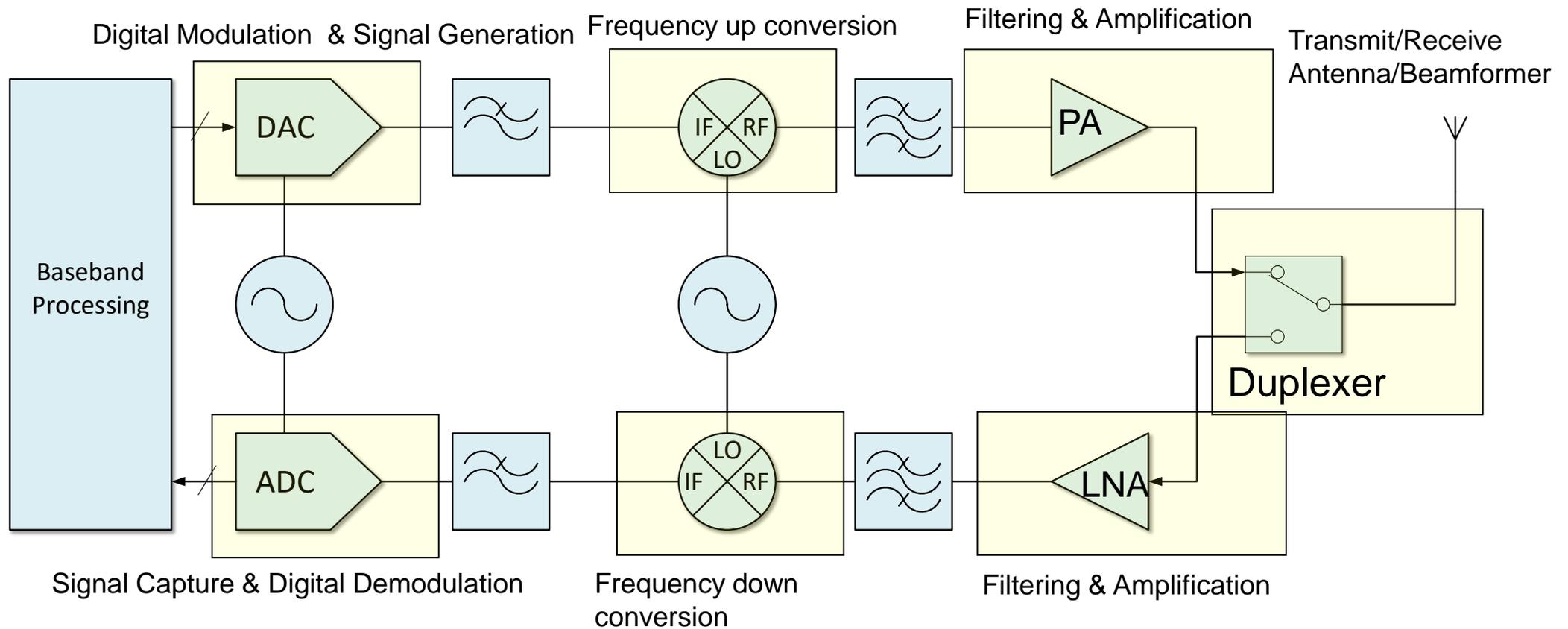
All Digital

- ▶ Every Element Digital Beamforming
 - ▶ No Analog Beamforming
- ▶ Distributed Receivers & Exciters
 - ▶ At a per element level

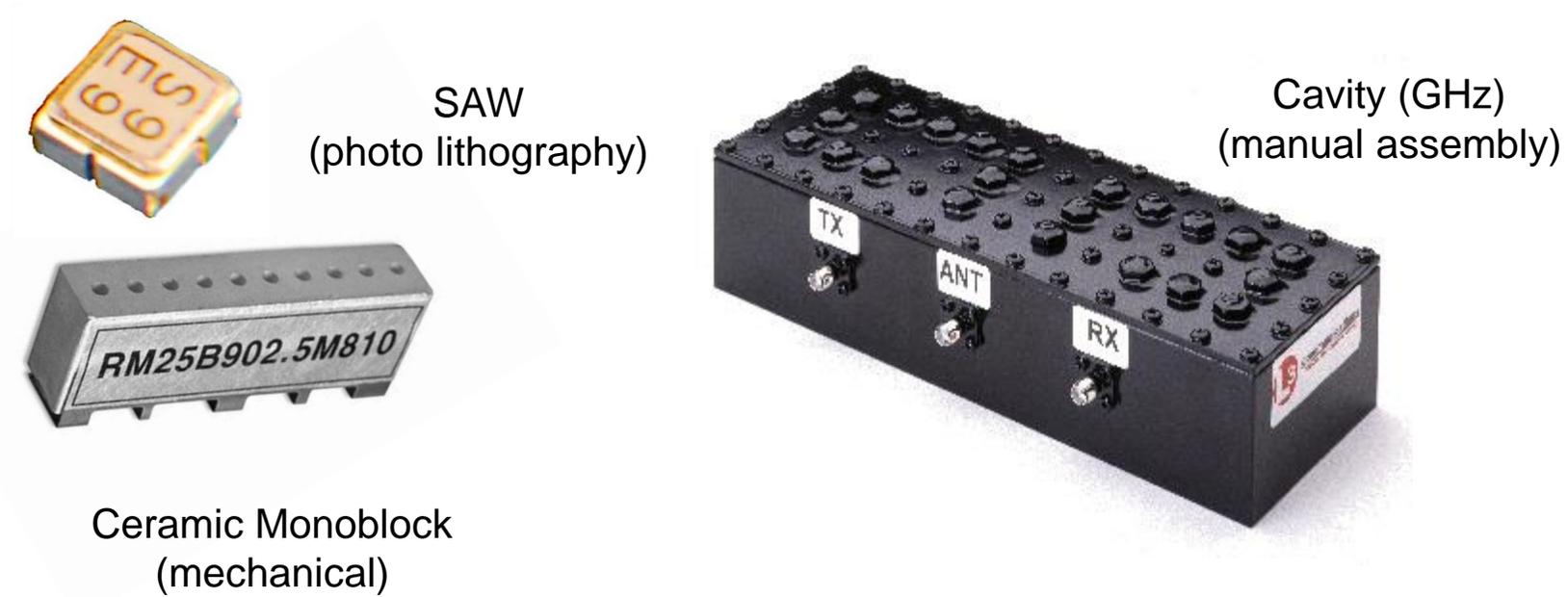
Generic beamforming phased array system signal chain



T/R signal chain (simplified)



The \$\$ stuff that does not want to scale: duplexer & other filters

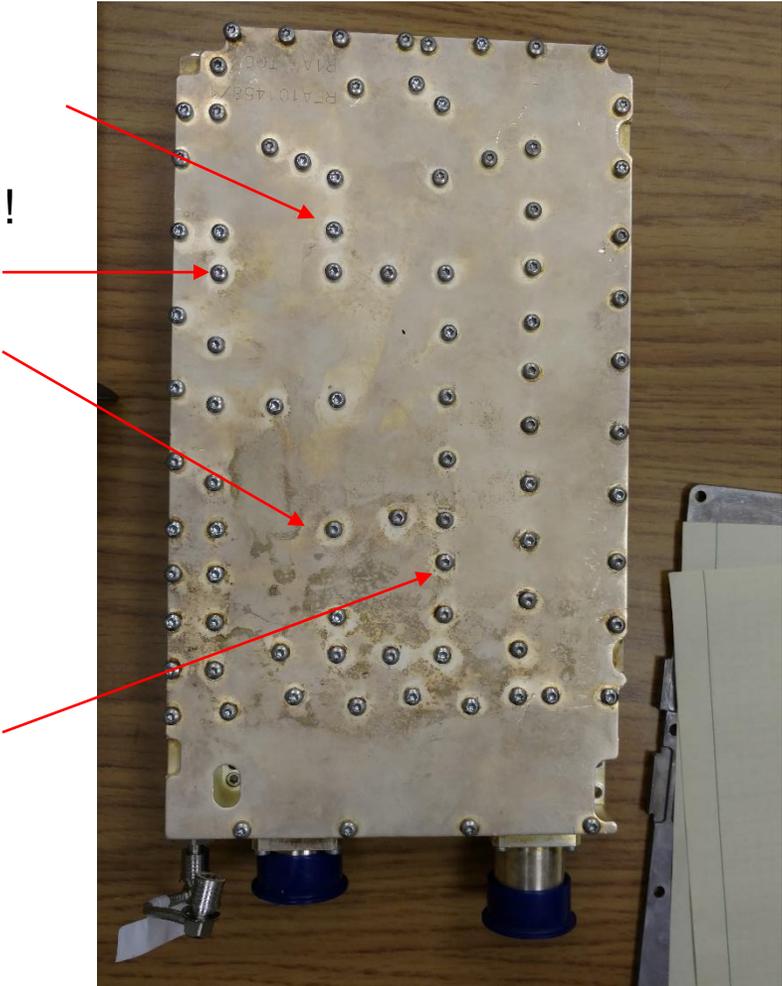


$$\text{size} \propto \text{performance} \quad \text{size} \propto \frac{1}{\text{frequency}}$$

$$\text{cost} \propto \text{size}$$

An actual BTS's duplexer

Tuning
screws!!!



An actual power amplifier

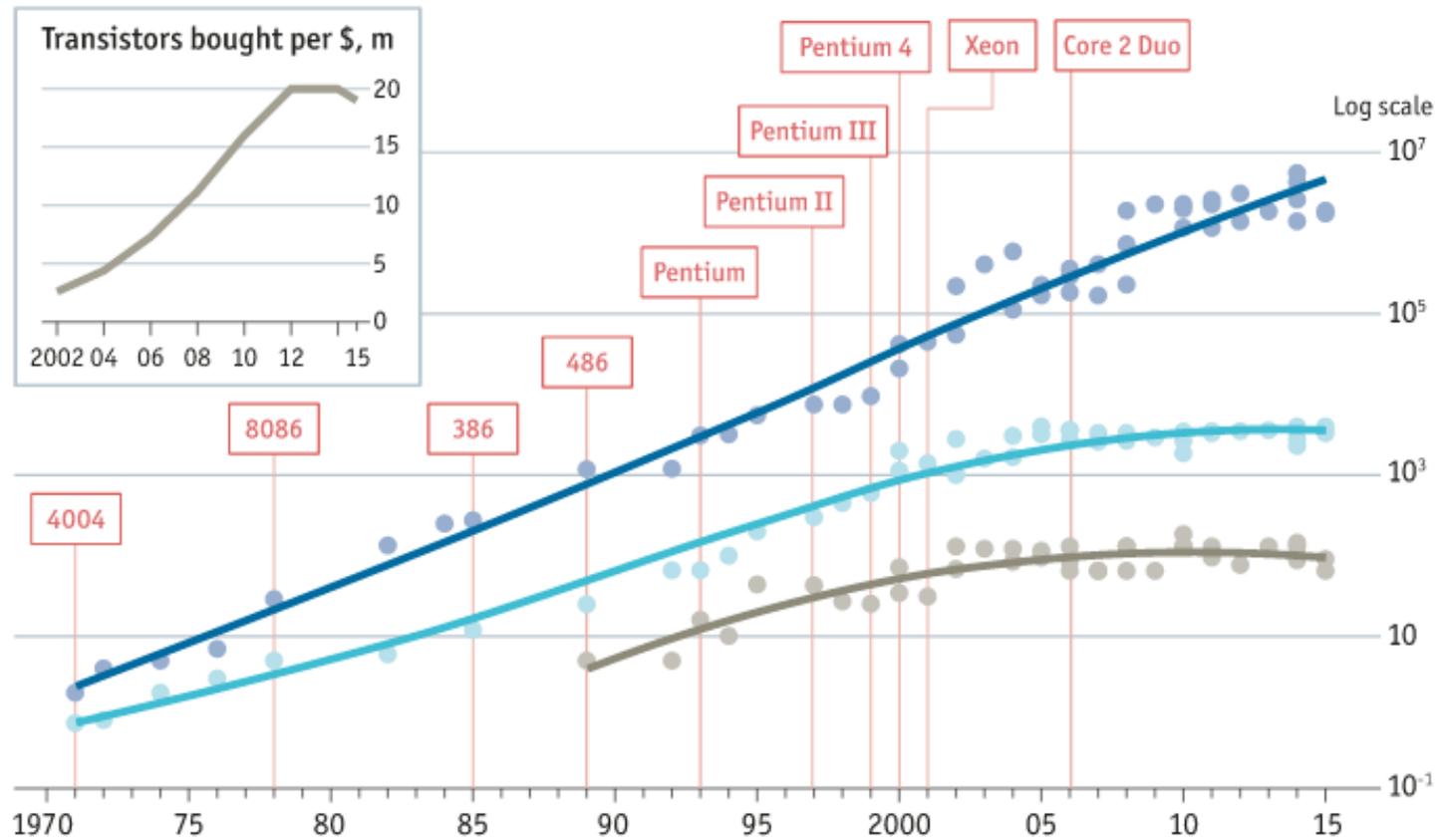


Process Technology

Moore's law

Stuttering

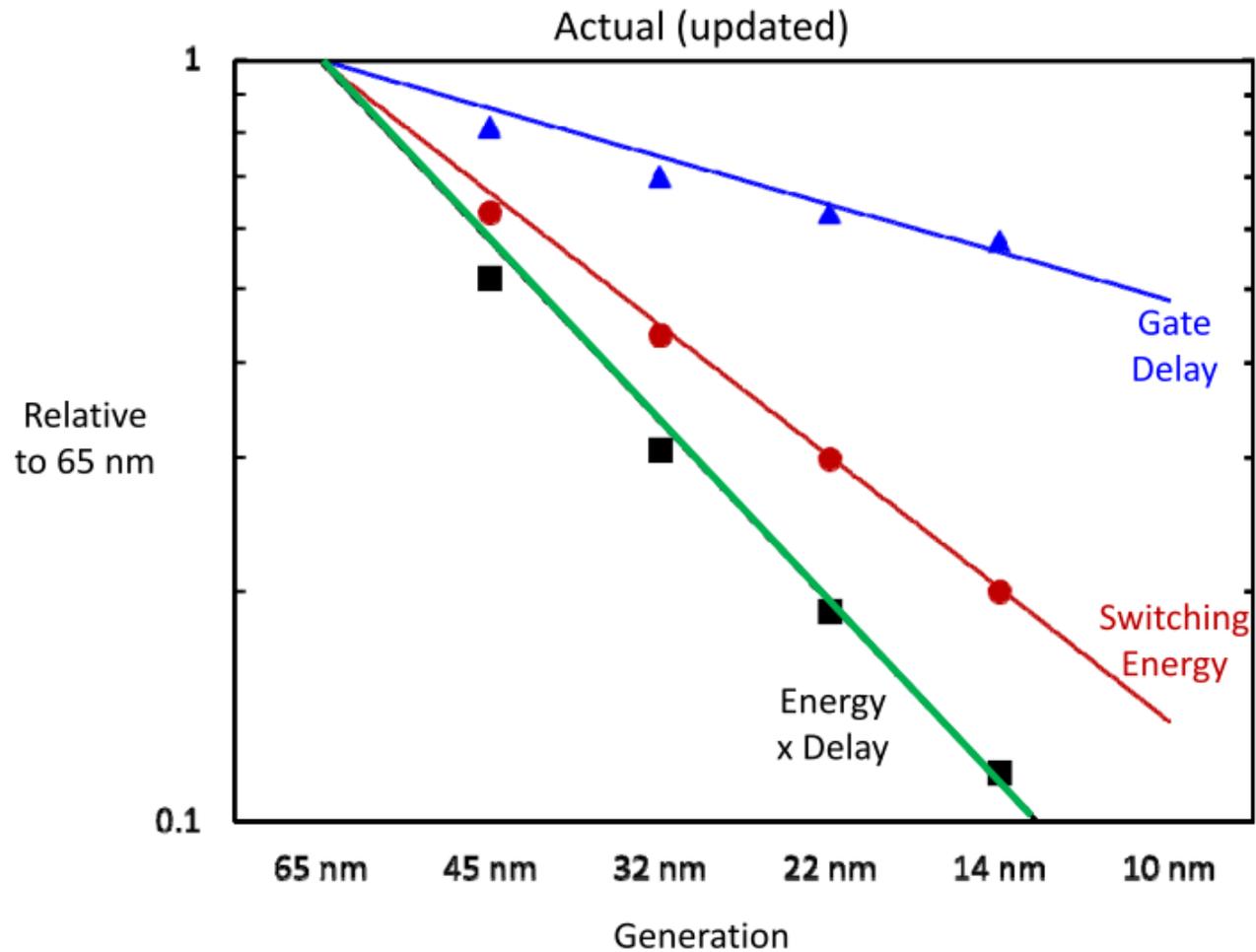
● Transistors per chip, '000 ● Clock speed (max), MHz ● Thermal design power*, w □ Chip introduction dates, selected



Sources: Intel; press reports; Bob Colwell; Linley Group; IB Consulting; *The Economist*

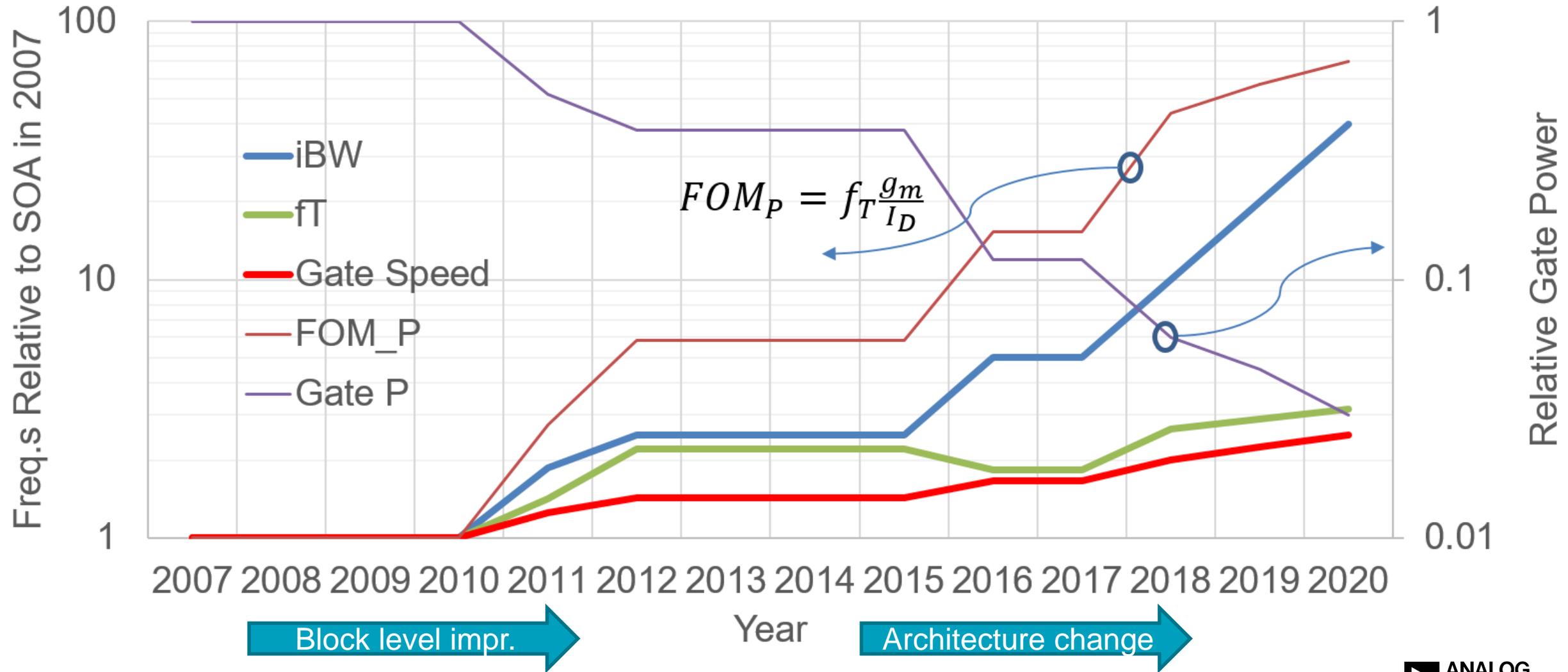
*Maximum safe power consumption

Higher digital power efficiency, but not (much) higher device speed!

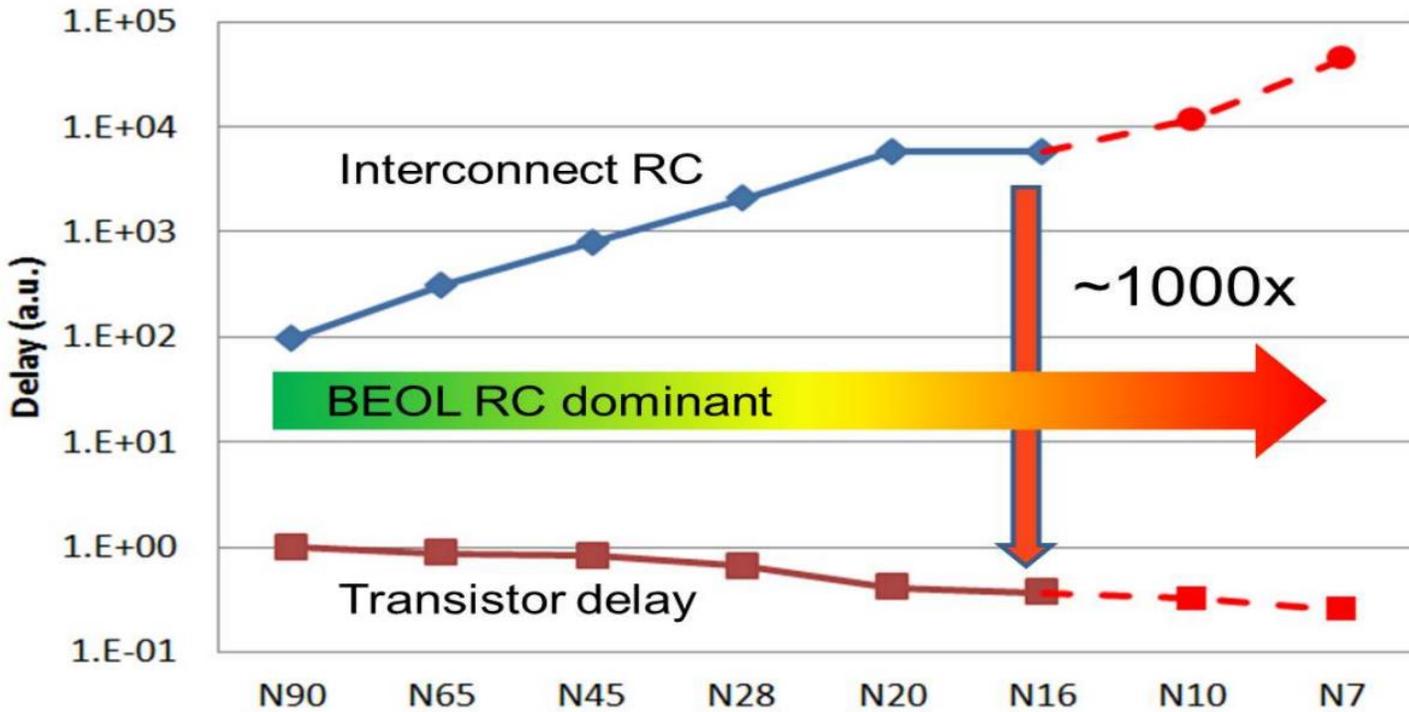


Source: W.M.Holt, “Moore’s Law: A path going forward”, ISSCC 2016

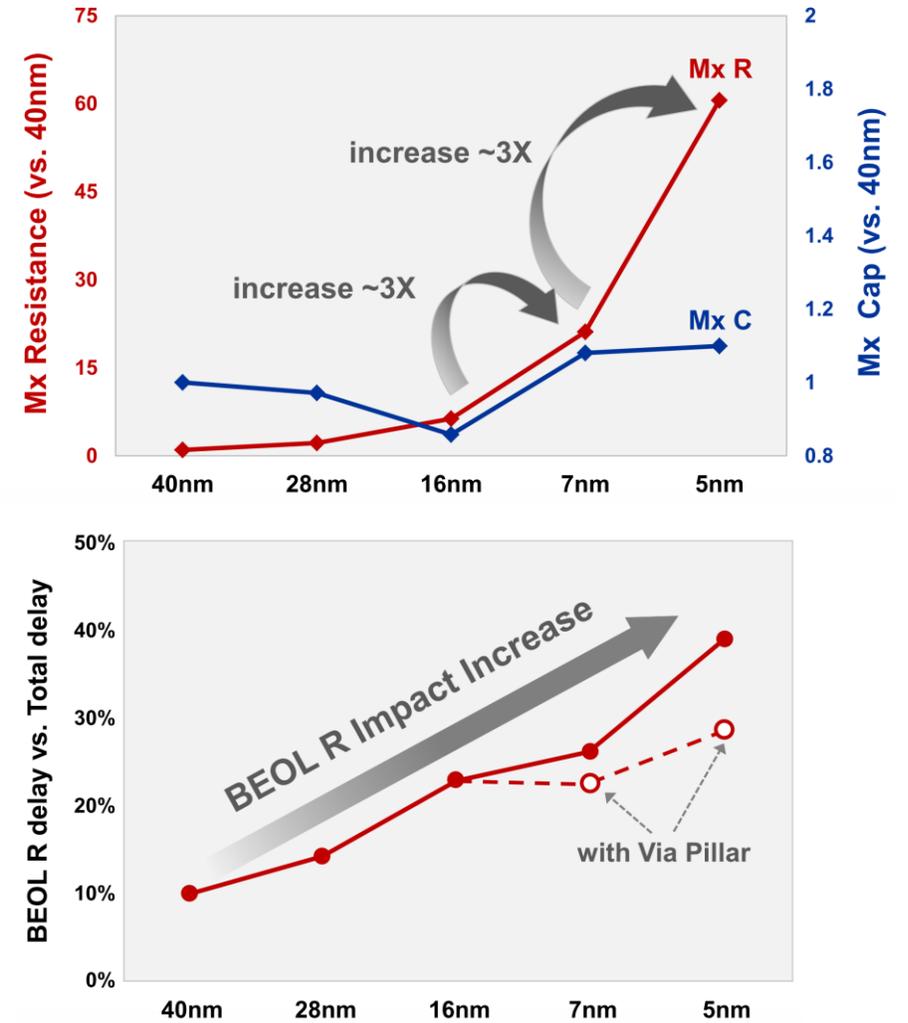
Application pull: Wireless Infrastructure (BTS) bandwidth demand versus MS CMOS capability



Die interconnects are the biggest bottleneck



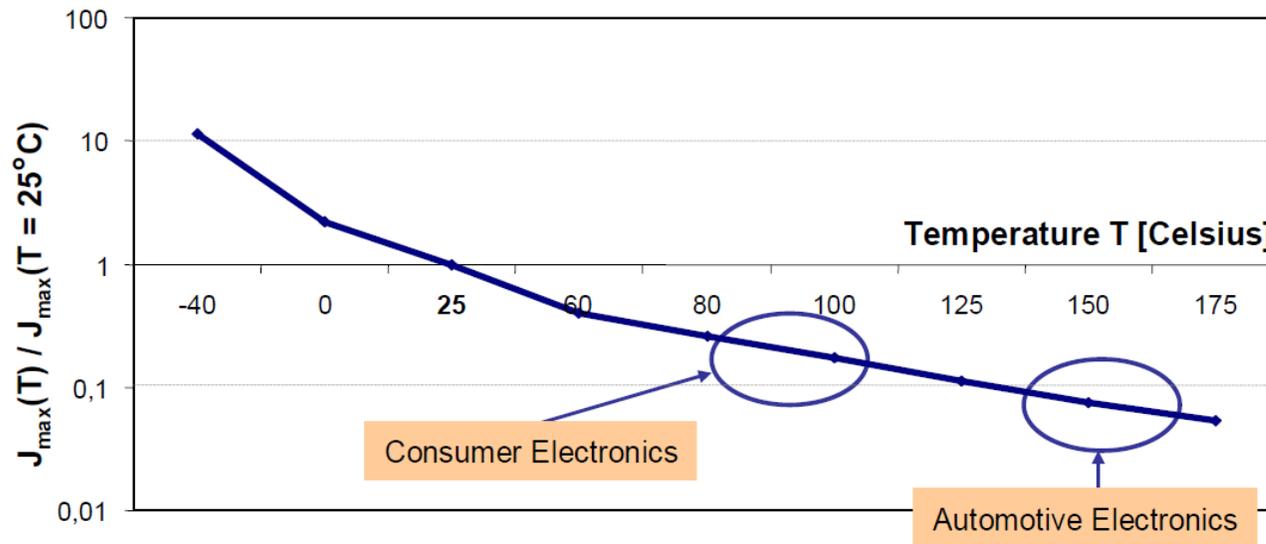
Source: G. Yeap (Qualcomm), IEEE Electron Devices Meeting (IEDM), 2013



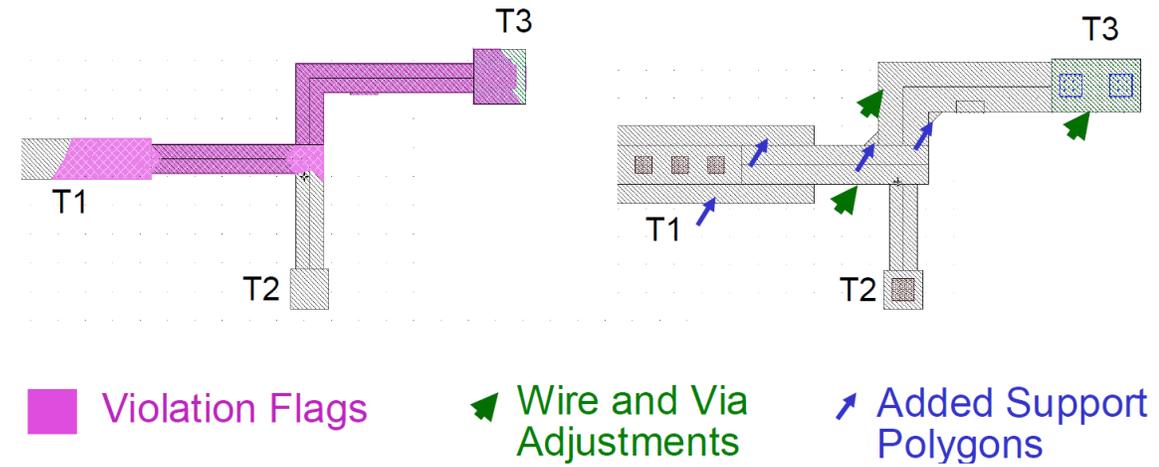
C. Hou (TSMC), ISSCC 2017 & L. Lu (TSMC), ISPD 2017

Electromigration

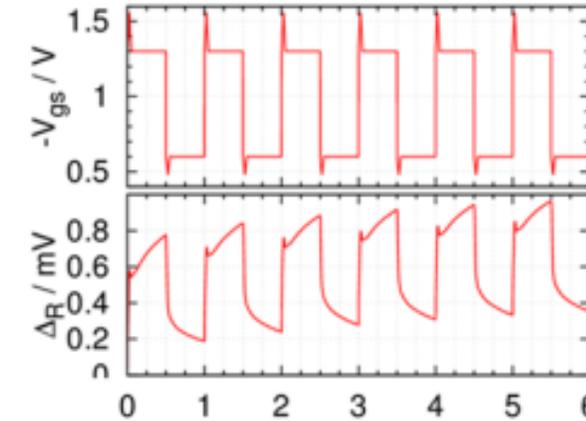
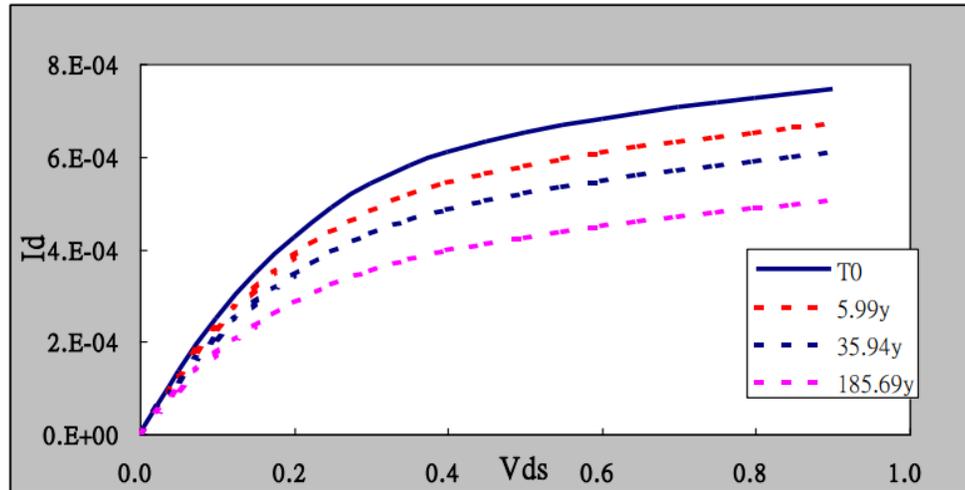
$J_{\max}(T)$ compared to $J_{\max}(T_{\text{ref}} = 25^\circ\text{C})$ [1]



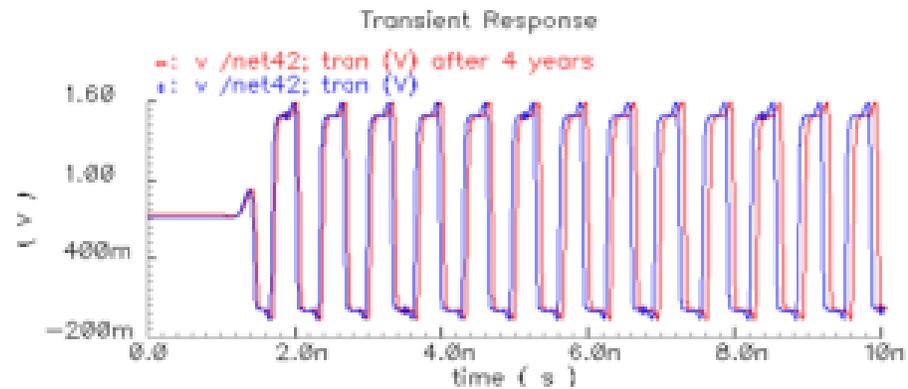
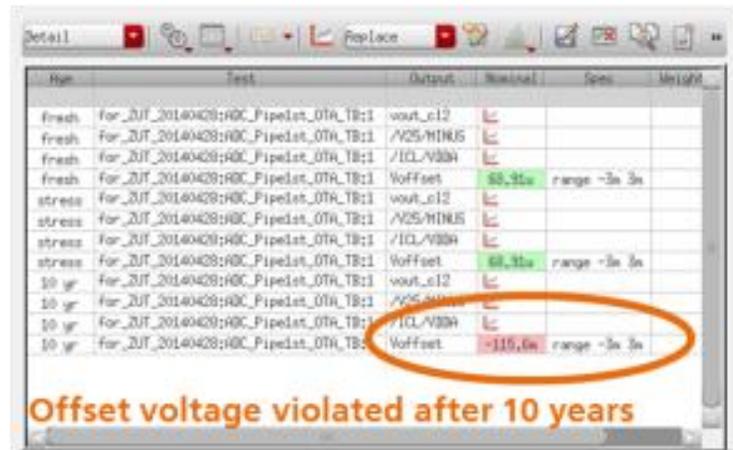
The maximum permissible current density of an aluminum metallization, calculated at e.g. 25°C, is reduced significantly when the temperature of the interconnect rises



Device Aging

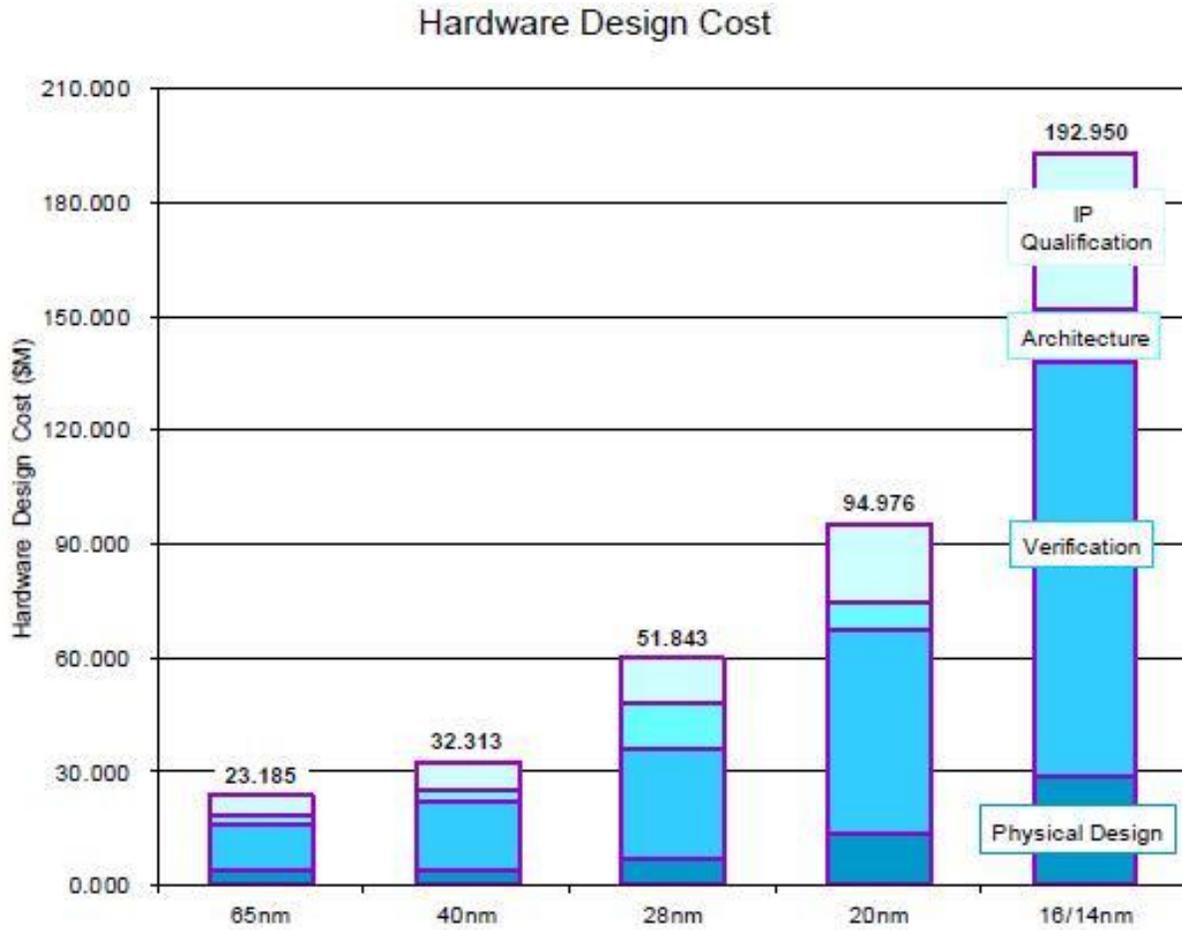


V_t shift due to NBTI degradation



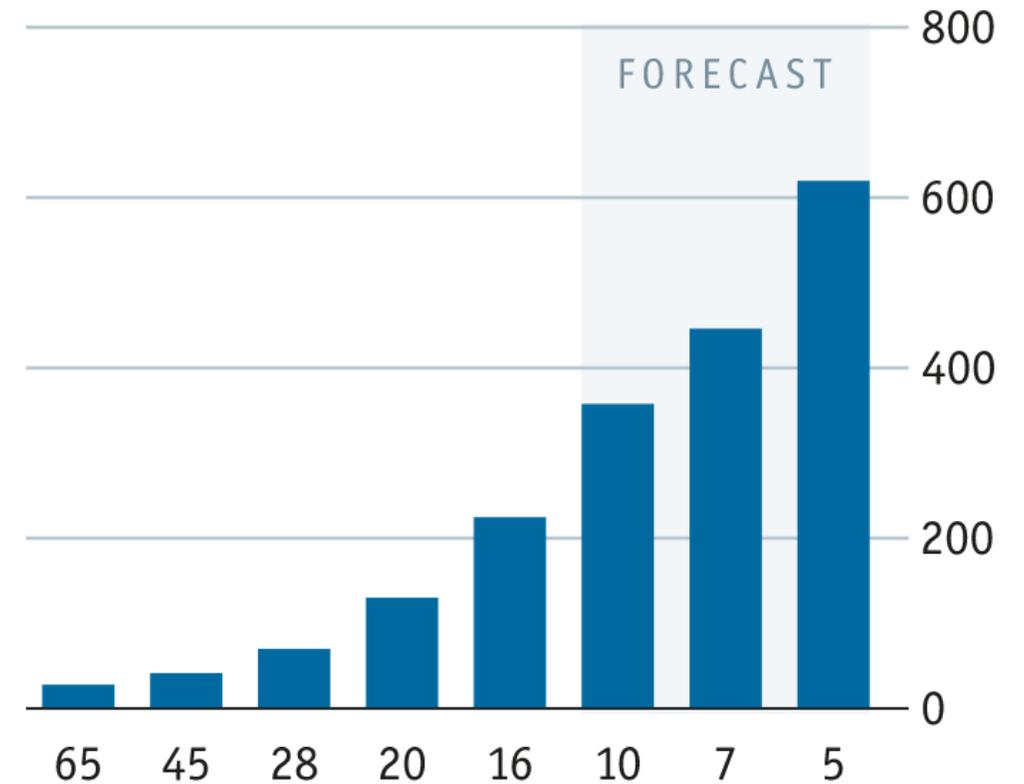
Frequency shift after 4 years of op.

Complexity drives development cost



Source: International Business Strategies, Inc 2013 report

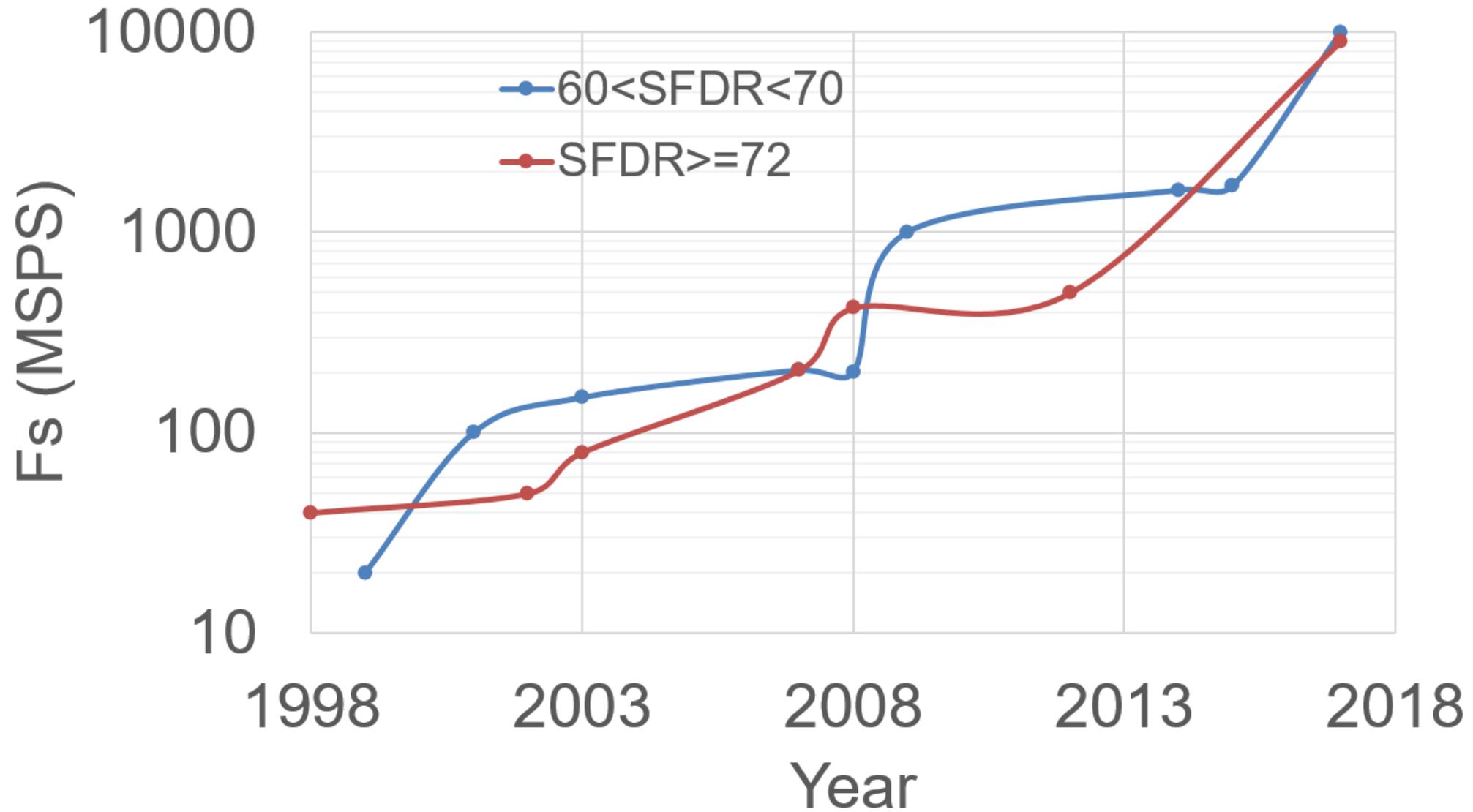
Design cost by chip component size in nm, \$m



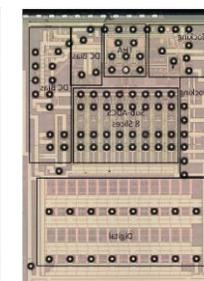
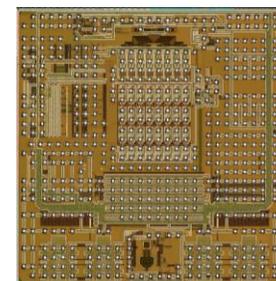
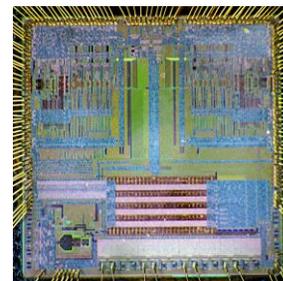
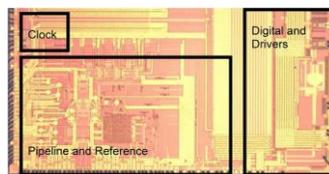
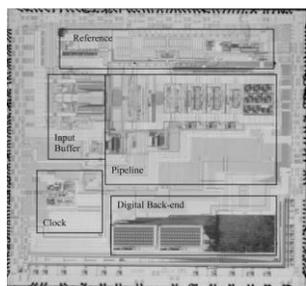
Source: IB Consulting

ADC architectures

Technology progression: 12b/14b High Speed (HS) ADC progression



Evolution of high-speed A/Ds at ADI (see ISSCC papers)



2006 2007 2008 2009 2010 2011 2012 2013 2014 2015 2016 2017 2018 2019 2020

14b/125MSPS

16b/250MSPS

14b/1.25GSPS

14b/3GSPS

12b/10GSPS

12b/18GSPS

0.35u BiCMOS

0.18u BiCMOS

65nm CMOS

28nm CMOS

28nm CMOS

16nm FinFET

85%A/15%D

80%A/20%D

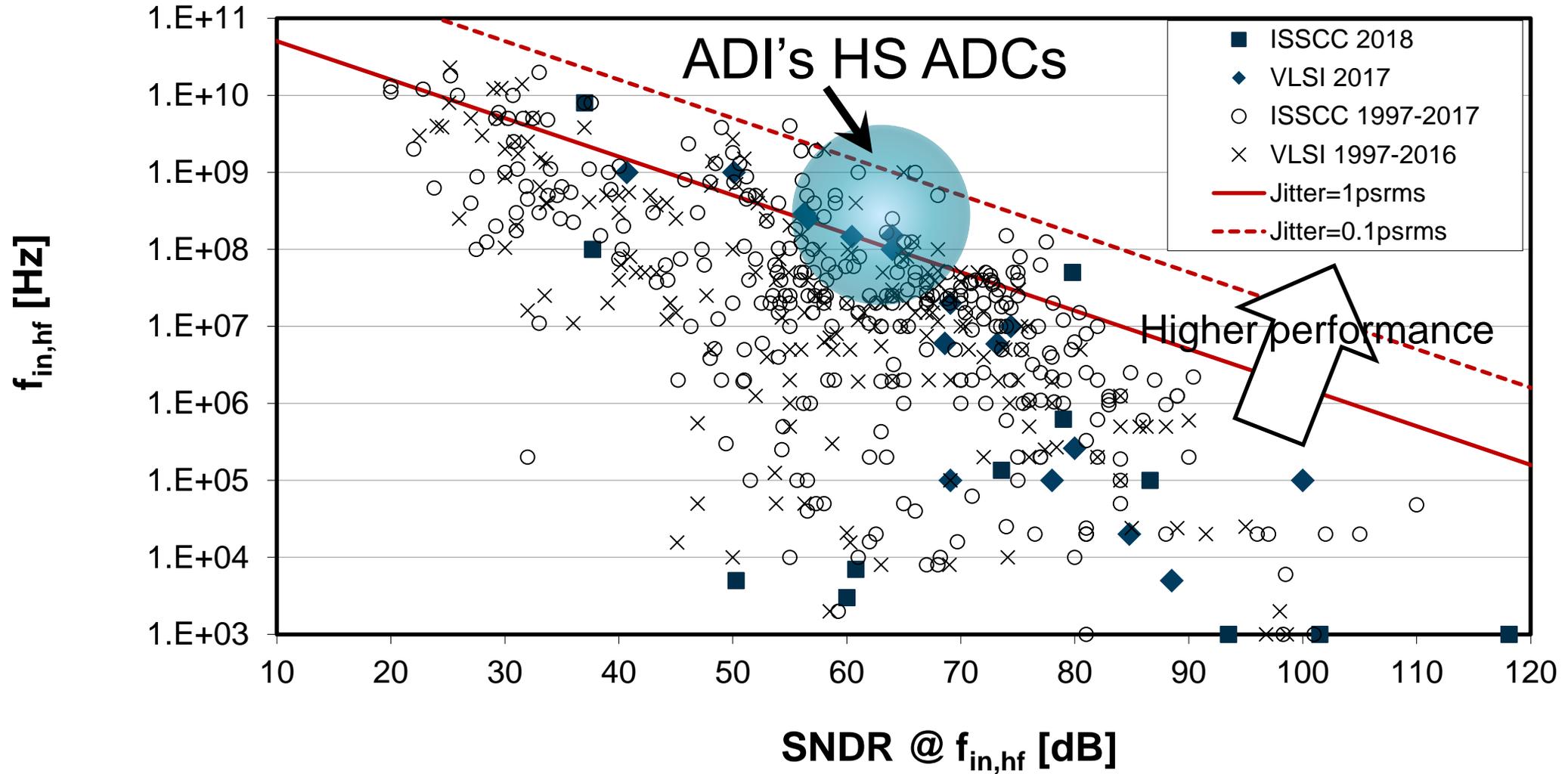
75%A/25%D

70%A/30%D

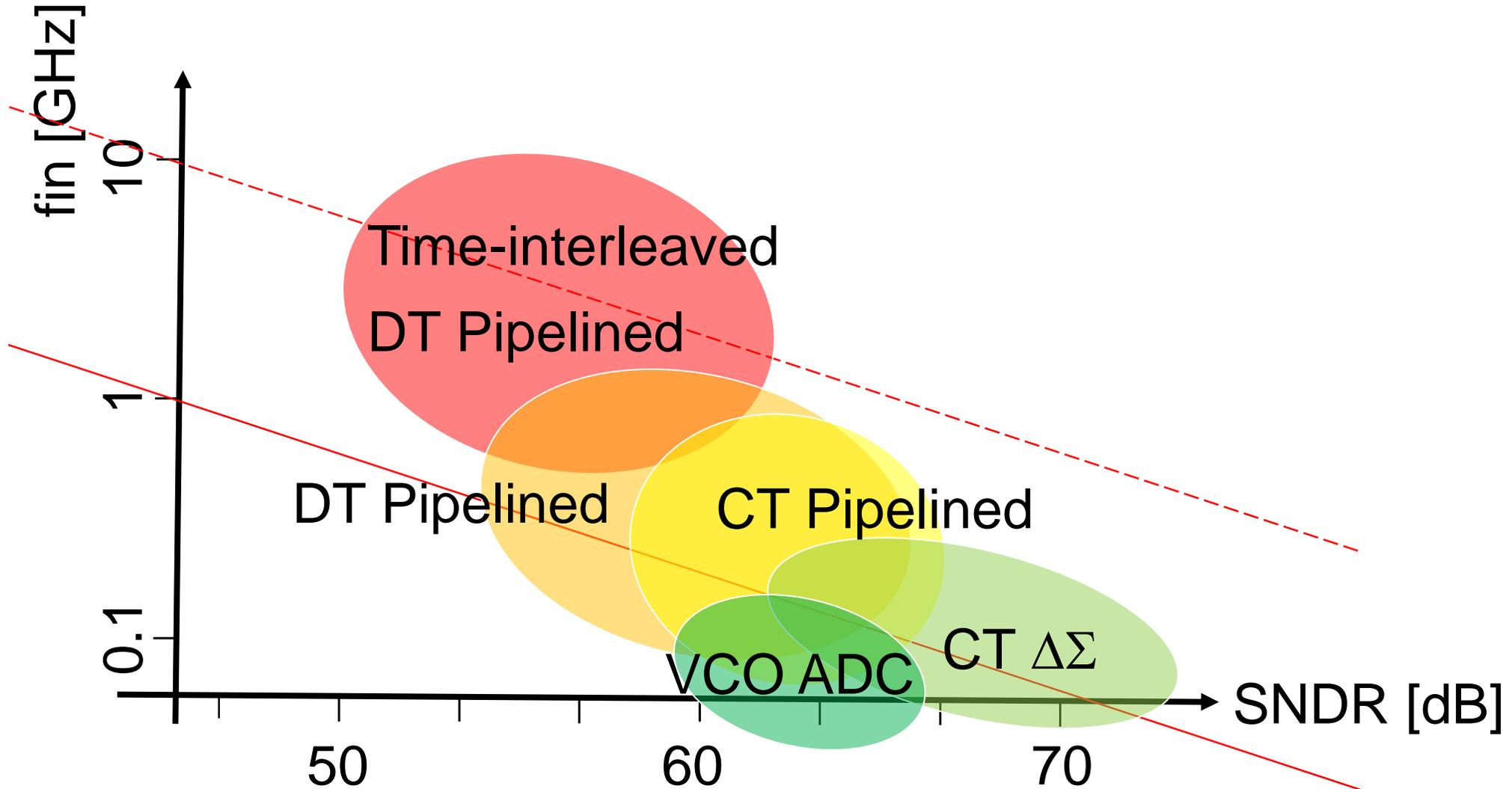
60%A/40%D

40%A/60%D

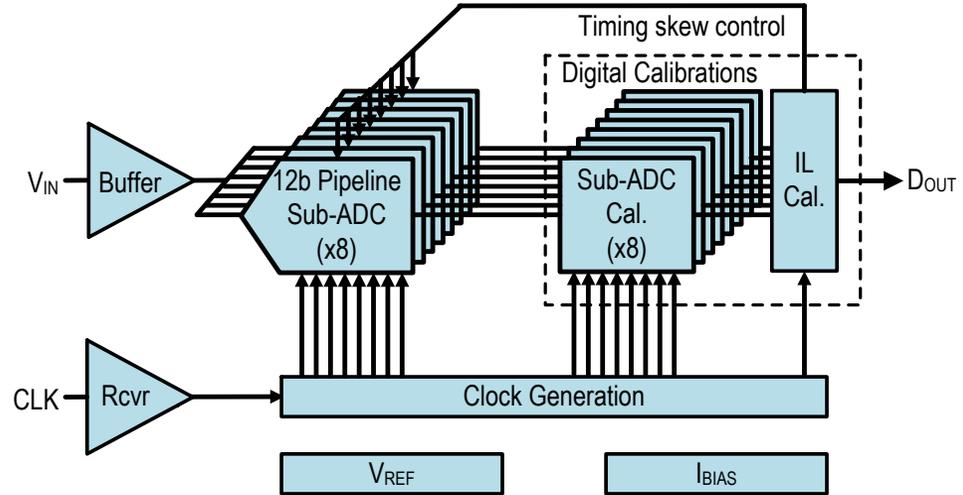
Architectures (no one fits all): ADC “Aperture plot” (i.e. Bandwidth vs. Dyn Range or sample rate vs. resolution)



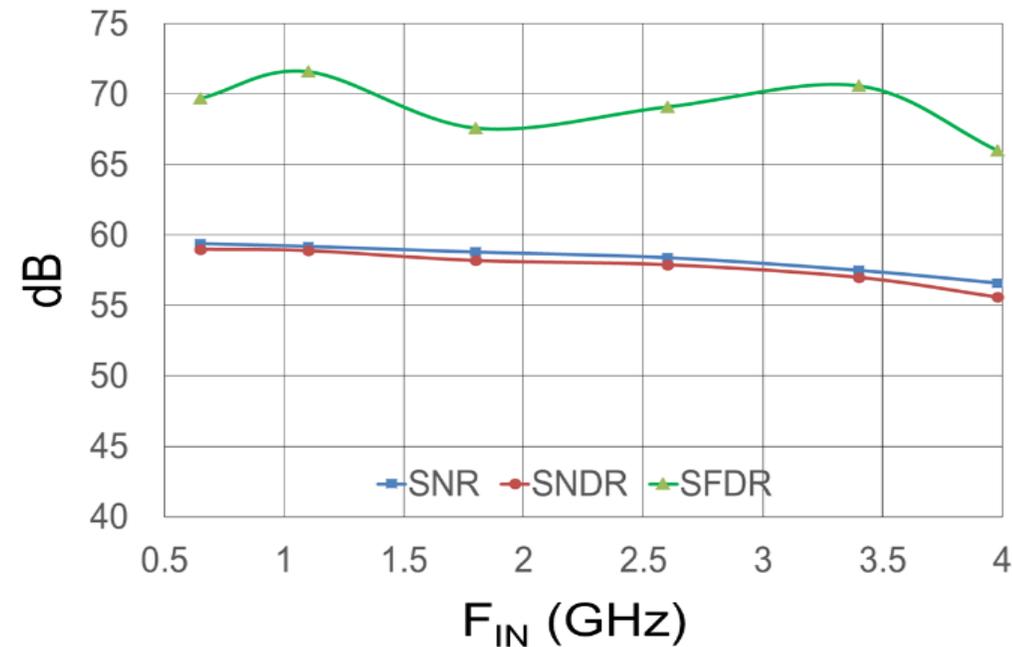
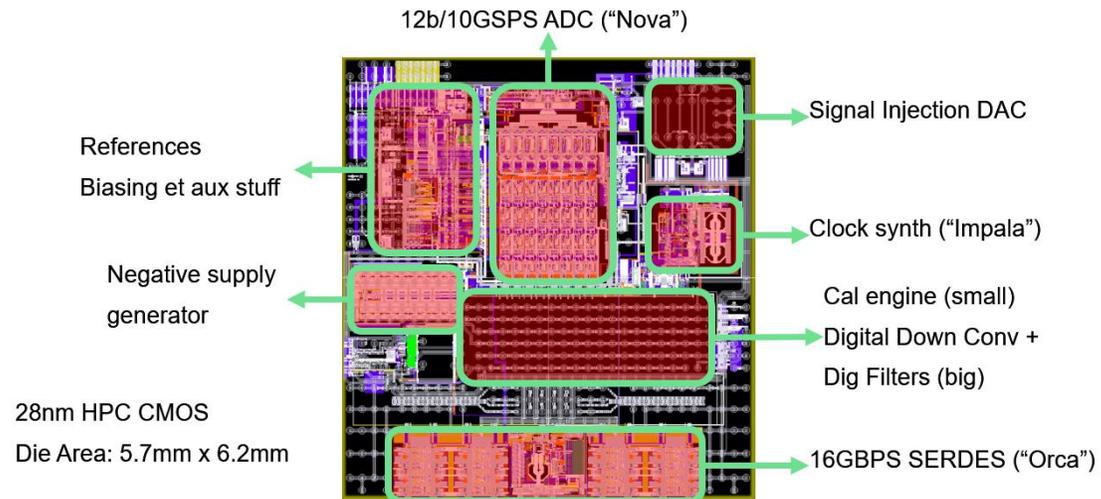
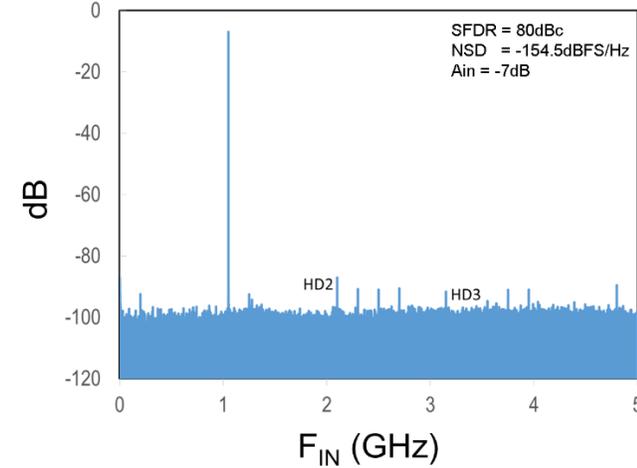
ADI's ADC architectures: one cannot fit all



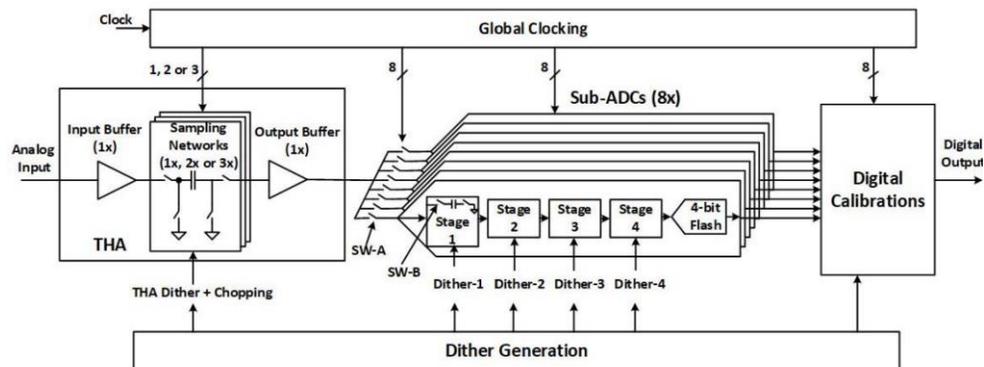
12b/10GSPS ADC: 8x interleaved Analog to Digital converter



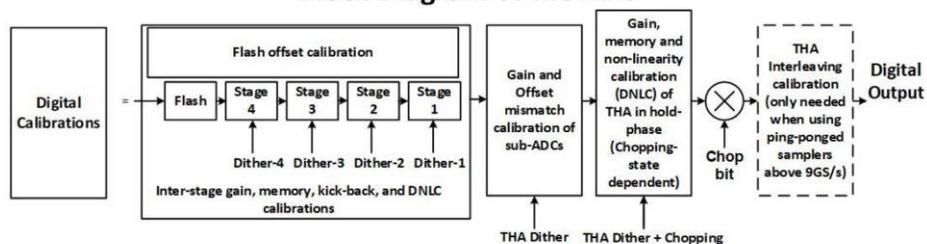
Resolution	12b
F_{SAMPLE}	10GS/s
SNR	56dB
SNDR	55dB
SFDR	66dB
Input fin	4GHz
Power	2.9W
FOMS_HF	147dB
BW	7.4GHz
DR	60dB
NSD_{small-signal}	-157dBFS/Hz
Technology	28nm



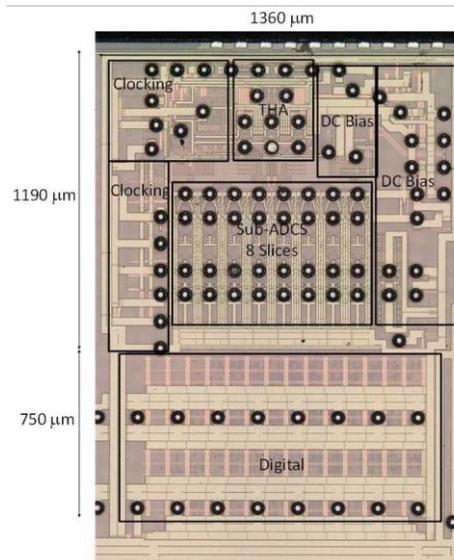
12b/18GSPS ADC: 8x interleaved Analog to Digital converter



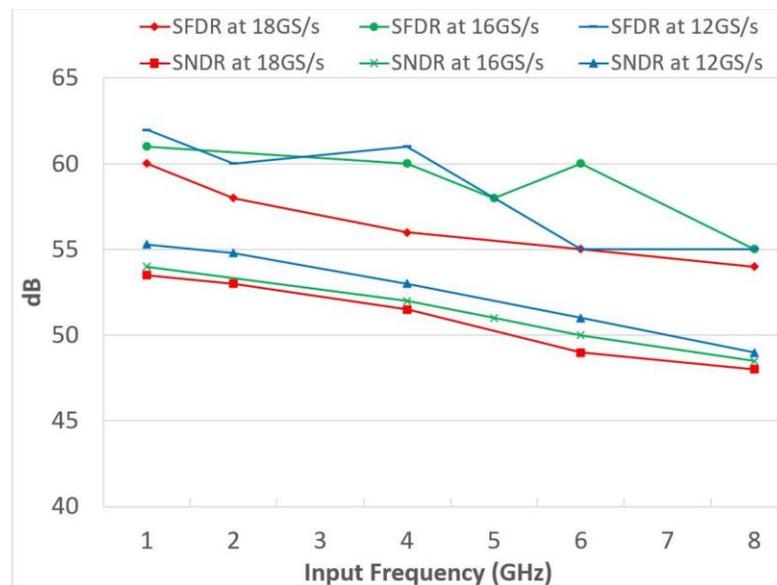
Block Diagram of the ADC



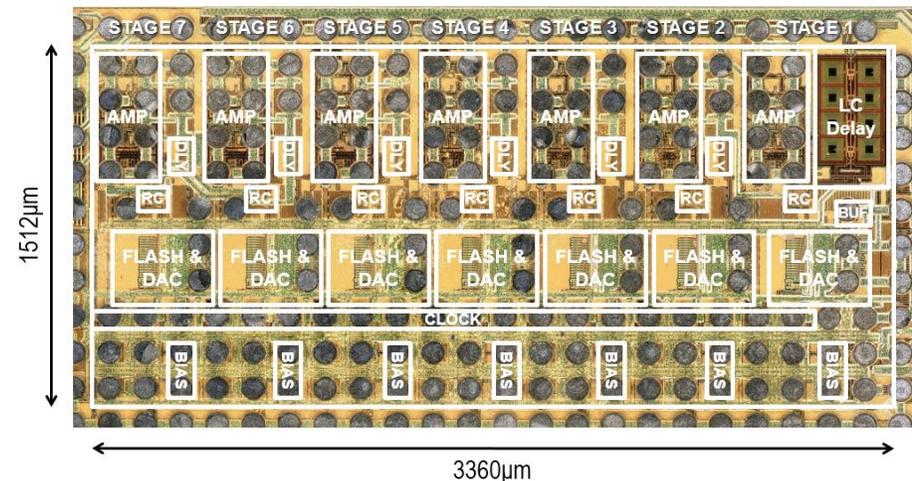
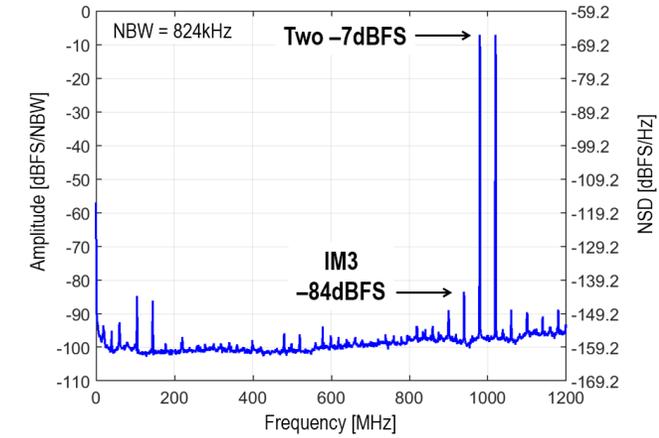
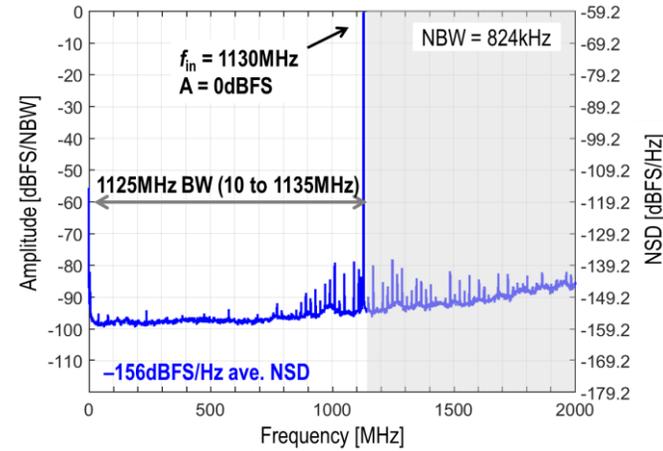
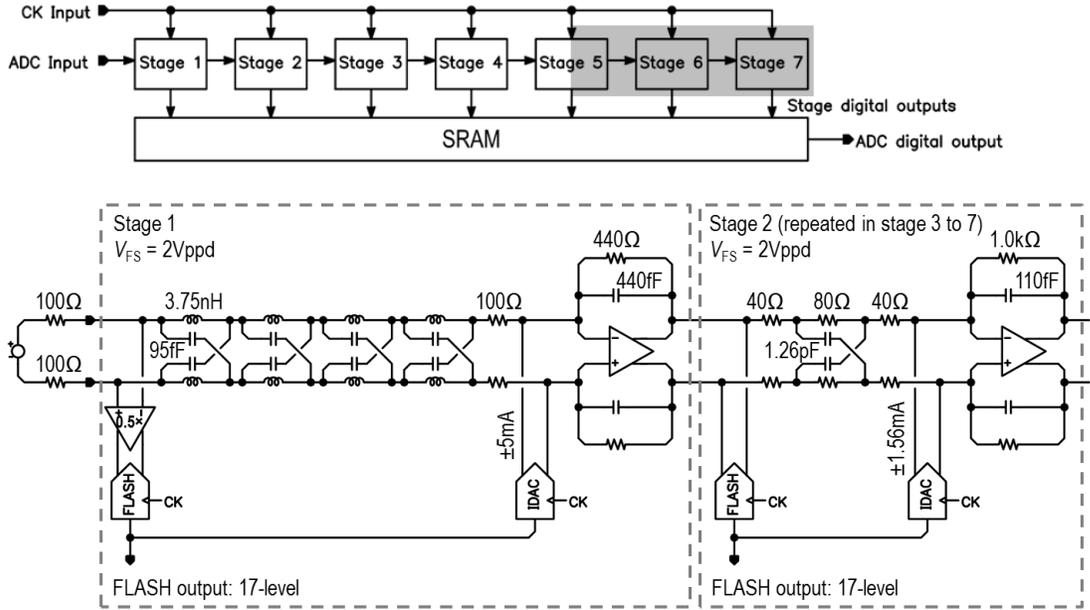
Block Diagram of the Digital Calibrations



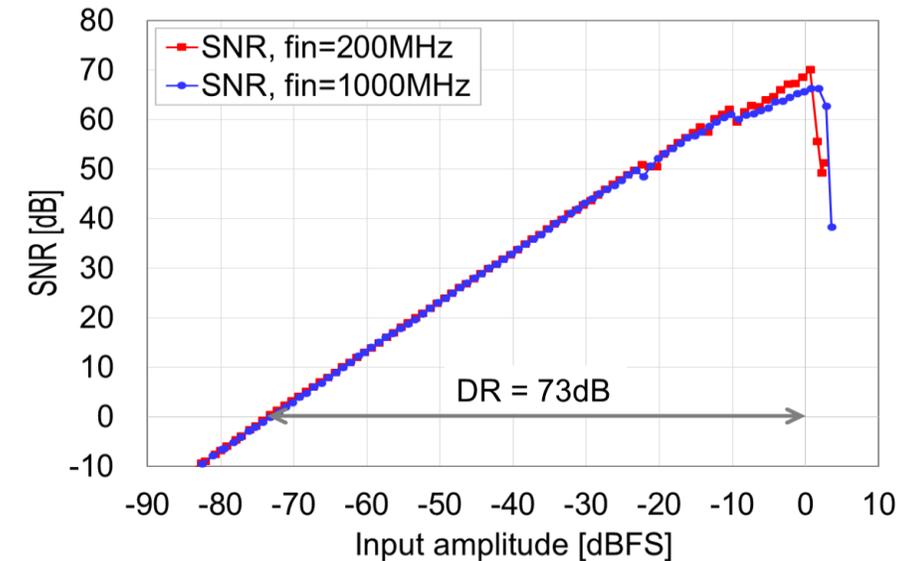
	This Work			
	18 GS/s		12 GS/s	
Sampling Rate (Fs)	18 GS/s		12 GS/s	
Resolution (bits)	12		12	
Input BW (GHz)	18		18	
Power (W)	1.3		0.85	
Noise Floor (dBFS/Hz)	-157		-157	
Fin (GHz)	4	8	2.5	4
SNDR at Fin (dB)	52	48	54.5	53
SFDR at Fin (dB)	56	54	60	61
Schreier FOM (dB):	150.4	146.4	153	151.5
FOMS_HF=SNDR+10log(Fs/(2*Power))	222	351.9	163.3	194.1
Walden FOM (fJ/step):	222	351.9	163.3	194.1
FOMW_HF=Power/(Fs*10 ^{(SNDR-1.76)/20})	222	351.9	163.3	194.1
THA or input buffer	THA		THA	
Sampling time and BW mismatch	2-way or optional randomized (2+1)		2-way or optional randomized (2+1)	
Sub-ADC	Pipeline		Pipeline	
Area	2.6		2.6	
Process Technology	16nm FinFET		16nm FinFET	



CT pipelined ADC Gen 1

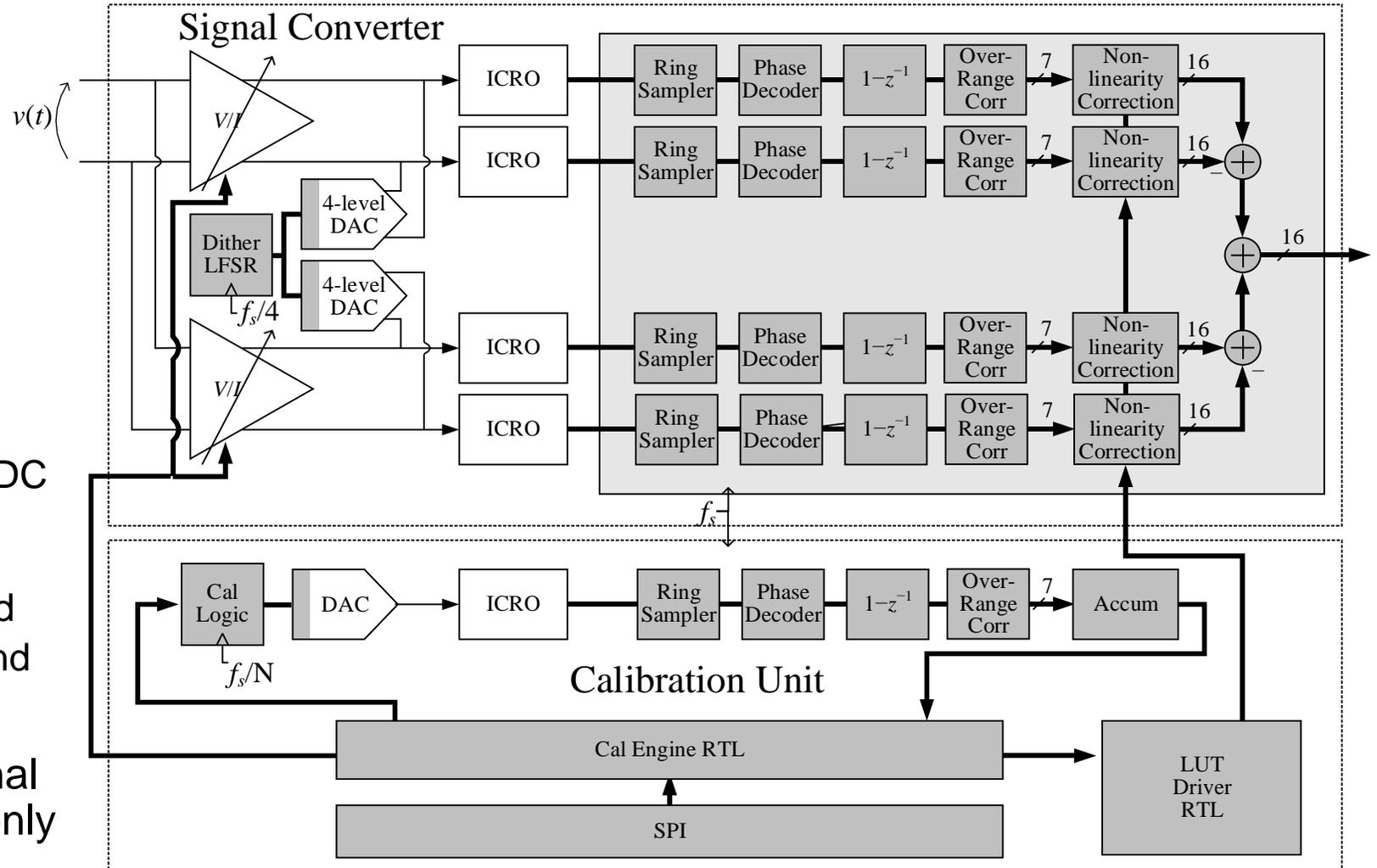


	This work
Architecture	CT pipeline
Inherent Anti-aliasing	Yes
Process Technology	28nm CMOS
f_s [GHz]	9
Raw BW = $f_s / (2 \text{ OSR})$ [MHz]	1125
App BW = $f_s / (2 \text{ App OSR})$ [MHz]	1125
App OSR	4.0
Small-signal NSD = $\text{DR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-164
Large-signal NSD (low f) = $\text{SNR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-160
Large-signal NSD (high f) = $\text{SNR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-156
IM3 [dBFS]	-84
HD2 [dBFS]	-79
HD3 [dBFS]	-86
SFDR [dB]	73
Area [mm^2]	5.1
Power [mW]	2330
$\text{FOM}_s = \text{DR} + 10 \log_{10}(\text{BW}/P)$ [dB]	160



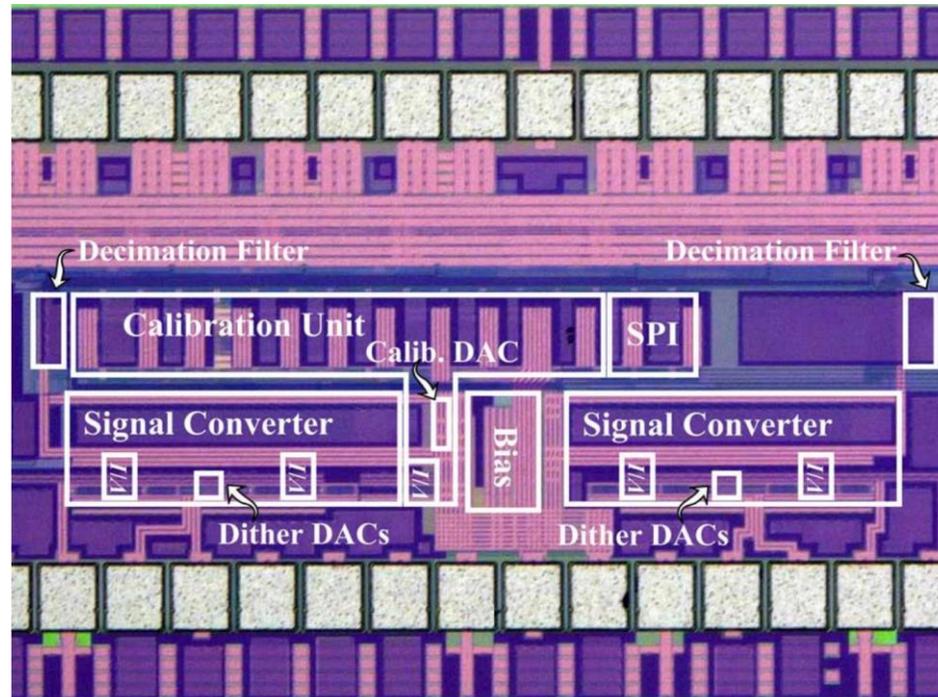
VCOADC

- ▶ Variable gain V/I
- ▶ Reconfigurable
 - $f_s = 1.1\text{-}2.2\text{Gsp}$ s
 - $\text{BW} = 10\text{-}20\text{-}50\text{MHz}$
 - $\text{NSD} = -147\text{ to } -154\text{dBFS}$
 - $\text{Power} = 7\text{-}30\text{mW}/\text{adc}$
- ▶ $\text{SFDR} > 85\text{dBc}$
- ▶ Calibration:
 - Background calibration of replica ADC signal path.
 - All calibration engine logic included with ADC IP, no uController required
 - Continuous calibration or on-demand
 - Calibration period = $15\text{-}30\mu\text{s}$
- ▶ Manual layout for high-speed signal path, P&R for calibration engine only

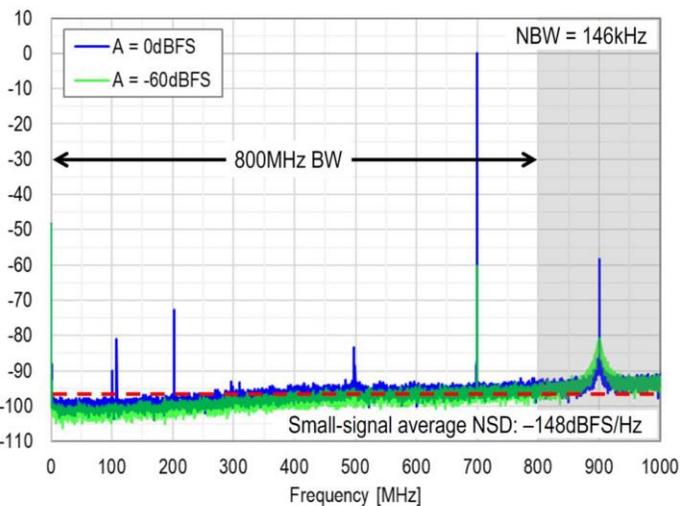
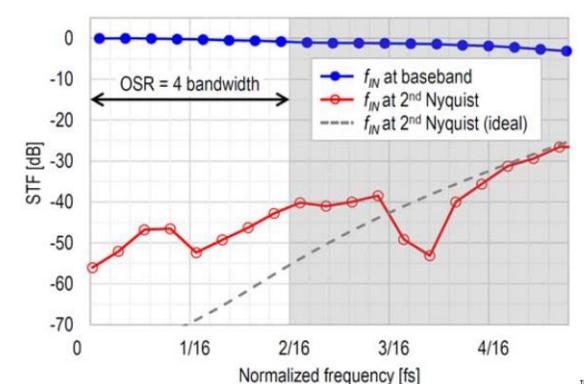
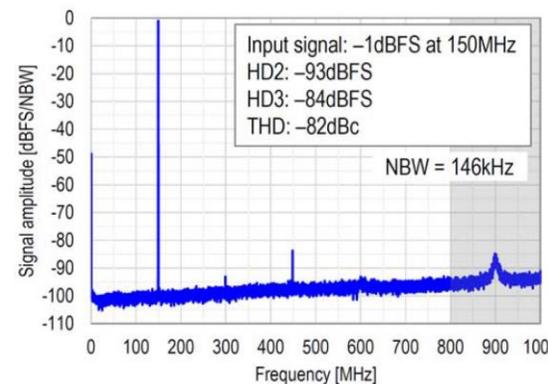
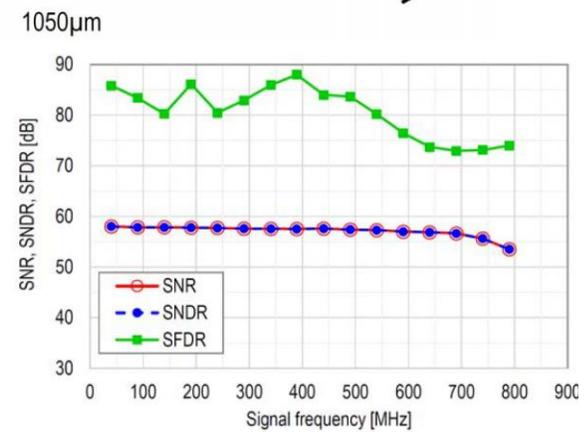
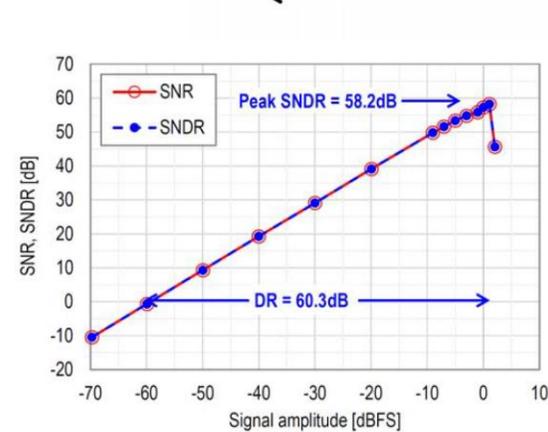
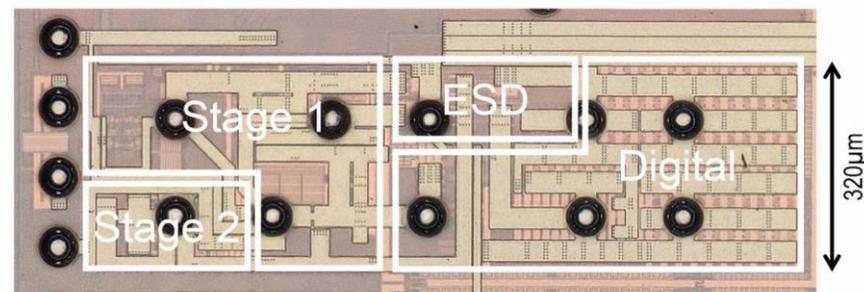
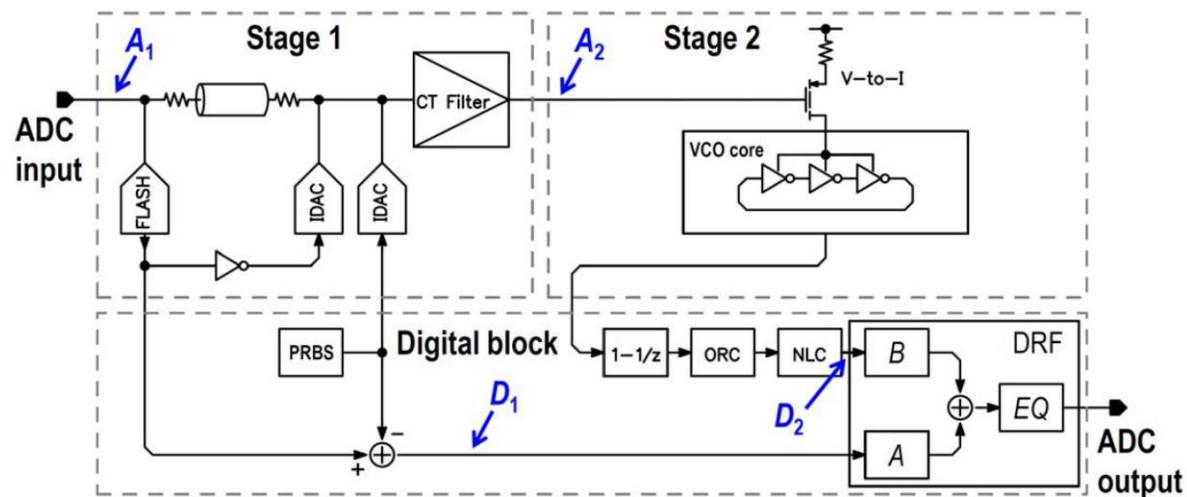


Why VCOADC?

- ▶ Area is 5-10x smaller than other ADCs with similar specs
- ▶ CT front end-> drive-able
- ▶ Mostly digital->Scalable



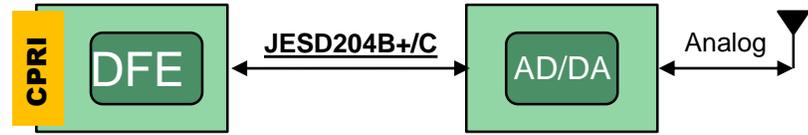
CT pipelined ADC Gen 2



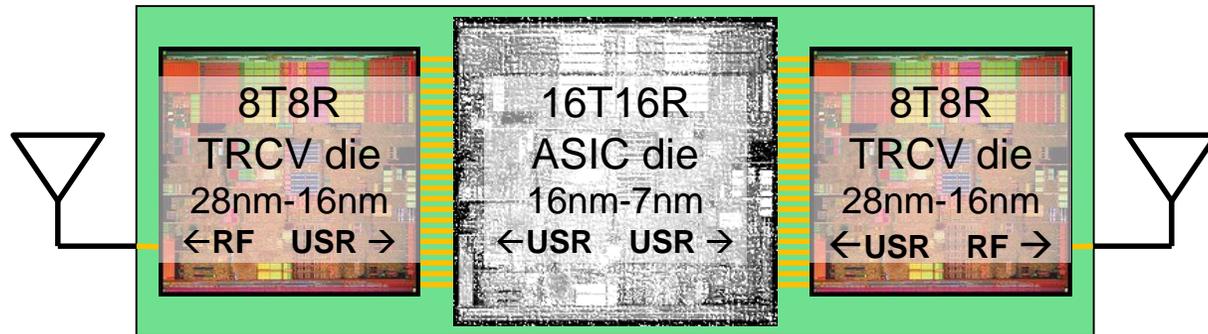
	This work	JSSC 2017 [1]
Architecture	VCO-based CT pipeline	CT pipeline
Inherent anti-aliasing [dB]	41	68
Process Technology	16nm FinFET	28nm CMOS
f_s [GHz]	6.4	9.0
Raw BW = $f_s / (2 \text{ OSR})$ [MHz]	800	1125
App BW = $f_s / (2 \text{ OSR})$ [MHz] (OSR ≥ 4 for all ADCs)	800 (OSR = 4.0)	1125 (OSR = 4.0)
Power [mW]	280	2330 **
Dynamic range [dB]	60	73
Peak SNDR [dB]	58	66
HD2 [dBFS]	-93	-79
HD3 [dBFS]	-84	-86
SFDR [dB]	73	73
Area [mm ²]	0.34	5.1 **
FOM _S = SNDR + 10 log ₁₀ (BW / P) [dB]	153	153 **

Integrated Systems: SoCs/SiPs with Mixed-Signal + Embedded DSP Capability

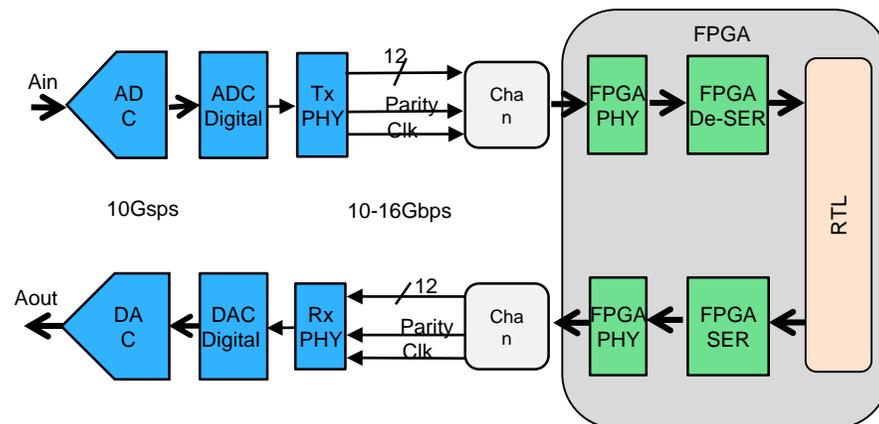
Interfaces: JESD204B/C, High Speed Parallel and Ultra Short Reach



Optimised for 20cm on PCB



USR/ASIC target integration in 70mm x 70mm laminate



JESD204B/C

- ▶ Core1 – 16.2Gbps, 8 pJ/b
- ▶ Core 2 – 25Gbps, 9.4 pJ/b

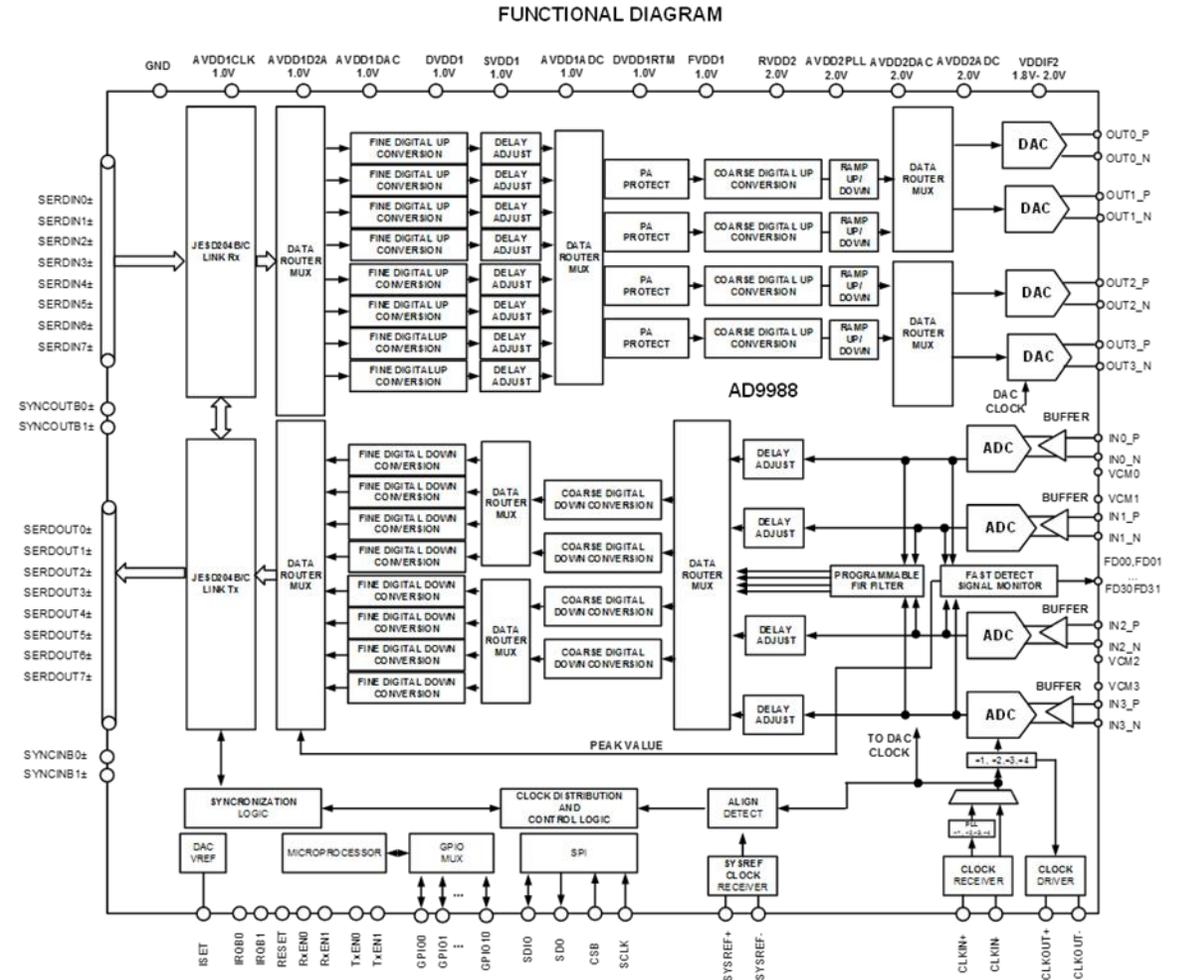
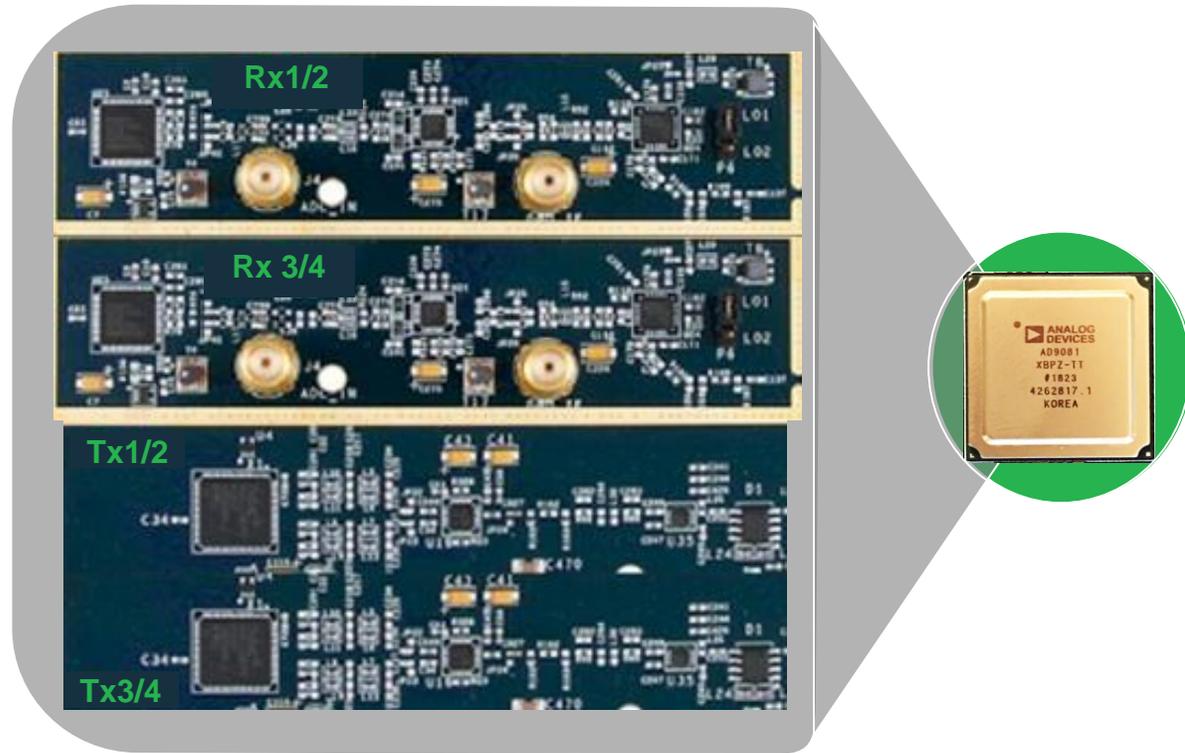
USR - Ultra Short Reach Interface (2pJ/b)

- ▶ Goal - Scalable, Power Efficient (2 to 4pJ/b) Interface for SIP and near-Package connect
 - Spans OIFCEI 28G USR and VSR channels
- ▶ Lane Rates – 10-28Gbps

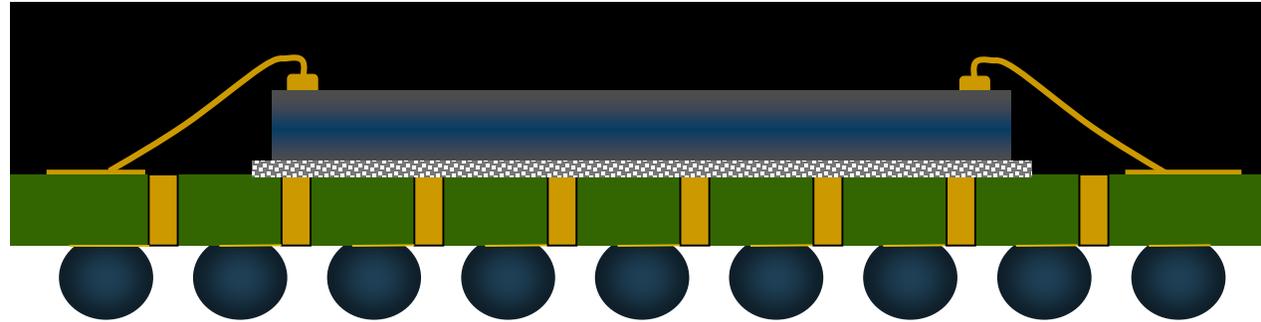
HSP – High Speed Parallel Interface (8pJ/b)

- ▶ Goal – Enable Ain to Aout Latency < 100ns
- ▶ Clock Forwarded Architecture
 - No CDR, Limited FIFOs, may not need PLL
- ▶ Benefits
 - Signal Path Latency <100ns
 - 30% FPGA Power Reduction vs. JESD

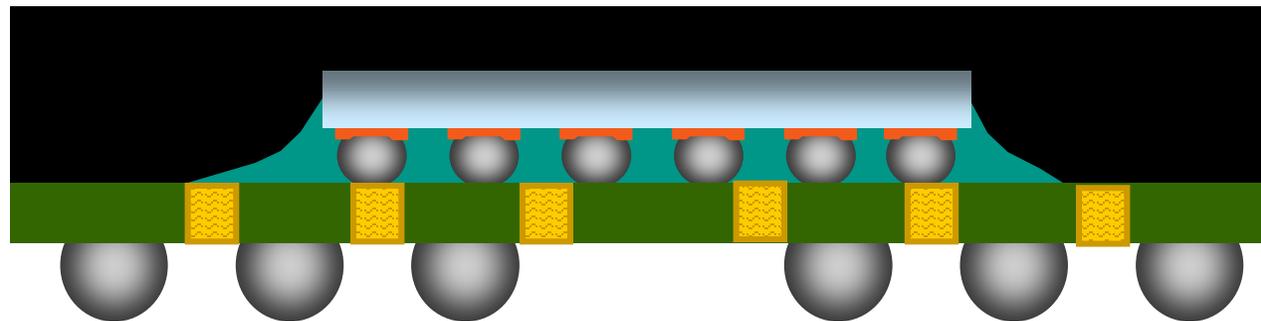
quad Tx / quad-dual Rx fully integrated wideband MxFE



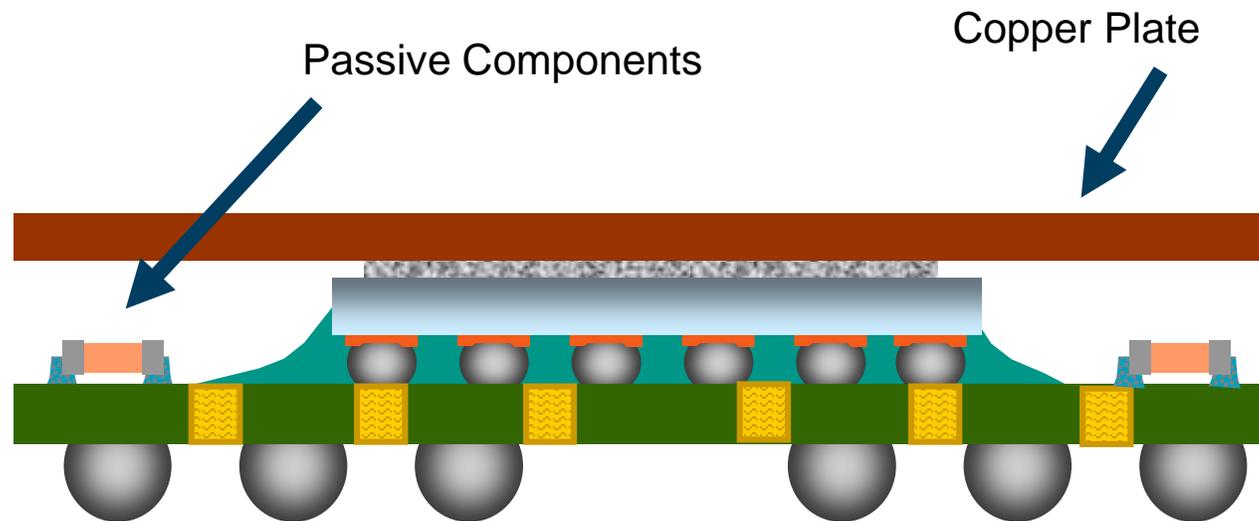
Flip Chip Chip Scale Package BGA



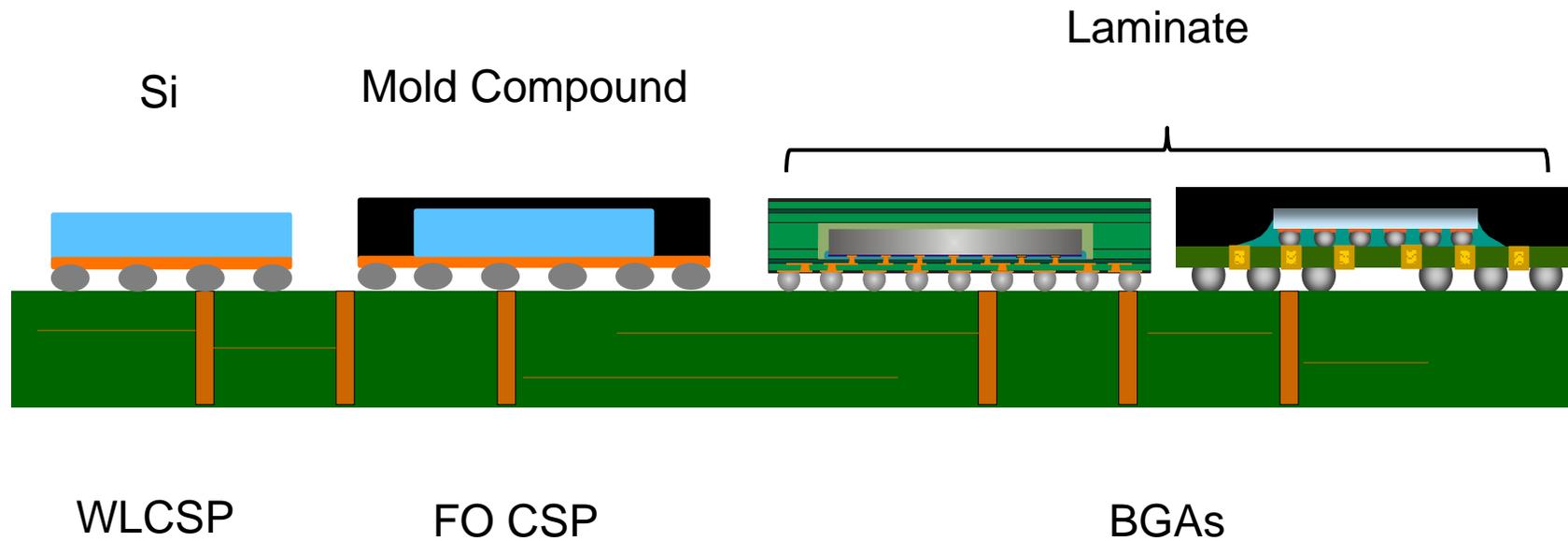
Flip Chip CSP BGA



Flip Chip – Thermally Enhanced BGA



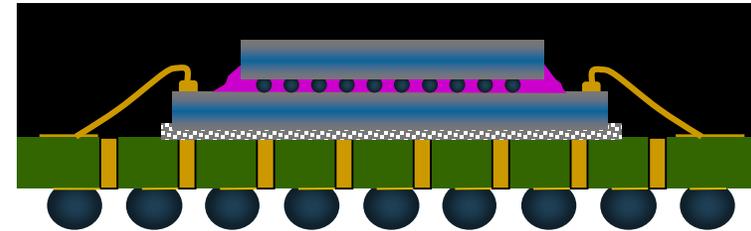
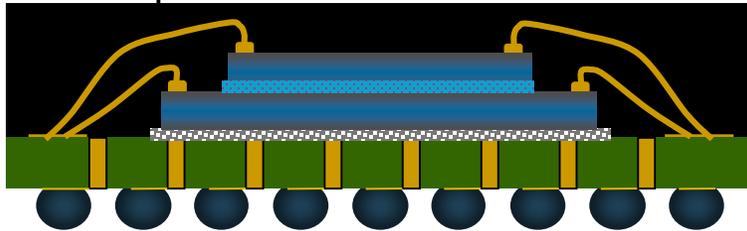
Higher frequency performance



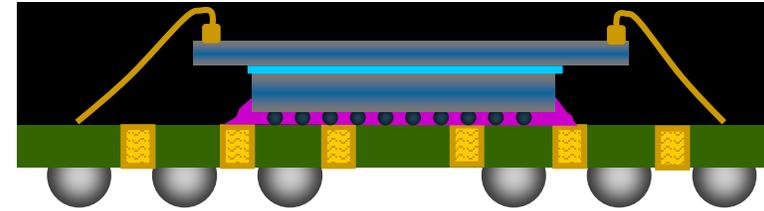
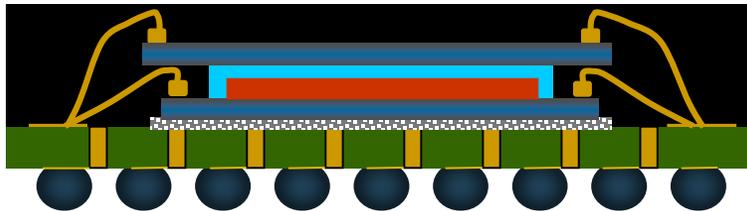
3D Packaging

“Pyramid”

Top Die Smaller Than Bottom



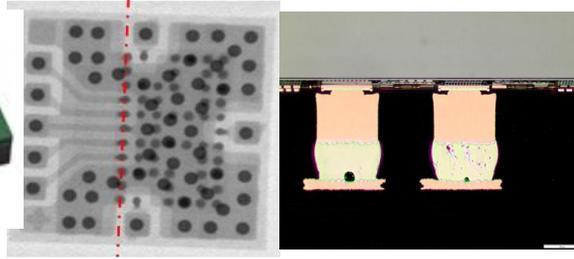
Top Die Same Size or Larger
Than Bottom



Wirebond Versions

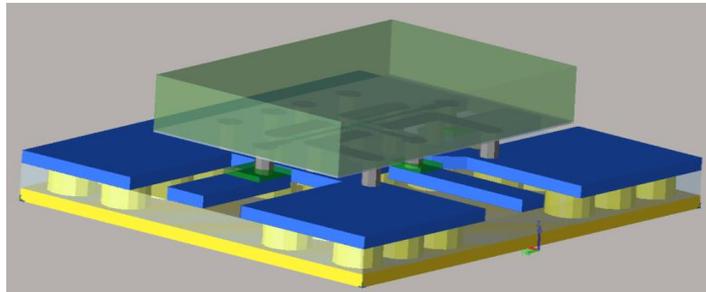
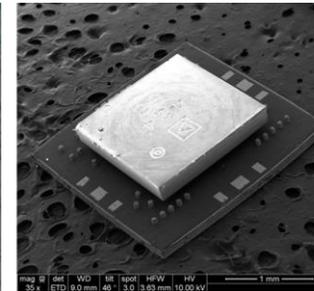
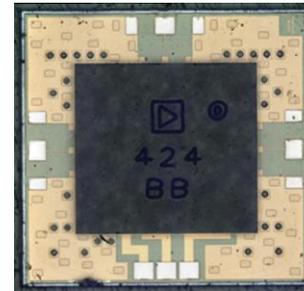
Bumped Die Flip Chip Versions

mmWave front-end modules



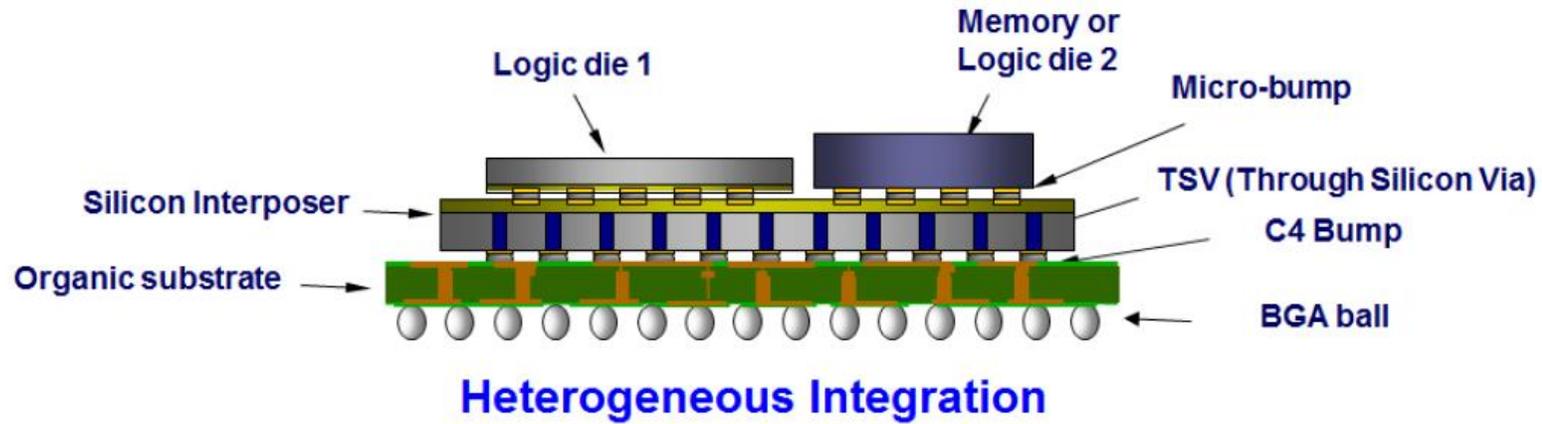
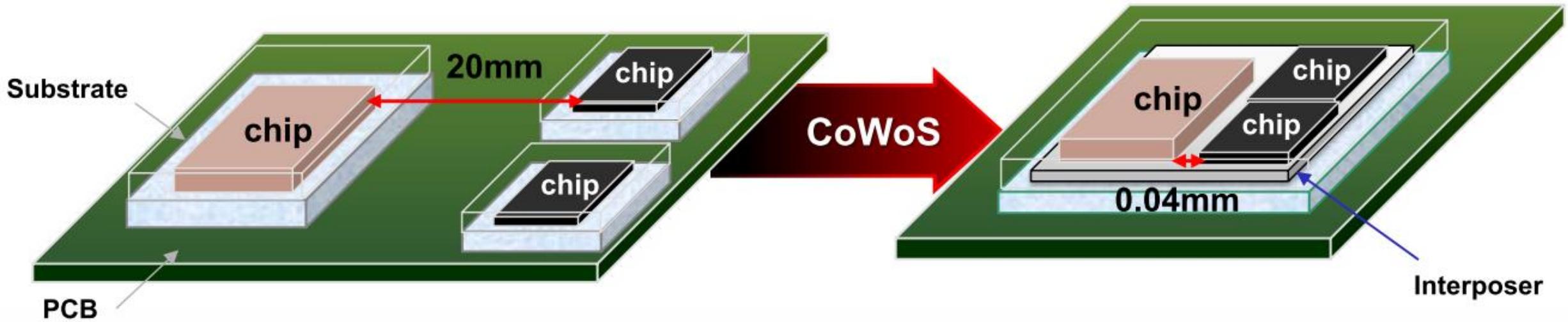
FlipChip on Laminate (LGA)

**Die-On-Carrier (DOC)
“Die-like” RF Product**



**Bumped Flip Chip
(SMT Assembly)**

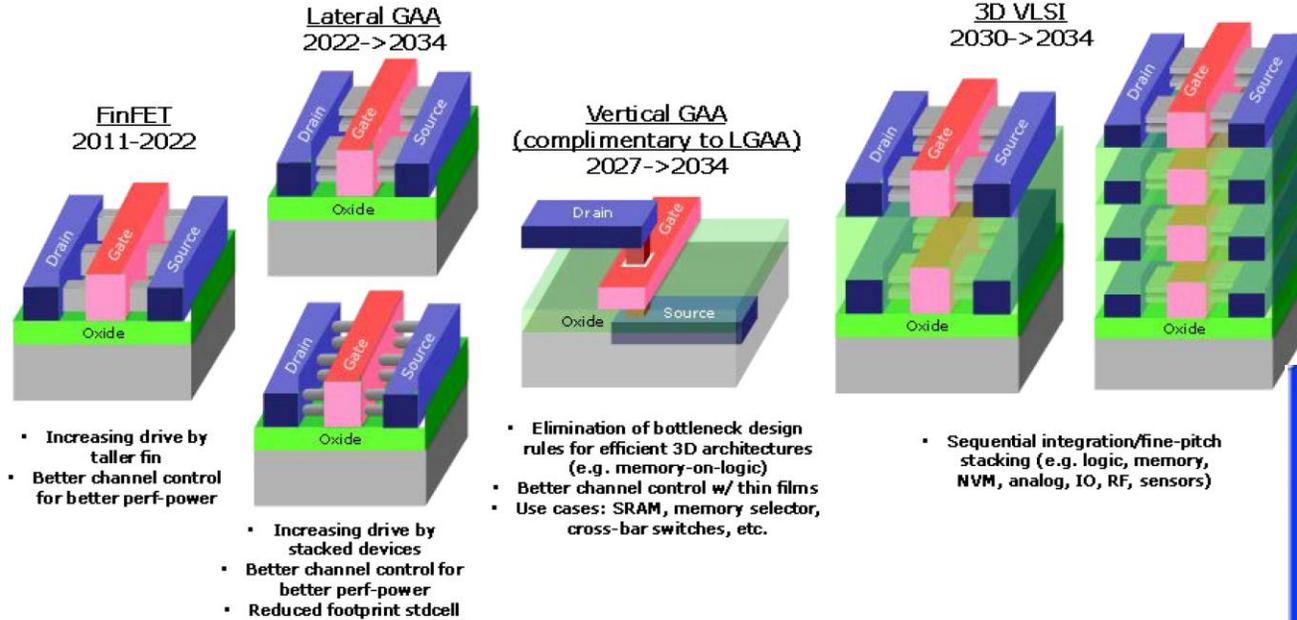
Interposer Systems in a Package



TSMC's CoWoS® (Chip-on-Wafer-on-Substrate) Services, <https://www.tsmc.com/english/dedicatedFoundry/services/cowos.htm>

Evolution of VLSI into 3D: density!

>2020: 2.5D/3D fine-pitch assembly + stacking



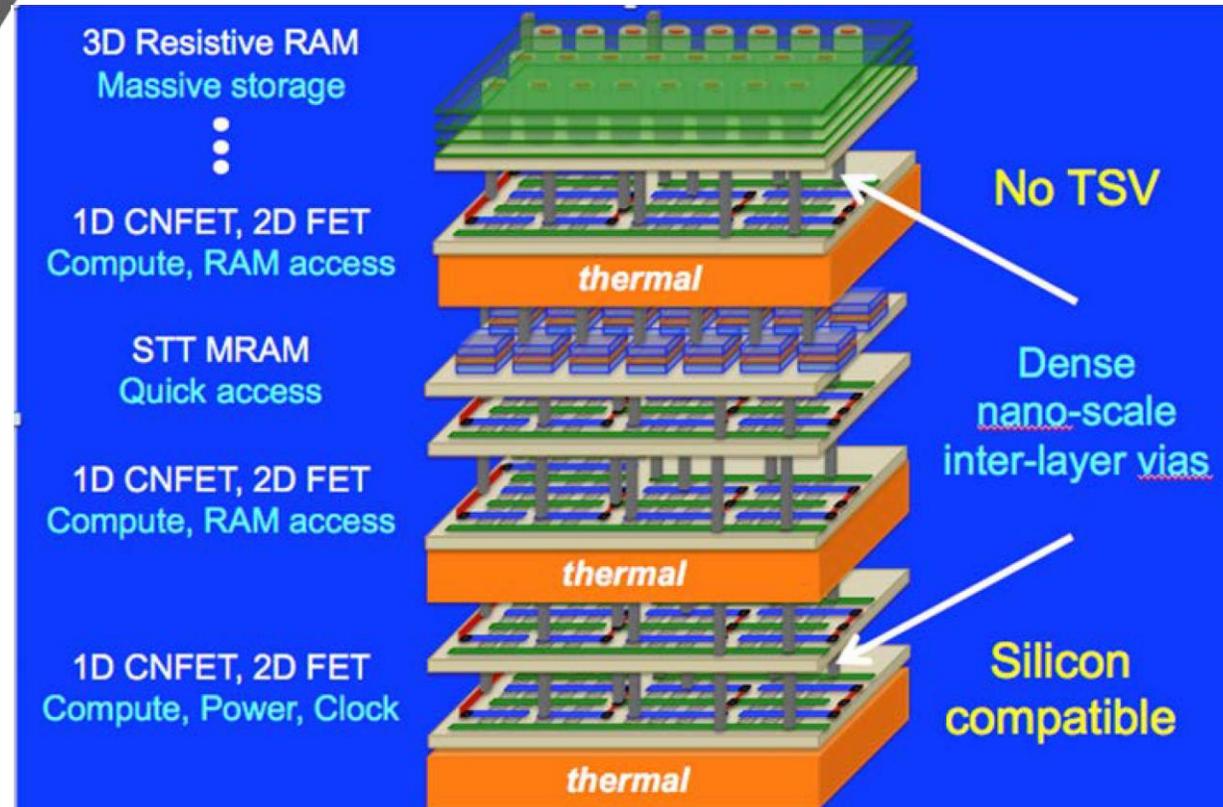
Main advantages:

- Density
- Power efficiency
- Mitigation of local interconnect issues

Main challenges:

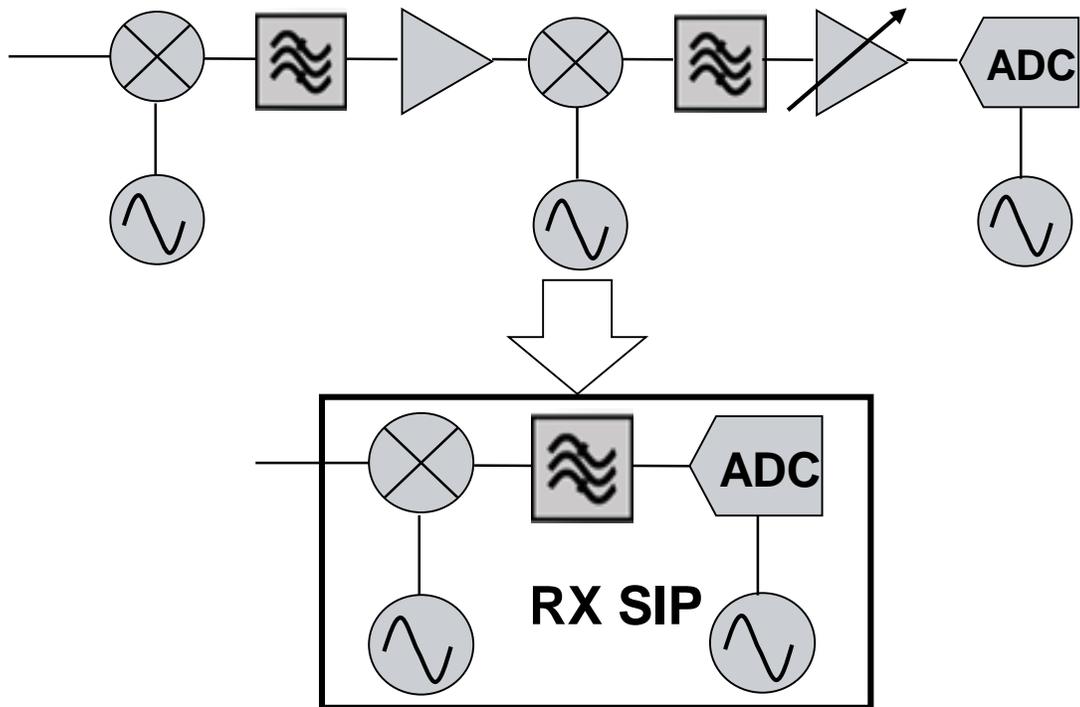
- Cost
- Heat management

International Roadmap for Devices and Systems (IRDS) – 2018 Edition.

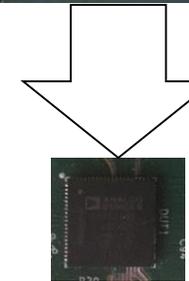
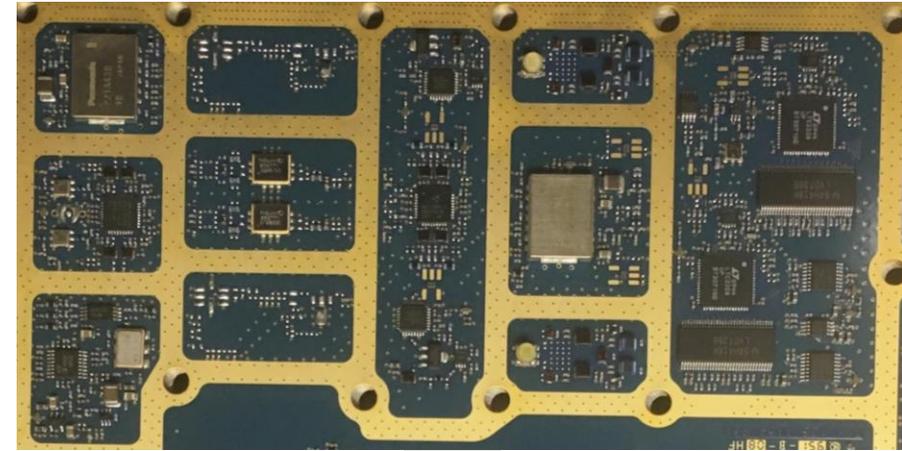


Why do a SiP?

Traditional Receiver Architecture

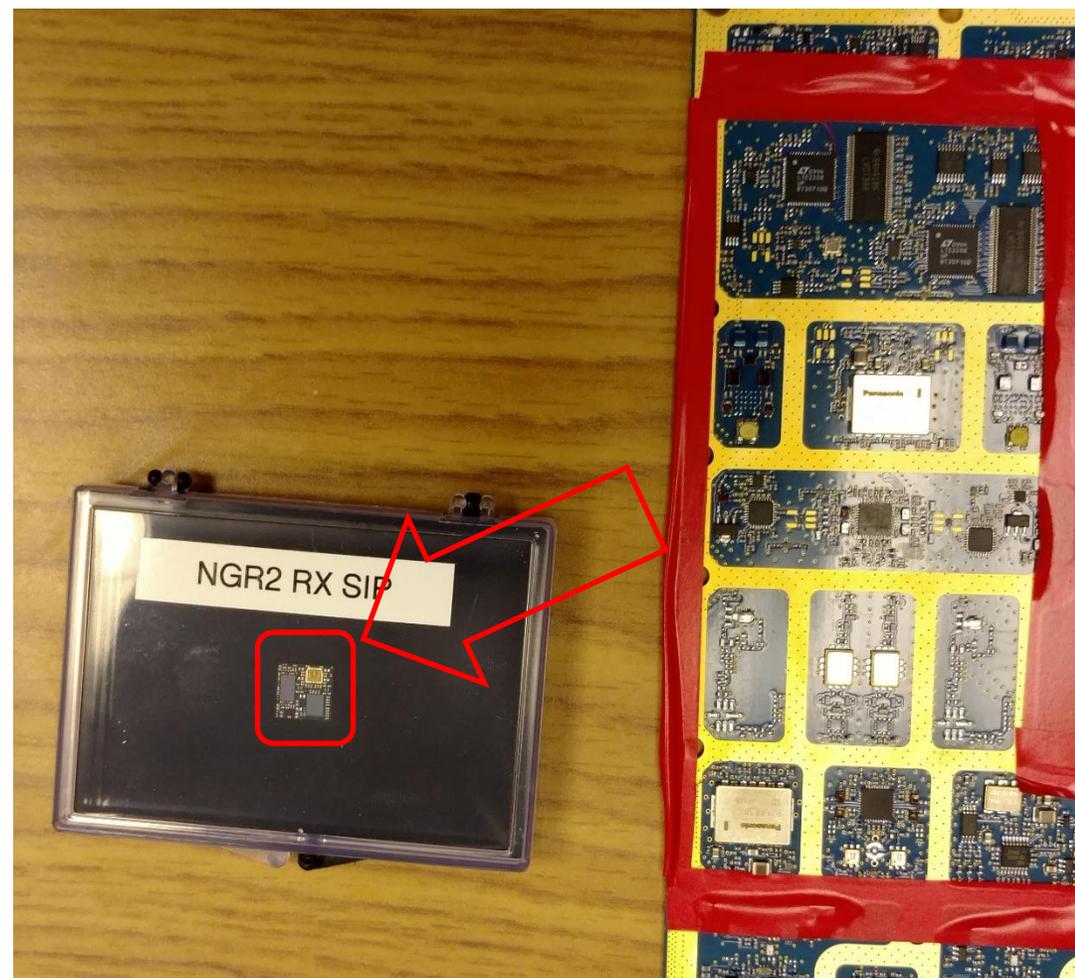
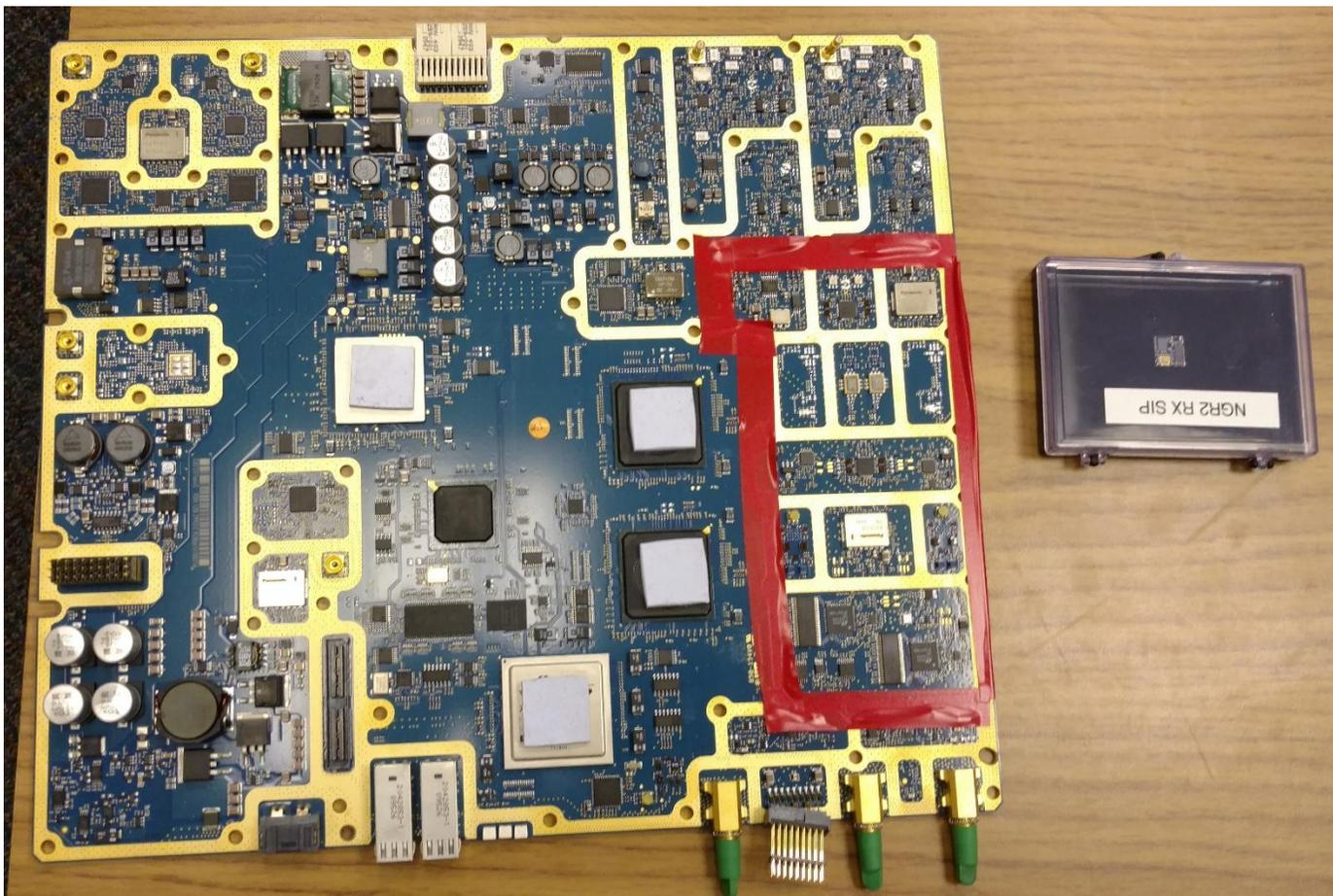


Traditional Base Station Board



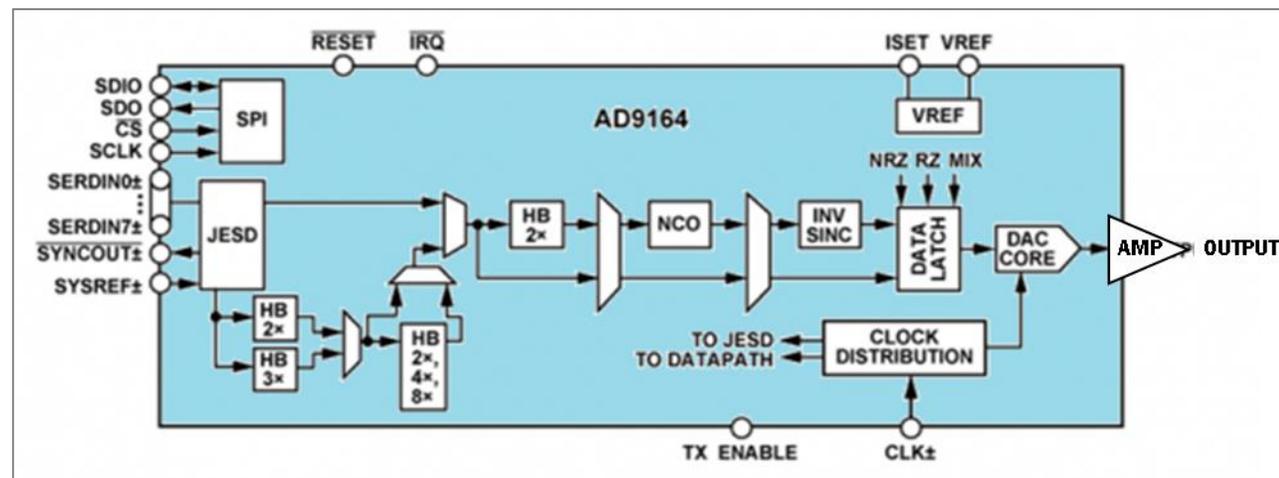
**RX SIP(11x11mm)
+ External Bypass
90% reduction in Board Area**

Real BTS's TRx board



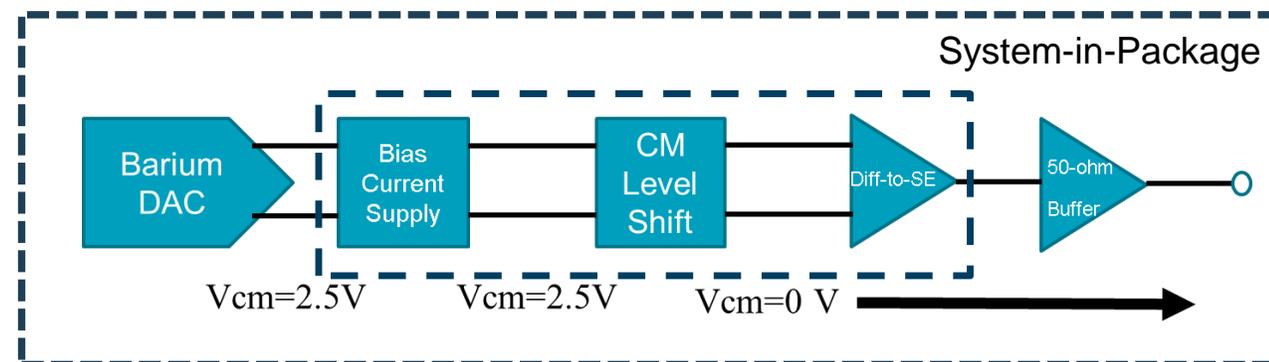
16-bit 12.0 GSPS RF DAC with Integrated Buffer

- ▶ Direct-to-RF synthesis up to 5GHz with 2.5 GHz maximum signal bandwidth
- ▶ Integrated amplifier reduces the overall cost of the system simplifies the design, and extends the overall broadband performance
- ▶ High-Dynamic range, ultra wideband and flexible frequency planning
- ▶ Enables software configurable radio transmitter with configurable data path signal processing functions



Key Benefits

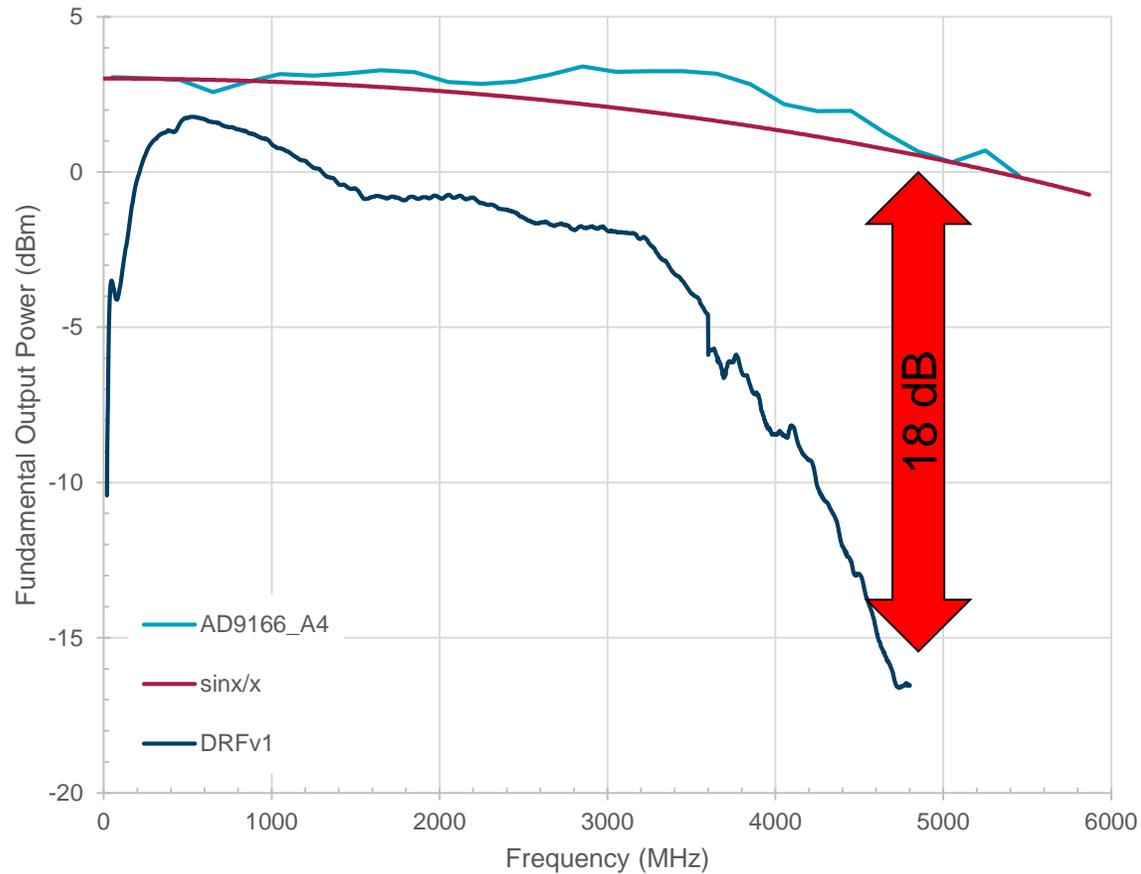
- ▶ Flexible frequency planning with multiple DAC rates and interpolation modes available for synthesizing the same RF frequency
- ▶ Common hardware platform for flexible and reliable RF design
- ▶ Absorbs analog RF functions into configurable digital domain and eliminates IF low pass filters and analog up-conversion imperfections
- ▶ Eliminates IF-to-RF up-conversion stage and LO generation lowering overall system power consumption
- ▶ Integrated amplifier extends operation to DC and provides bandwidth flatness out to 5GHz.



Frequency Response

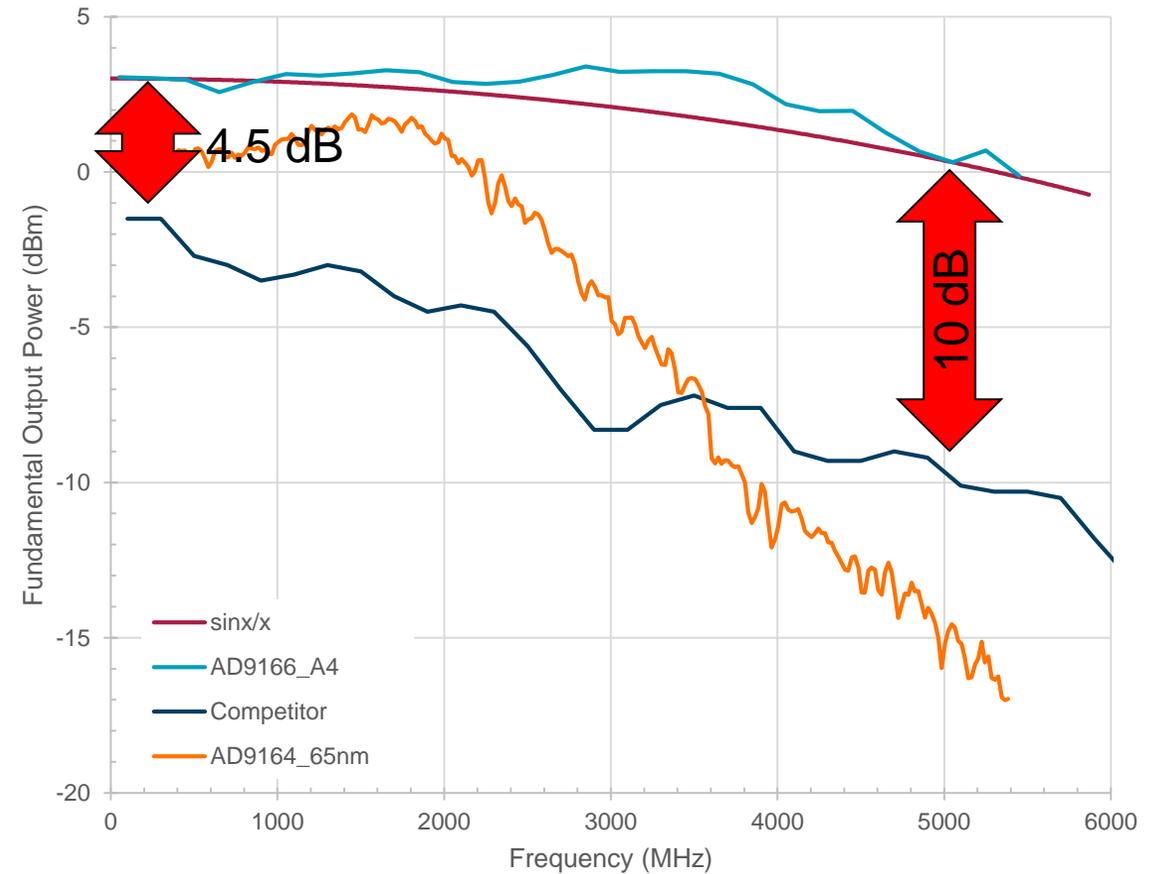
▶ AD9166

AD9166 vs. AD9162 Plus Discrete Amplifier on Board



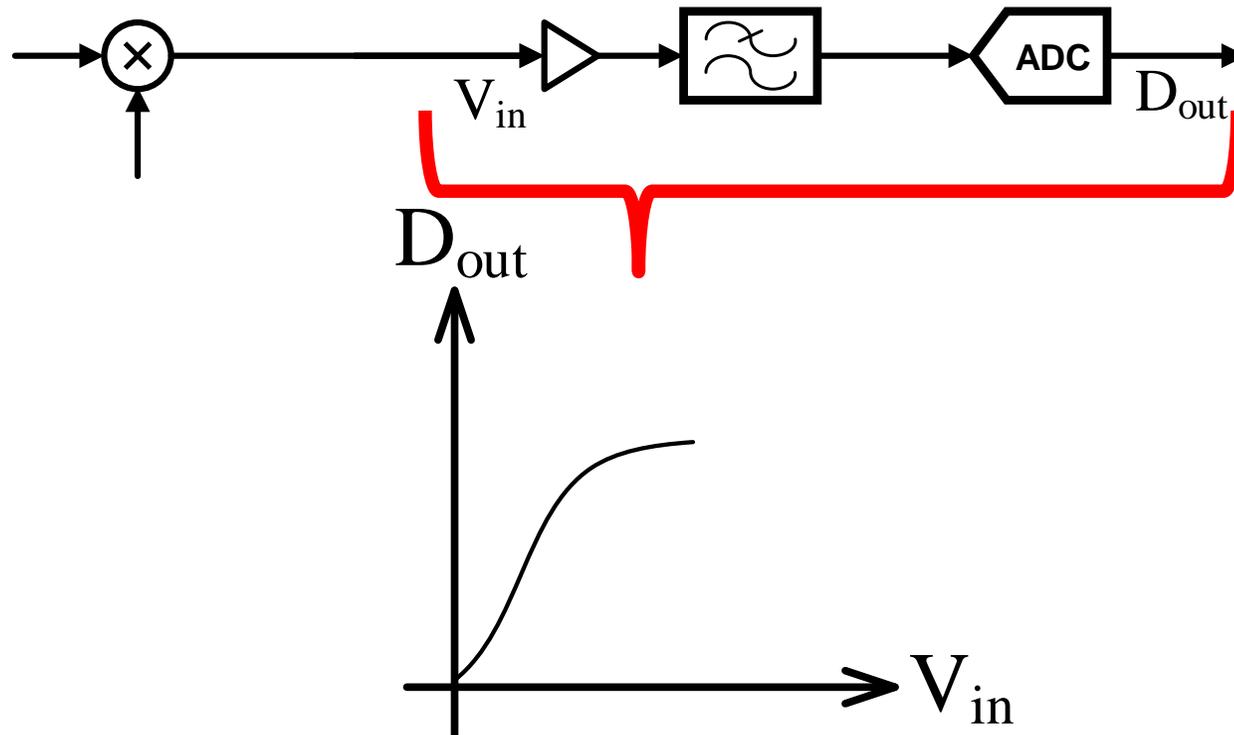
▶ AD9166 vs. Competitor

AD9166 vs. AD9162, Competitor

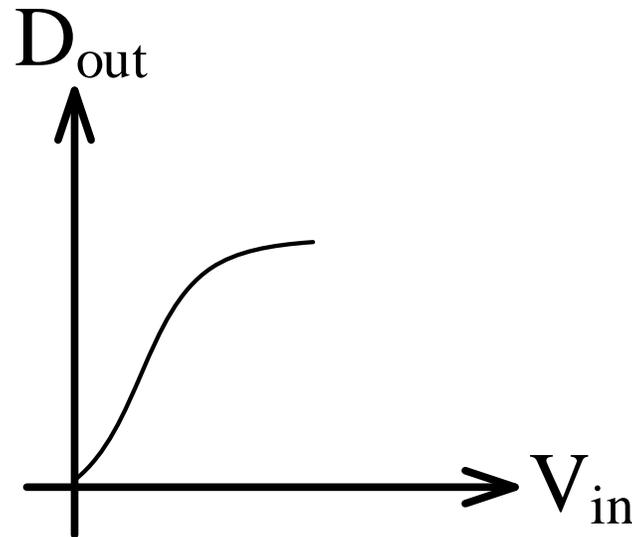
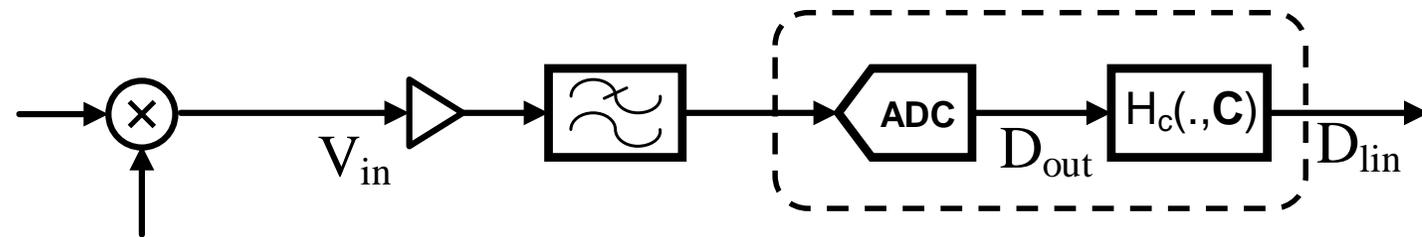


Algorithmic Capability: System-level Linearization

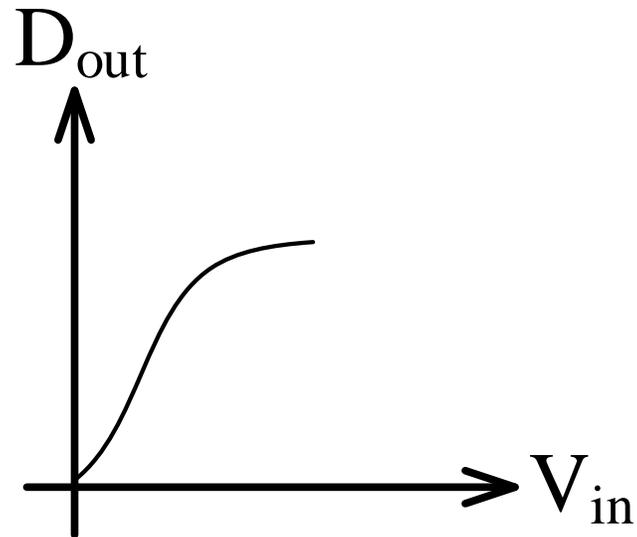
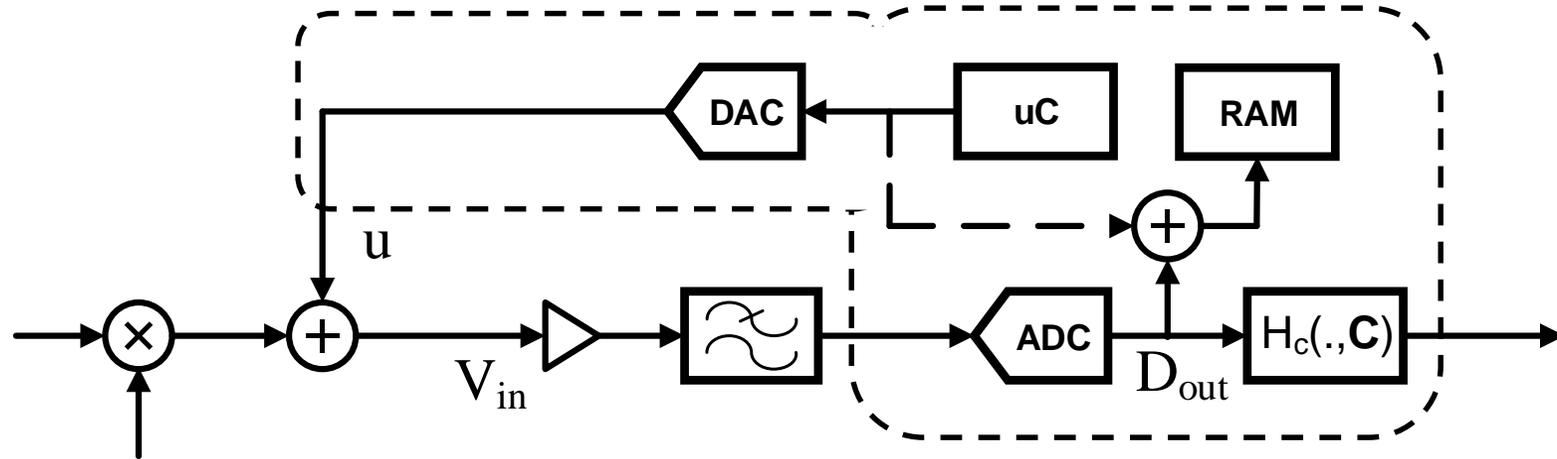
Non-linear Correction for Rx Signal Chain



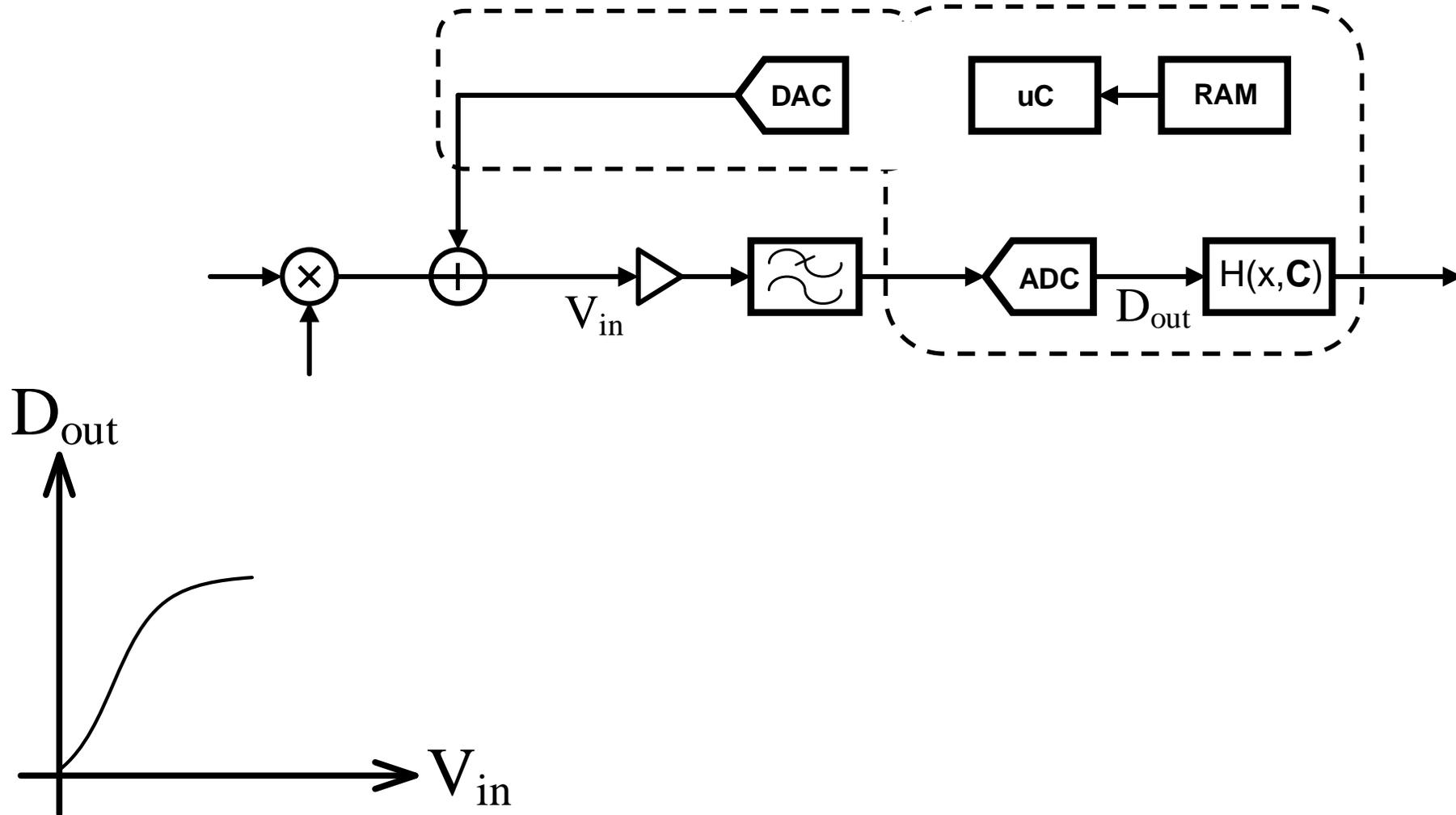
Non-linear Correction for Rx Signal Chain



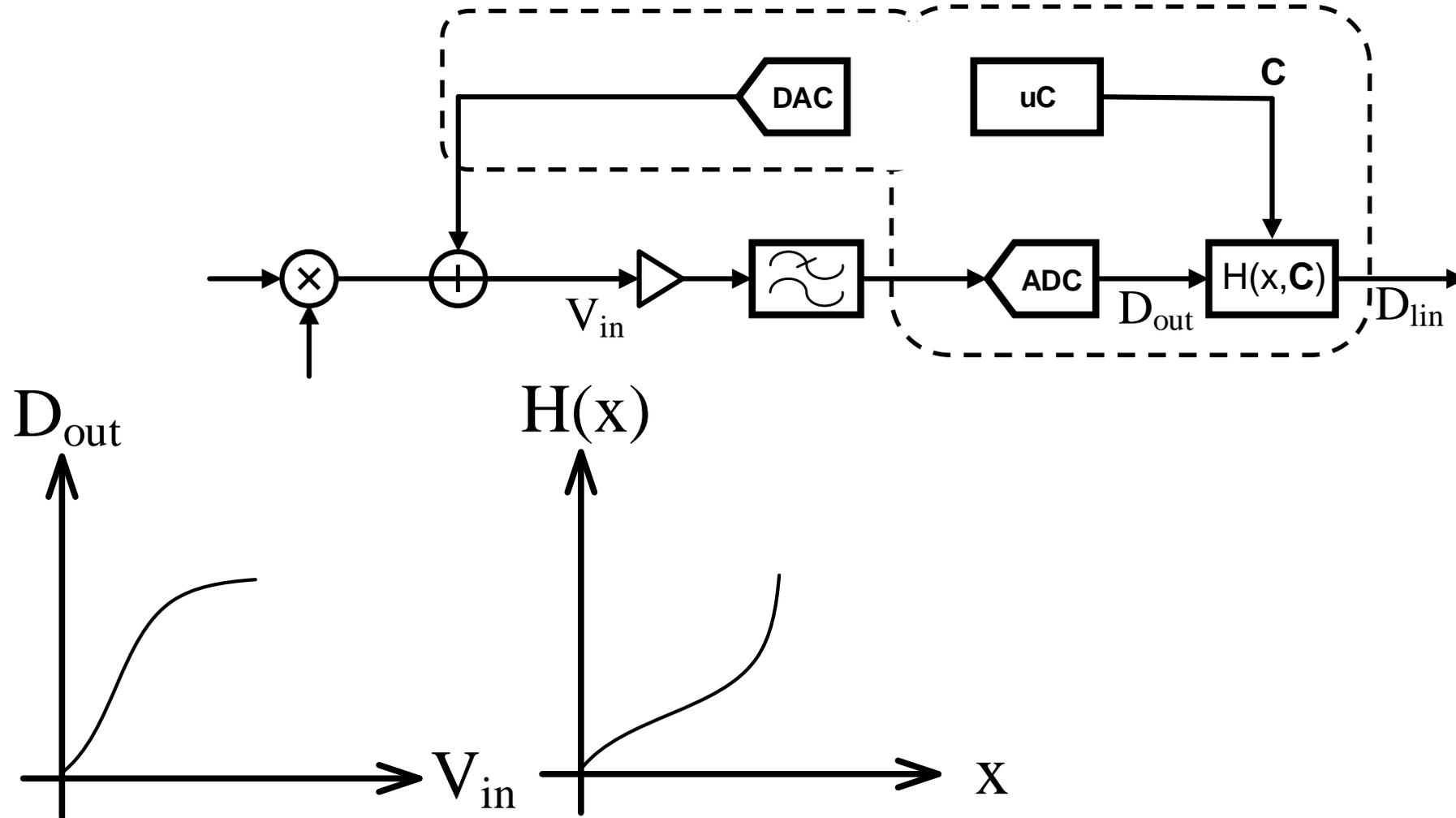
Non-linear Correction for Rx Signal Chain



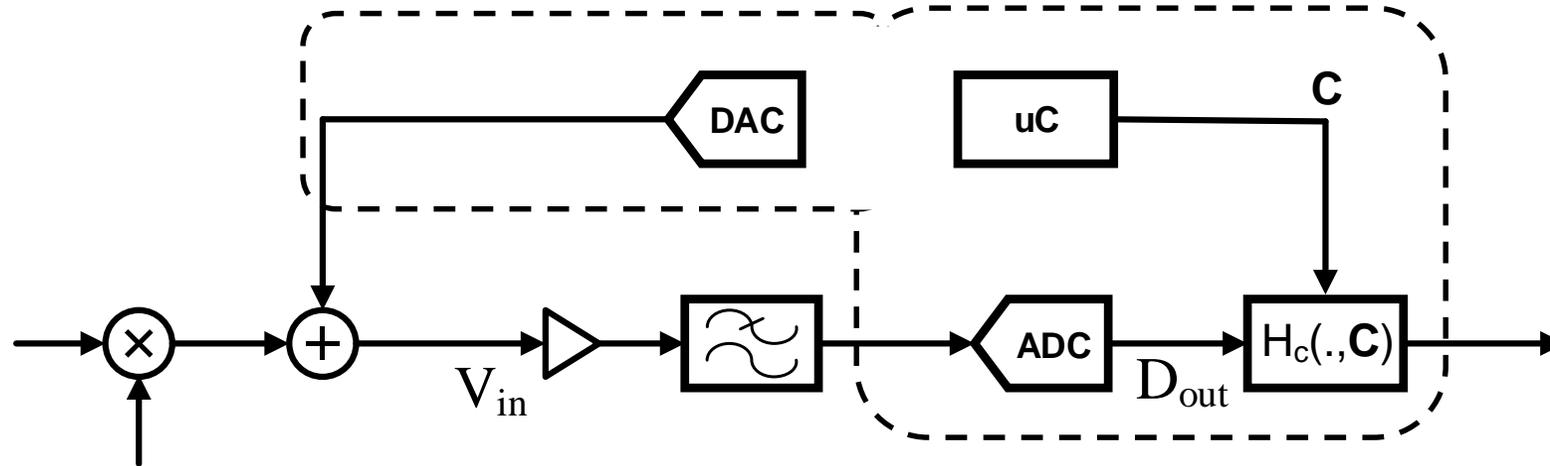
Non-linear Correction for Rx Signal Chain



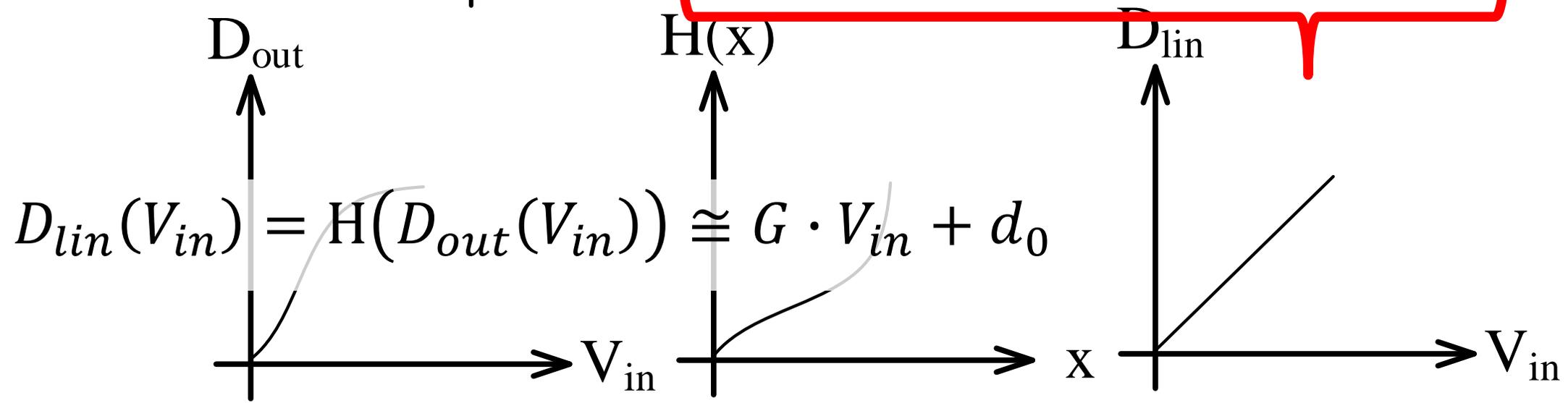
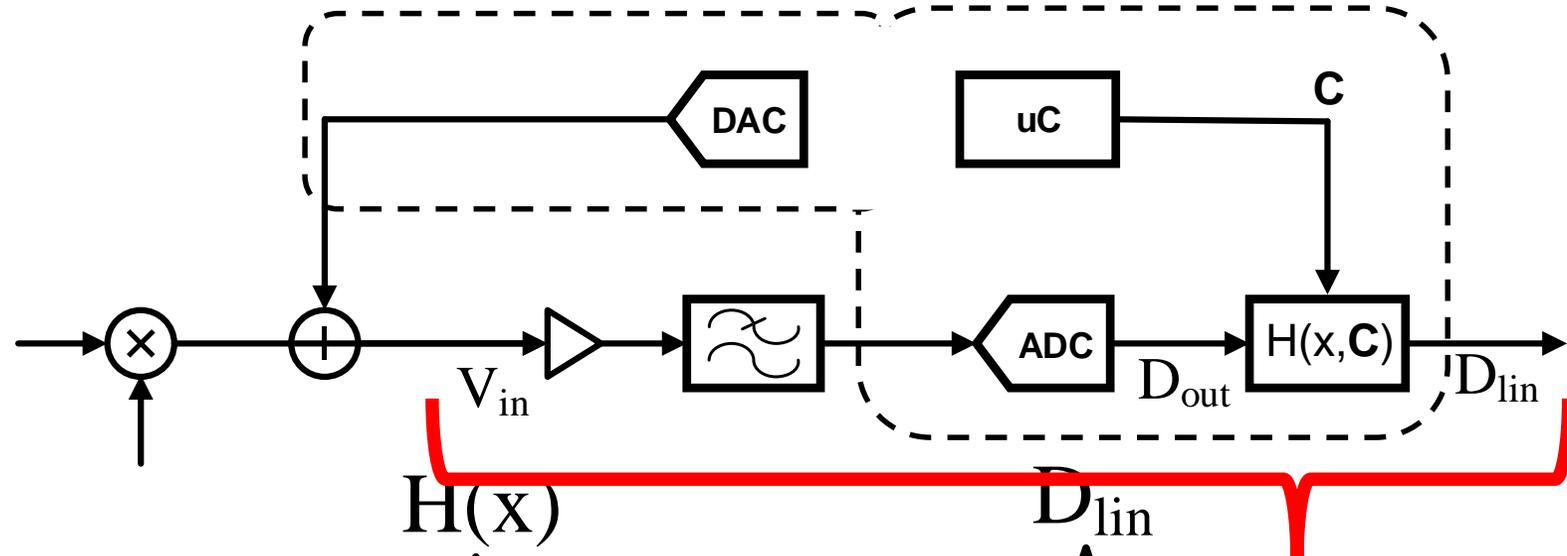
Non-linear Correction for Rx Signal Chain



Non-linear Correction for Rx Signal Chain

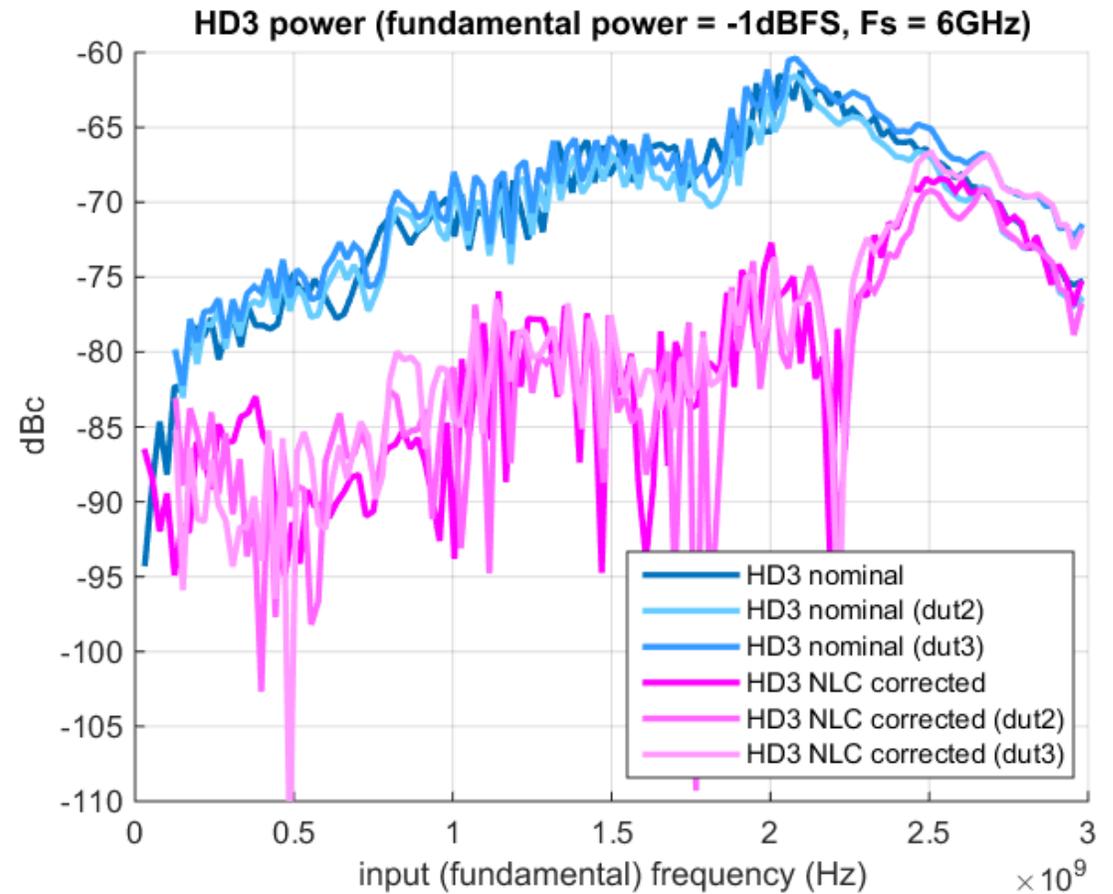
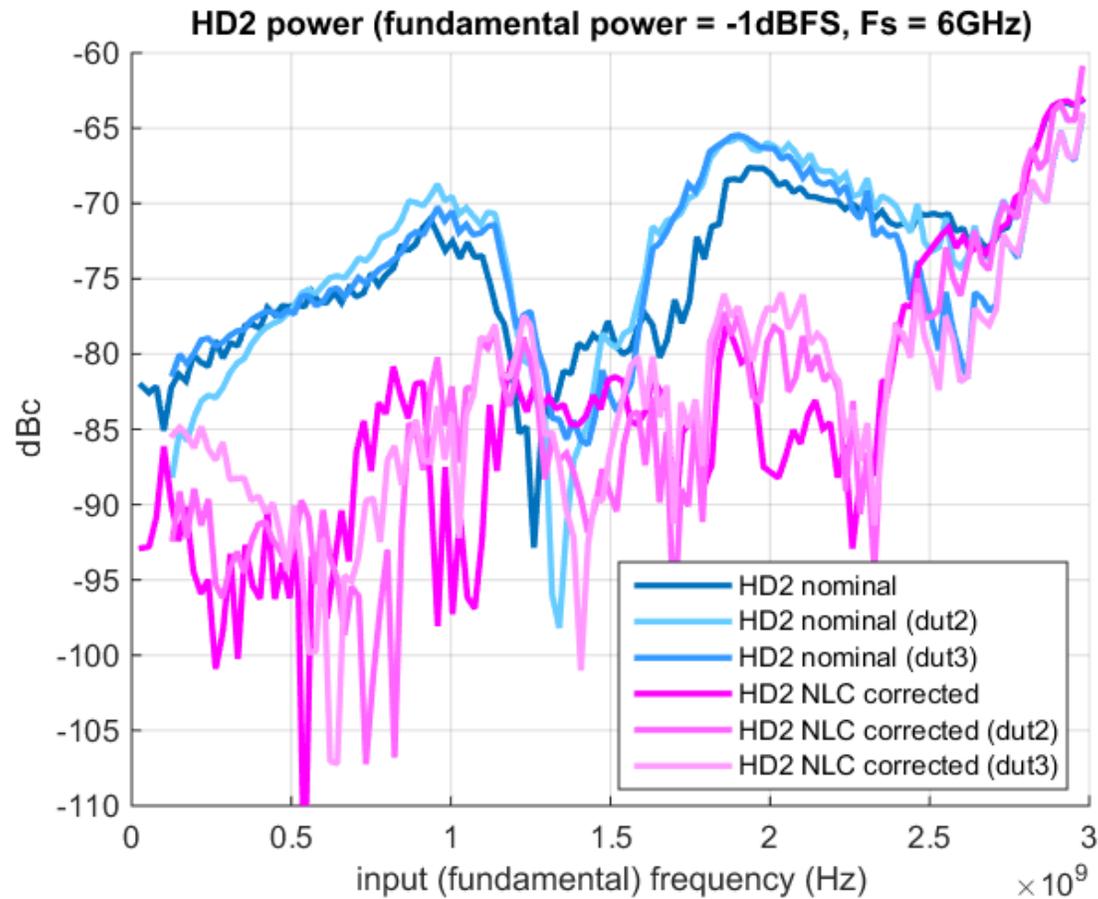


Non-linear Correction for Rx Signal Chain

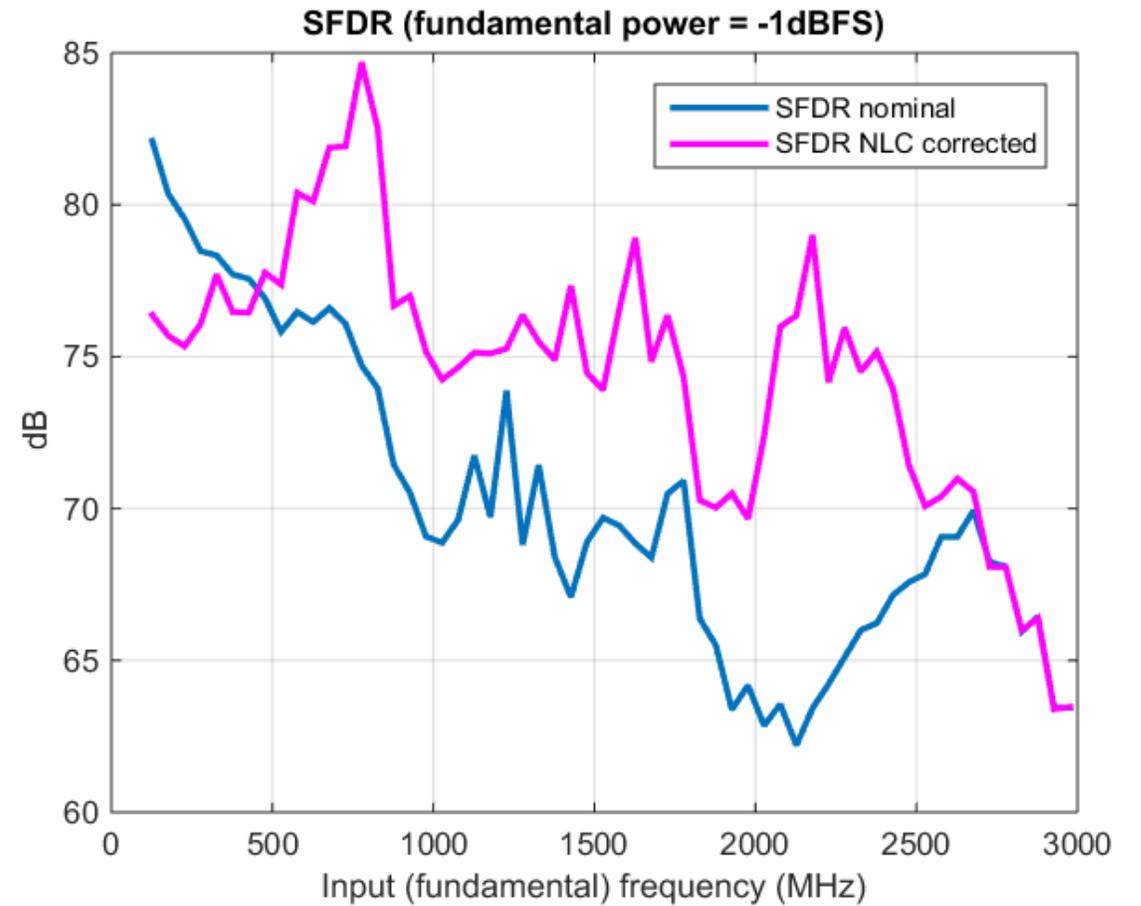
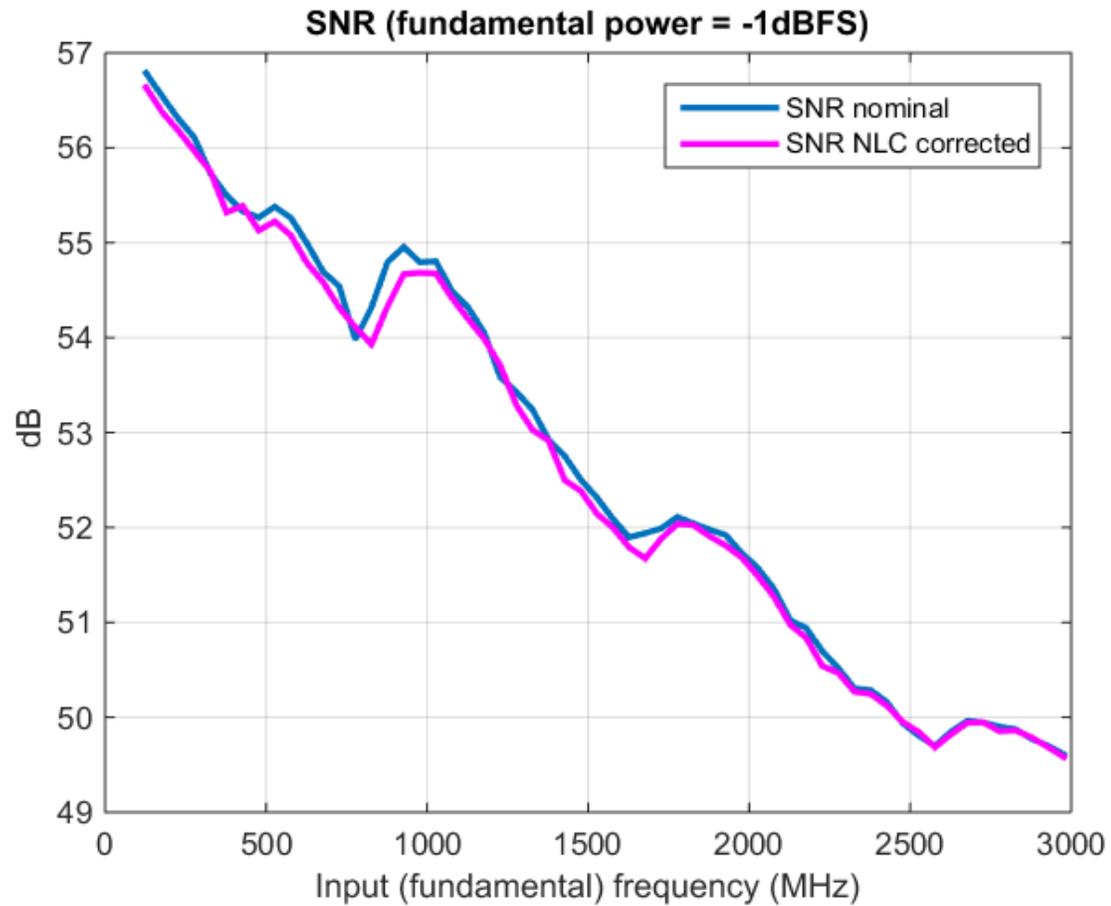


$$D_{lin}(V_{in}) = H(D_{out}(V_{in})) \cong G \cdot V_{in} + d_0$$

Fs=6GSPS Lab Data: HD2 & HD3 correction

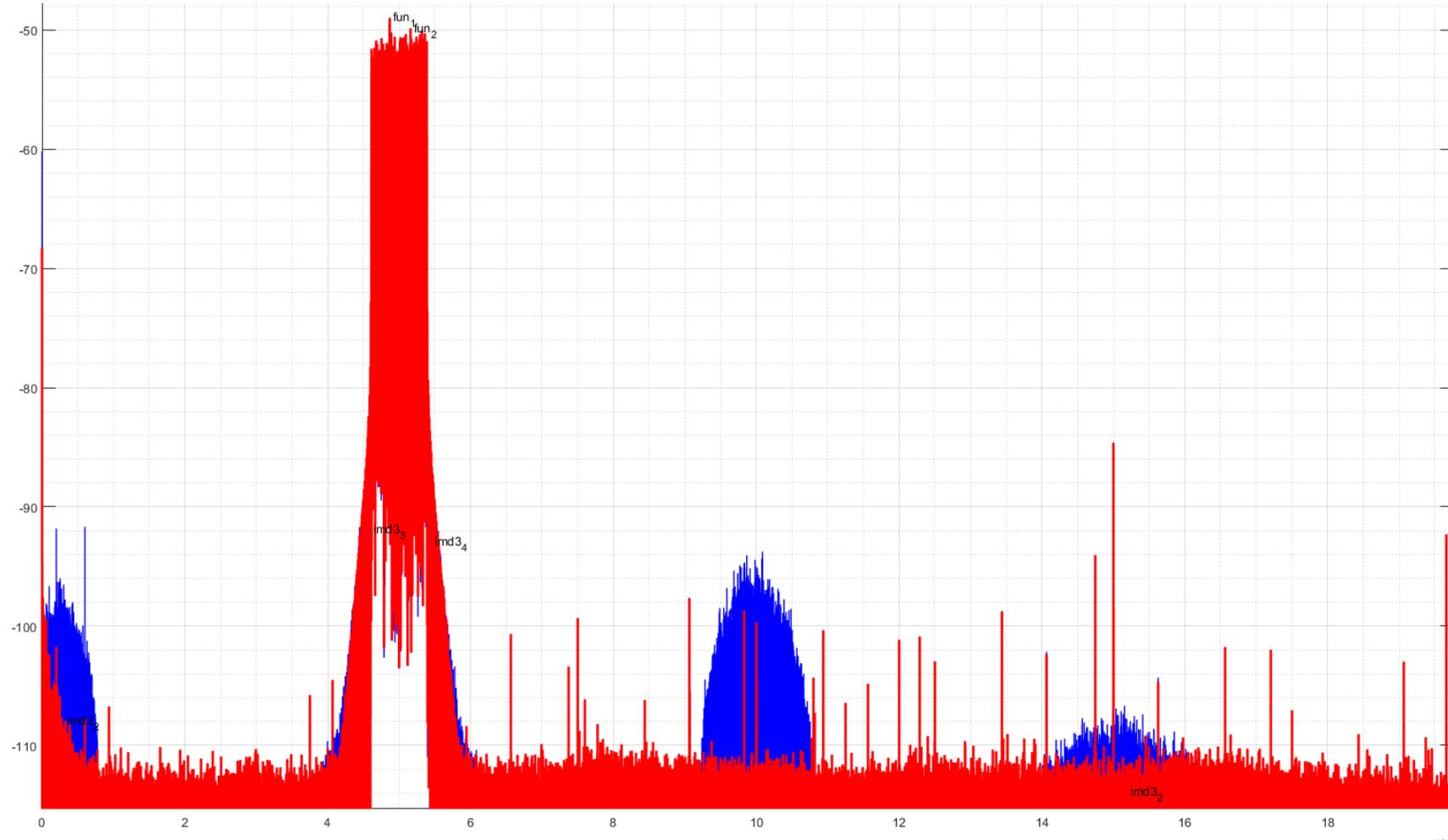


Fs=6GSPS Lab Data: SNR and SFDR



Wi-Fi 6 (802.11AX) Test Signal (500M)

- ▶ Test signal shown at right
- ▶ Before LinearX™ correction in blue
- ▶ After LinearX™ correction in red (tonal spurs are common to both)
- ▶ Training was done using a different wideband training signal spanning 400 – 600M



Conclusion

Summary

Challenges	Possible avenues to solutions
Heat management/Power efficiency	Power efficient Devices, Circuits and Systems
	New materials
	New architectures
Phase noise in sampling clocks	New materials (photonics?)
	Hybrid continuous-discrete sampling systems
Packaging/Interconnect strays	System partitioning
	Heterogeneous Integration
	3D integration
MOS scaling	Greater digital-analog co-design
	Parallel analog processing architectures
Higher frequency electronics	New devices/III-V
	Photonics/CMOS integration

Conclusion

A comprehensive approach is required to address the multiple important design constraints:

- Heat removal
- Devices' reliability and aging
- Process technology
- Packaging
- Data interfaces
- Performance/band/power consumption
- Area/costs

QUESTIONS!?

